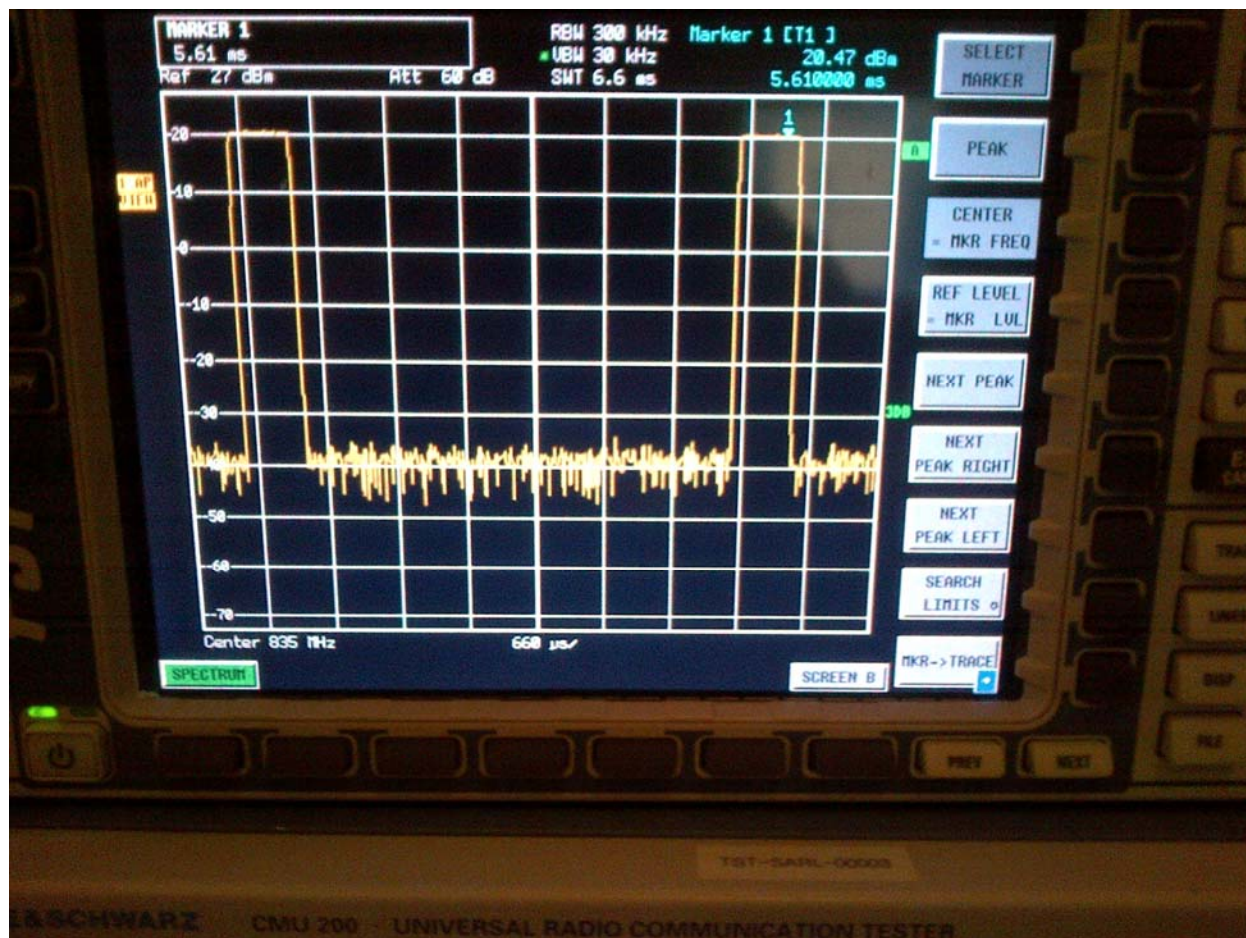


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Annex A: Measurement data and plots

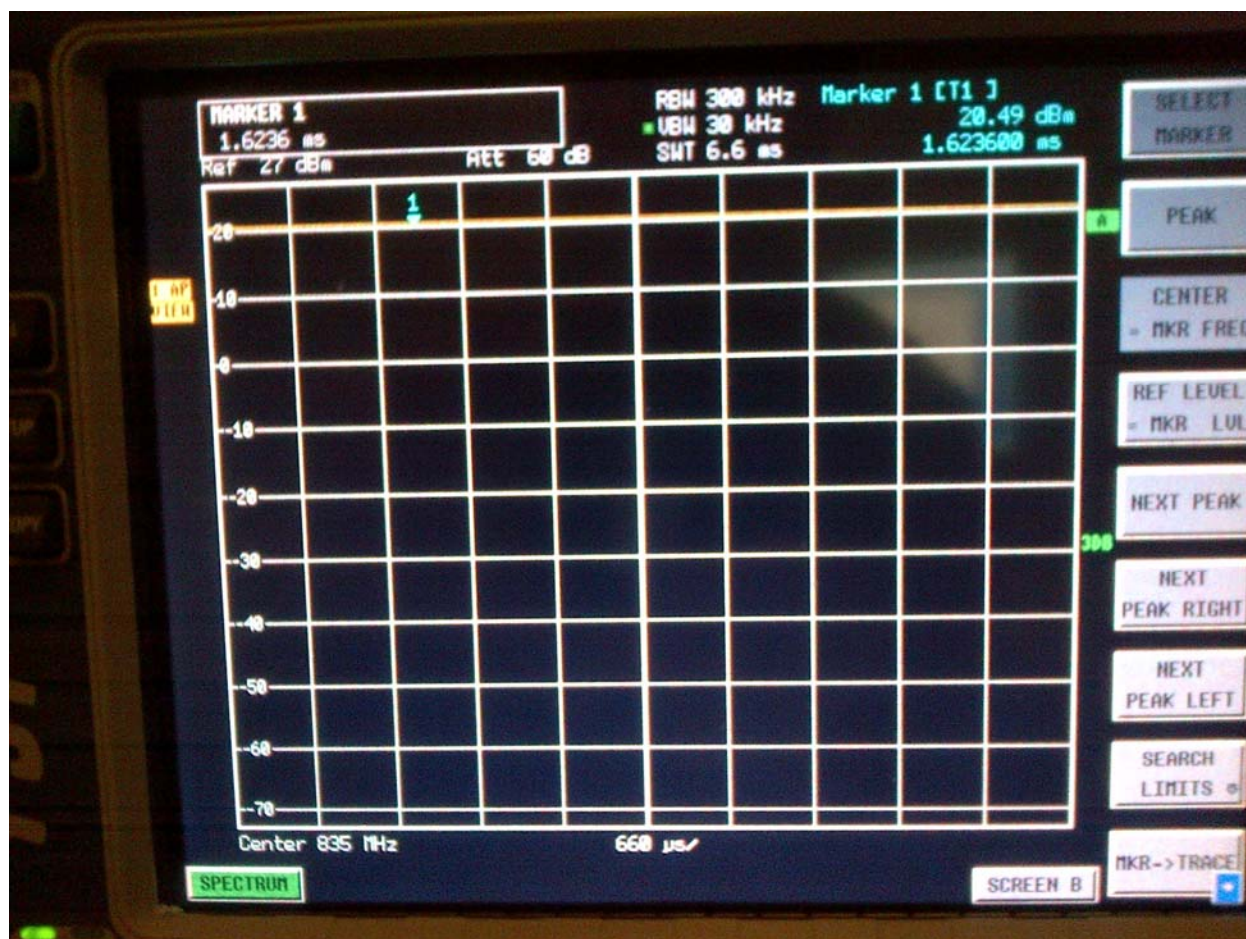
A.1 Spectrum analyser plots: GSM, UMTS, CDMA, CW, 80%AM, signals

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GSM 835 MHz

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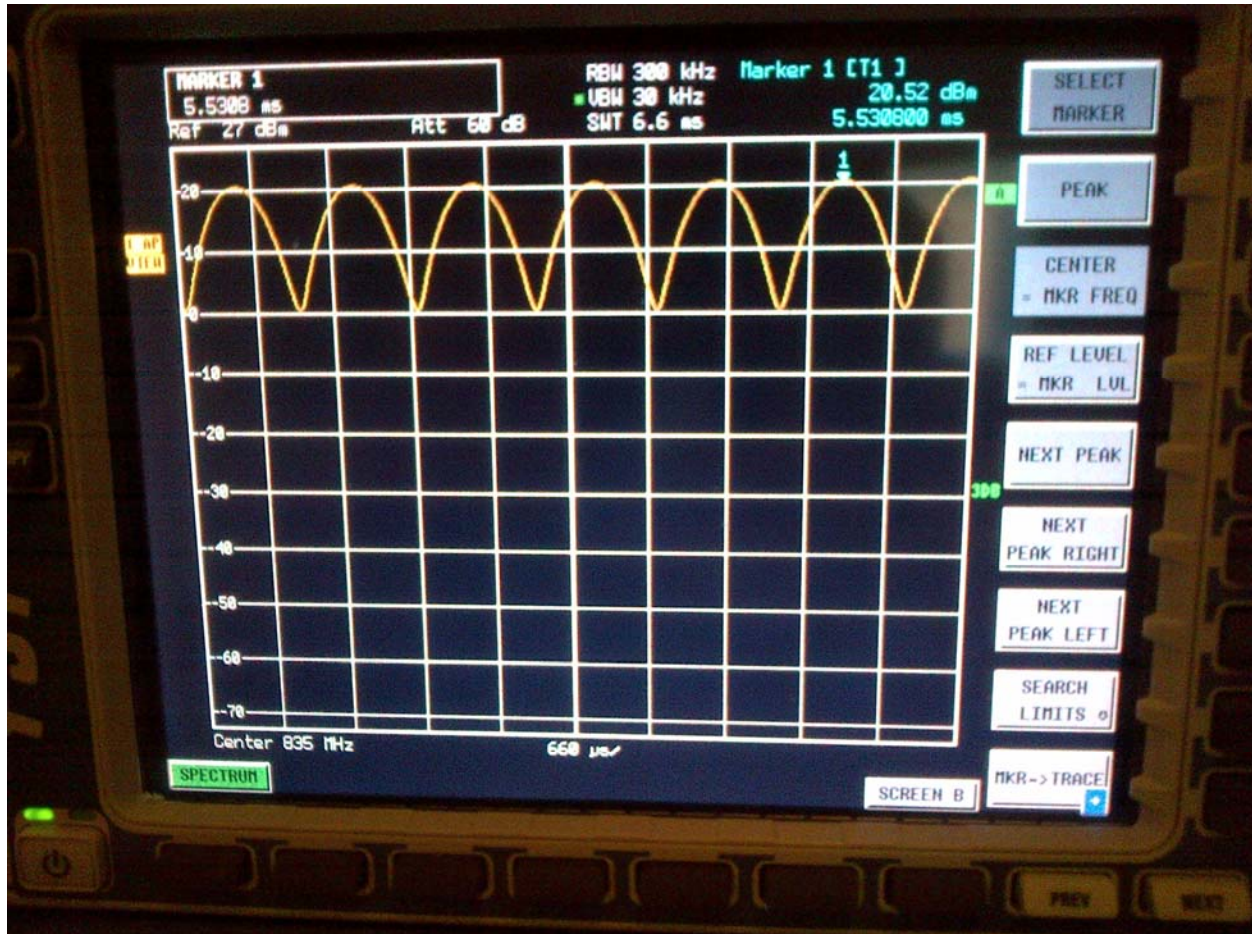
CW 835 MHz

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

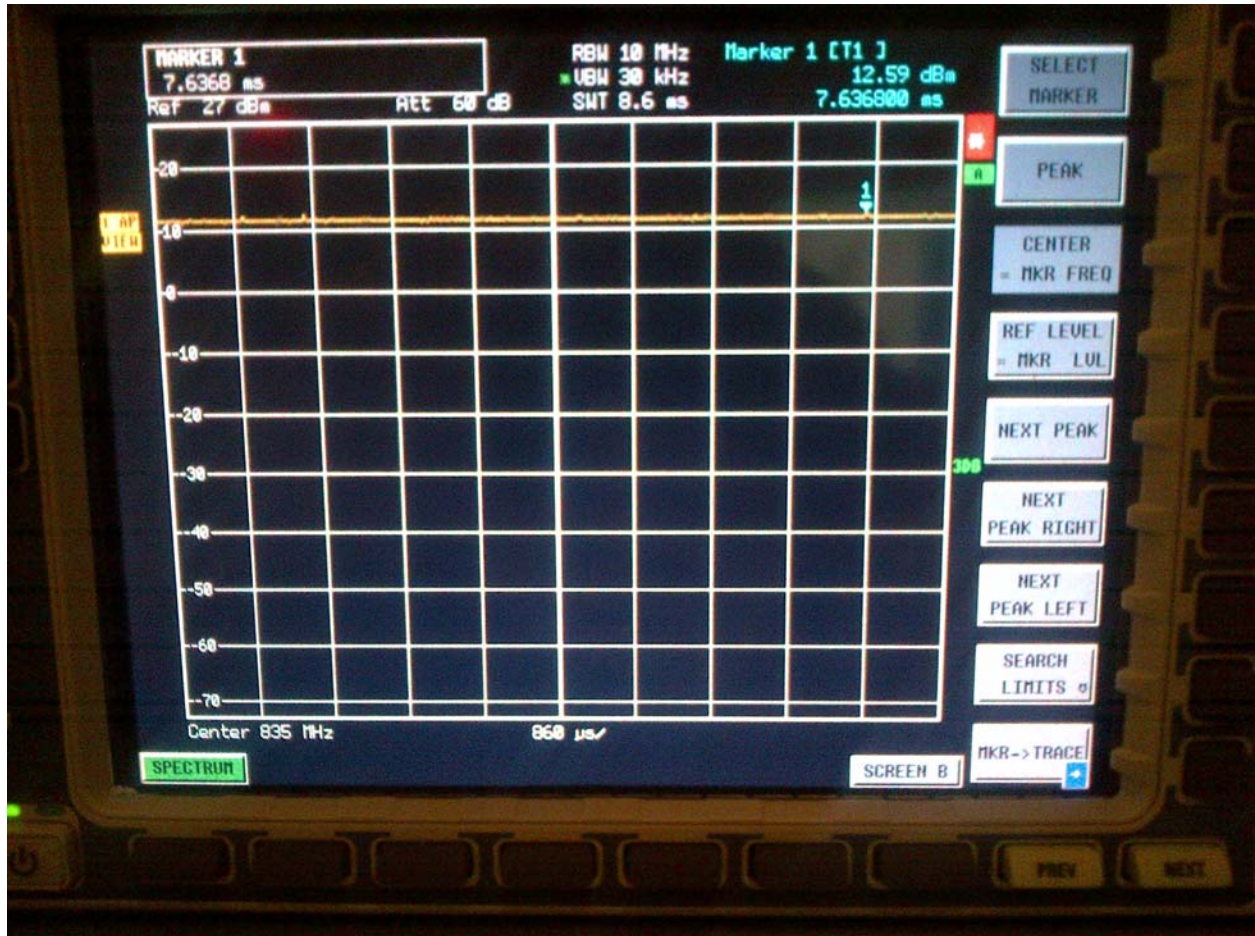
Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW



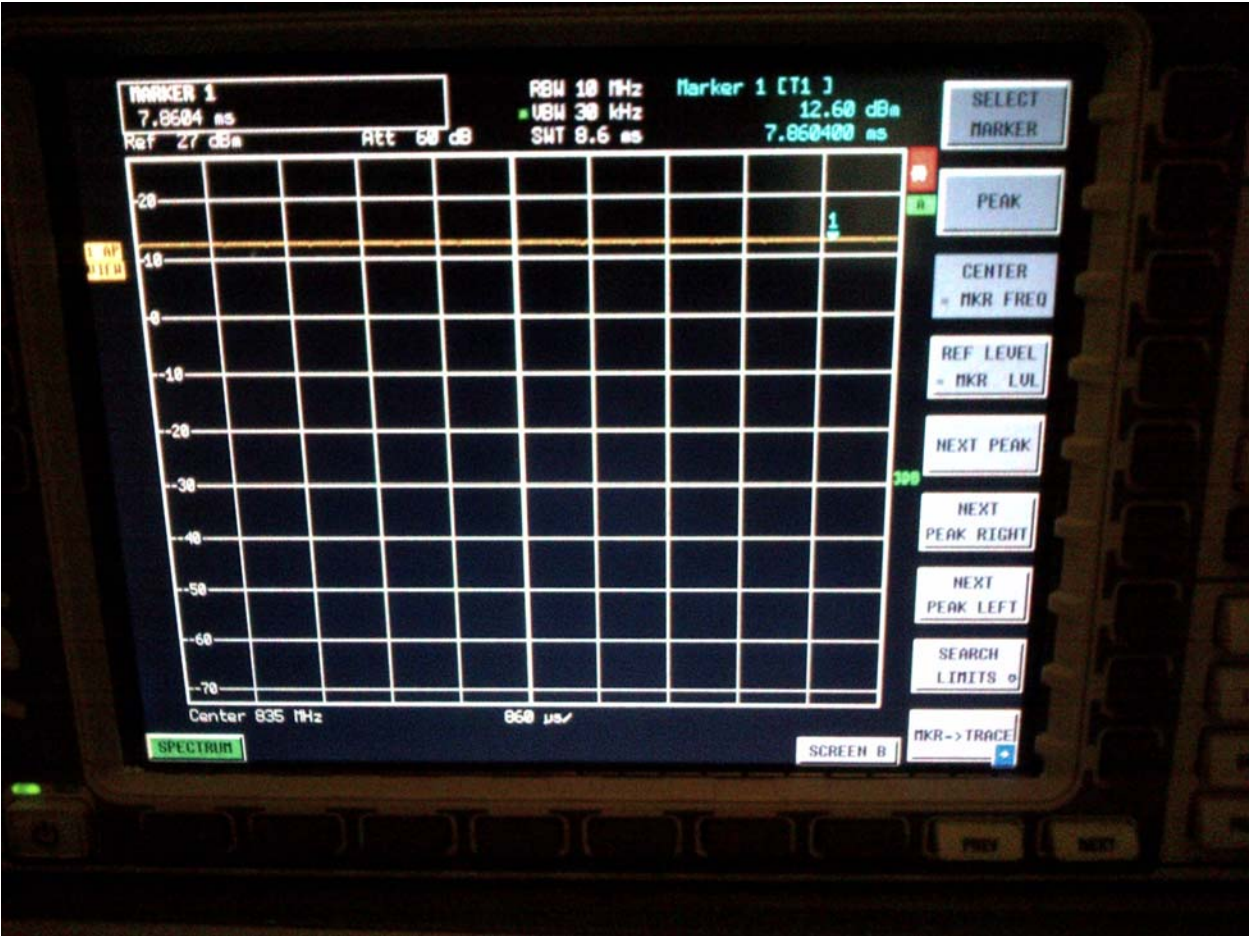
AM 80% 835 MHz

		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 5 (158)
Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW	



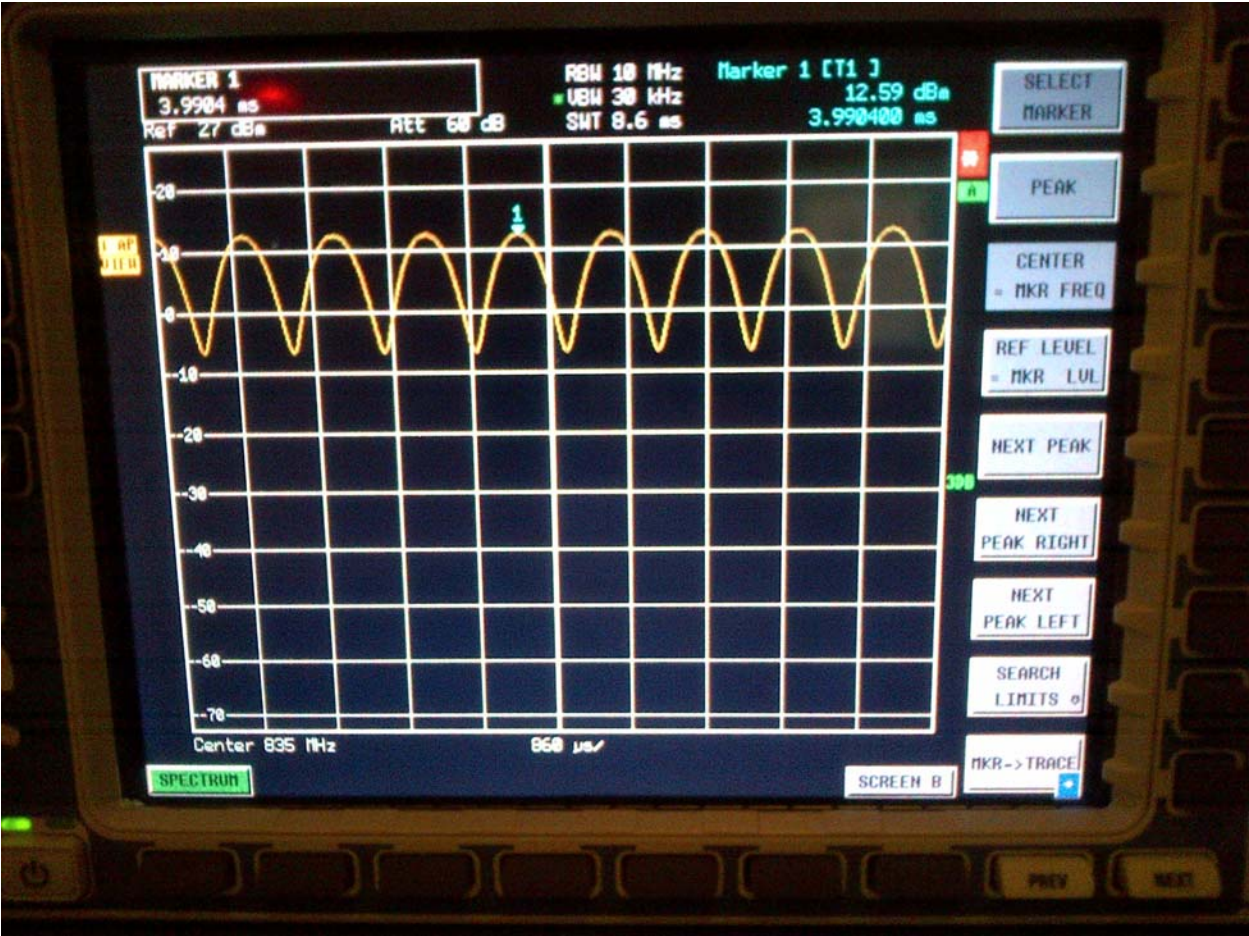
UMTS 835 MHz

		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 6 (158)
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CW 835 MHz

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AM 80% 835 MHz

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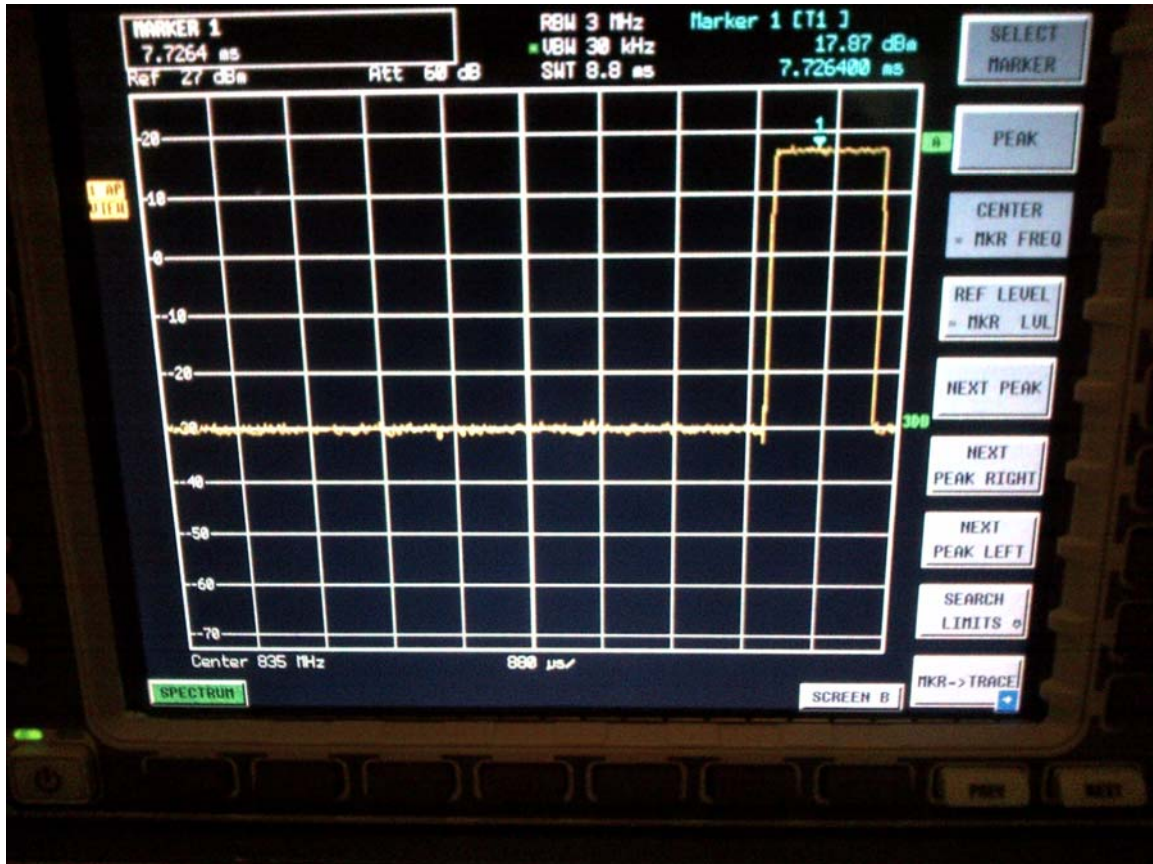
CDMA 835 MHz (BC0)

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW



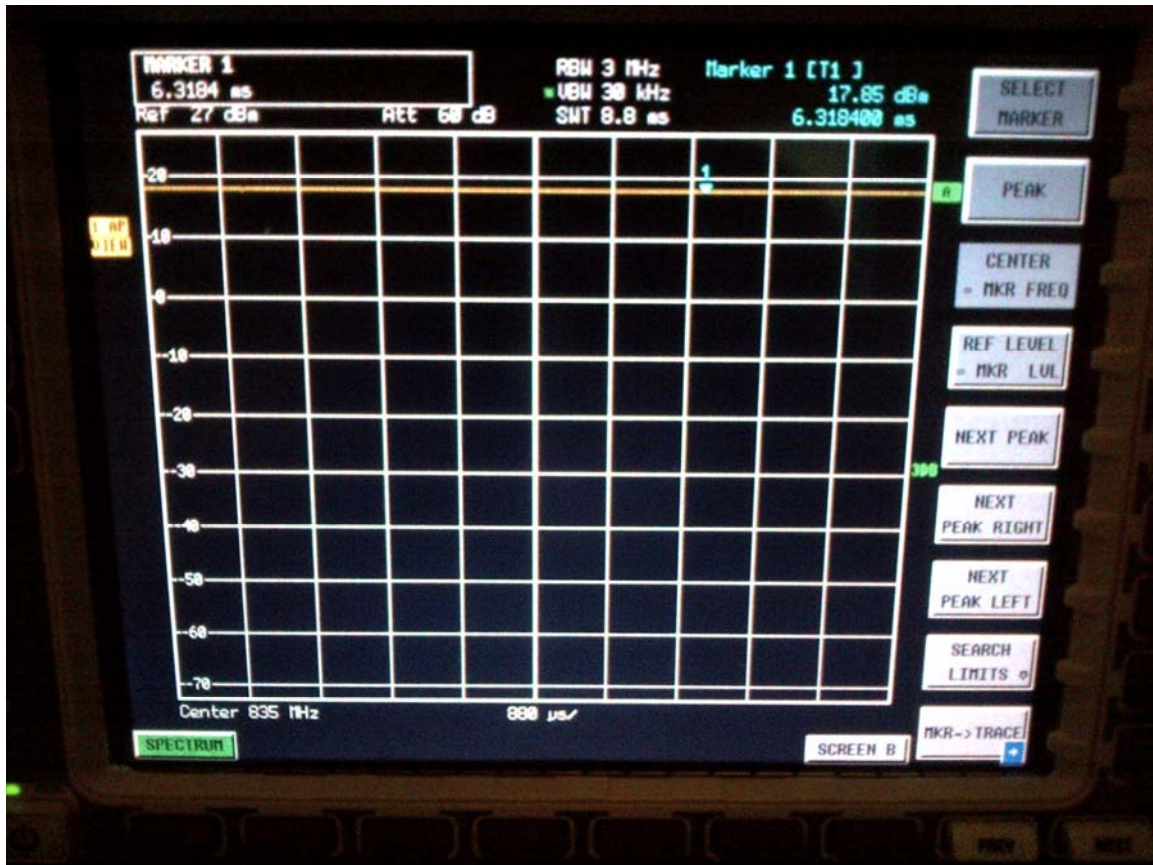
CDMA 835 MHz (BC0) 1/8th

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

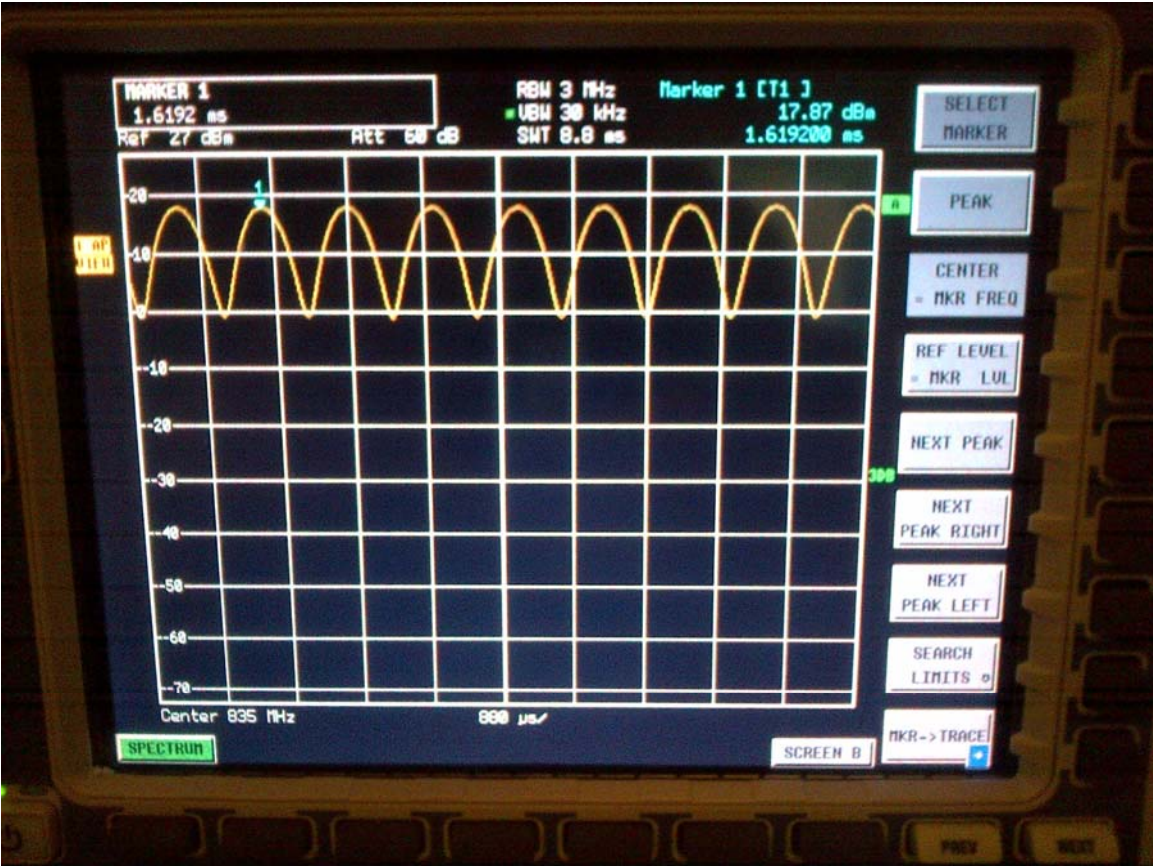
Report No
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FCC ID
L6ARFQ110LW



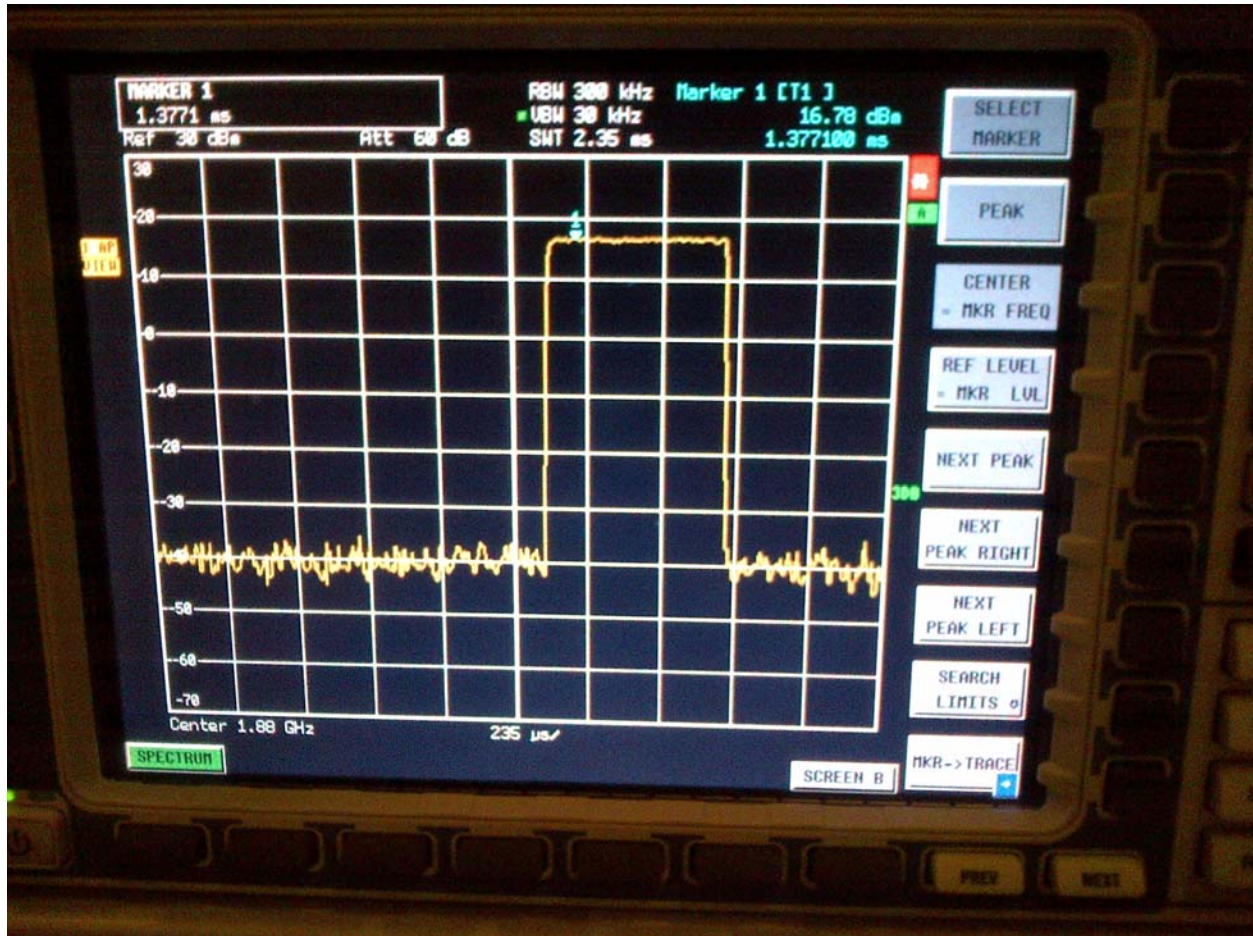
CW 835 MHz

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Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW	



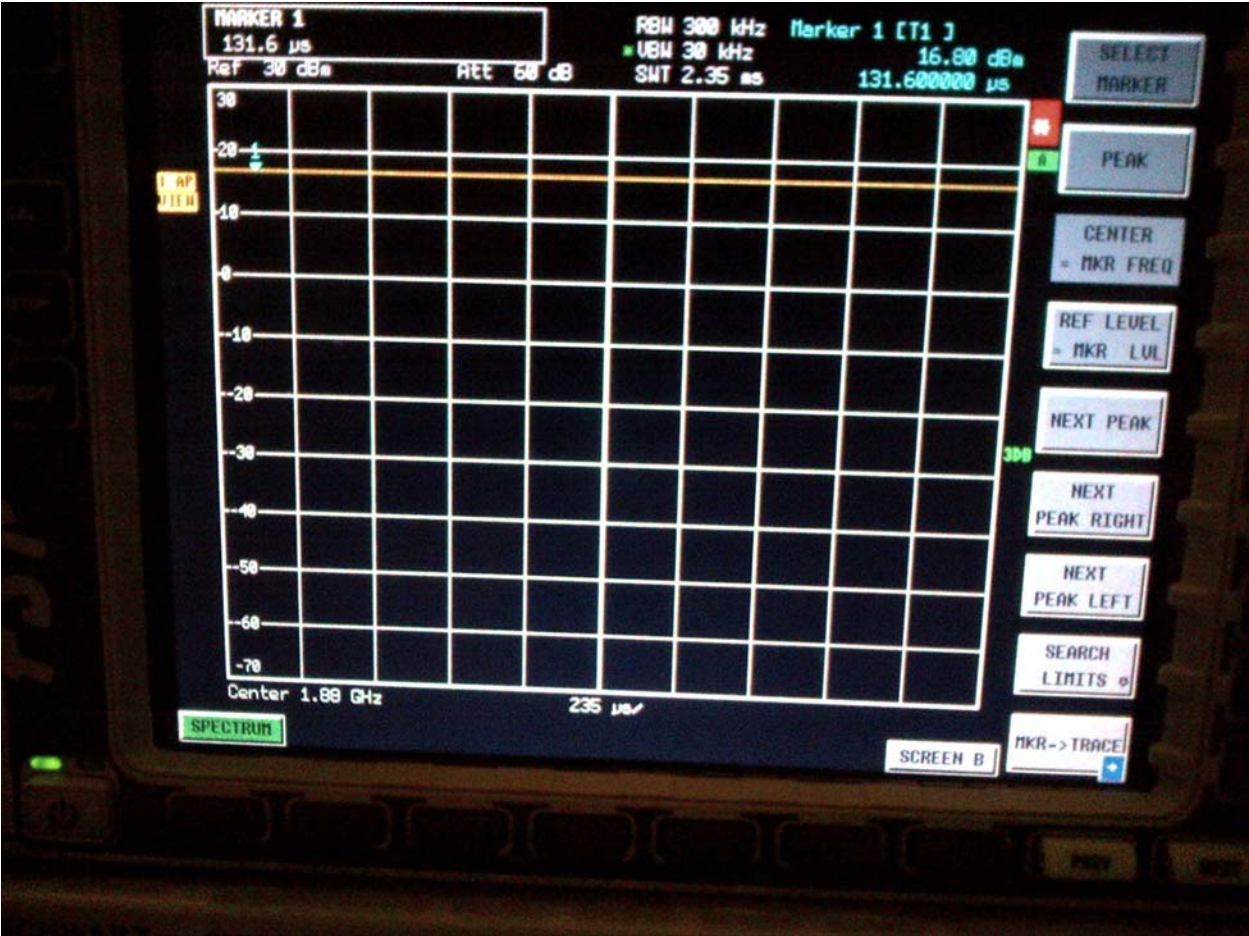
AM 80% 835 MHz

	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 12 (158)
Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW



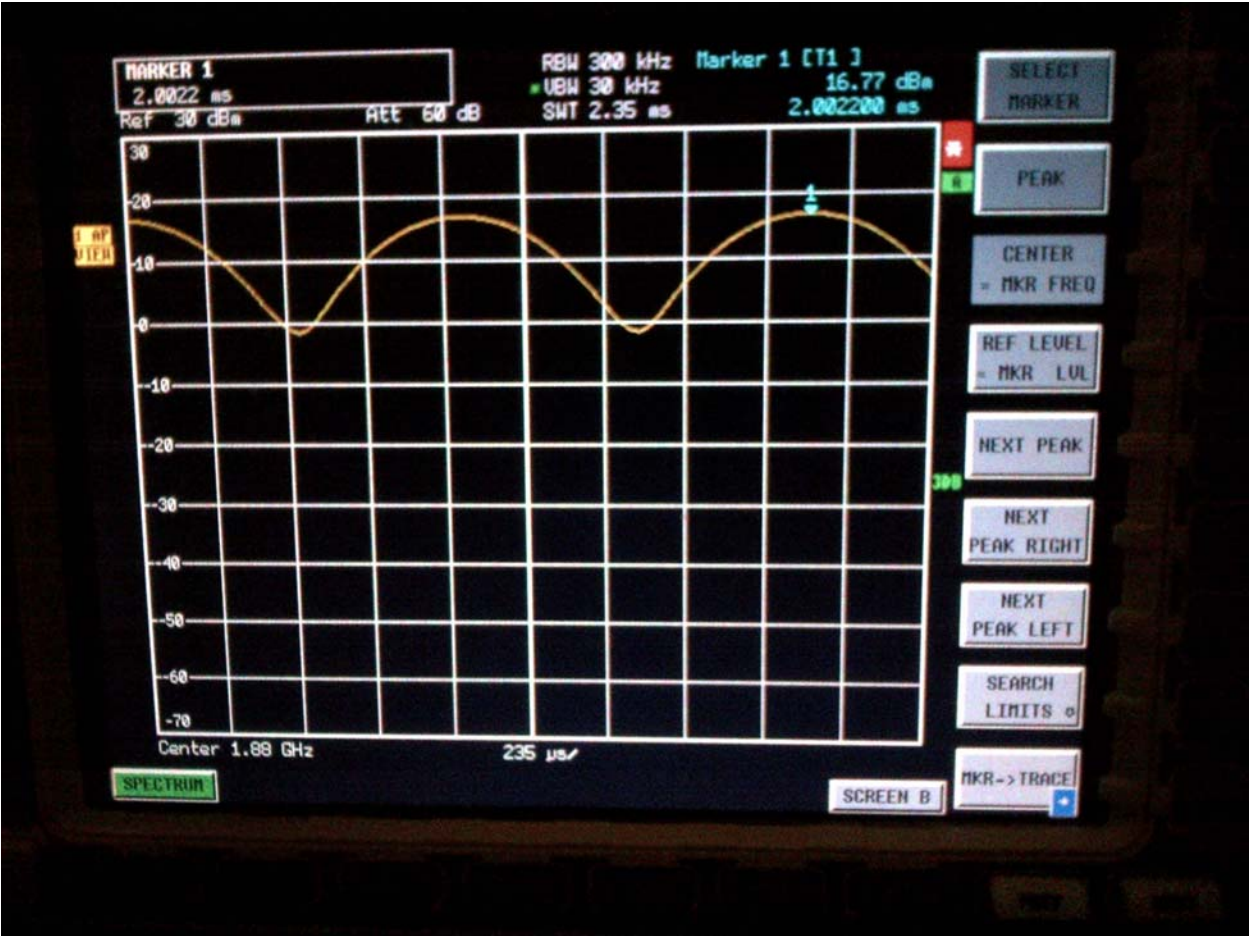
GSM 1880 MHz

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CW 1880 MHz

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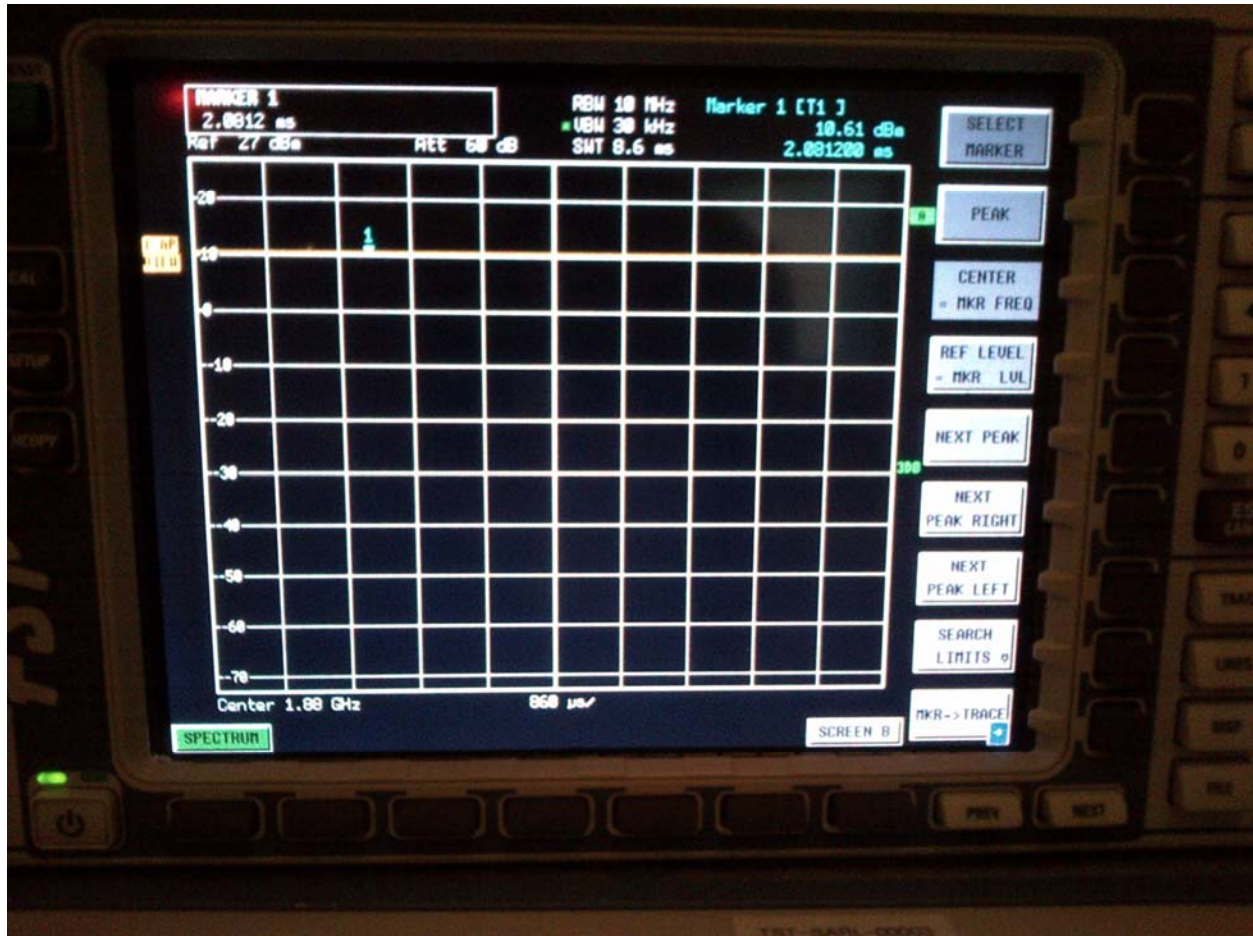
AM 80 % 1880 MHz

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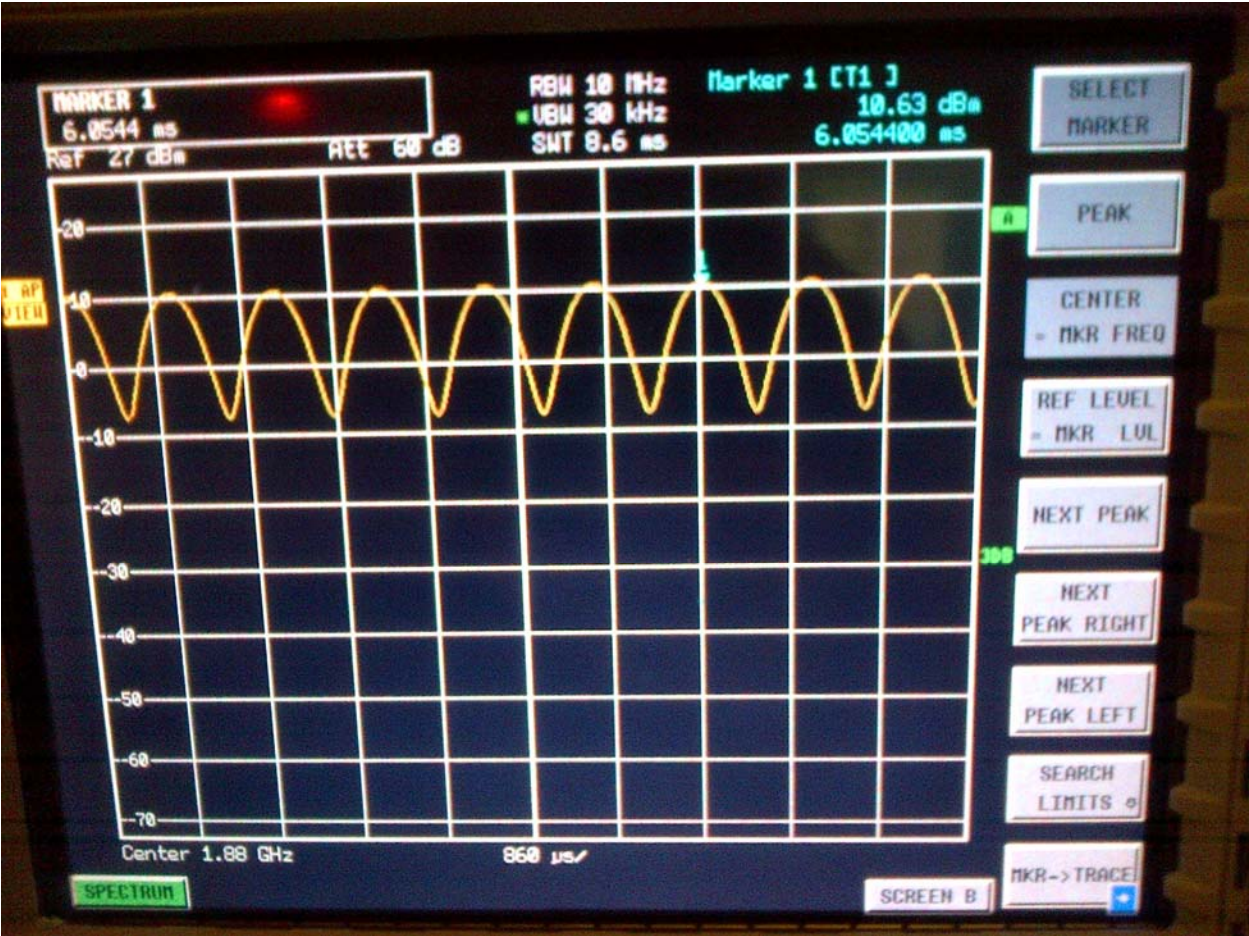
UMTS 1880 MHz

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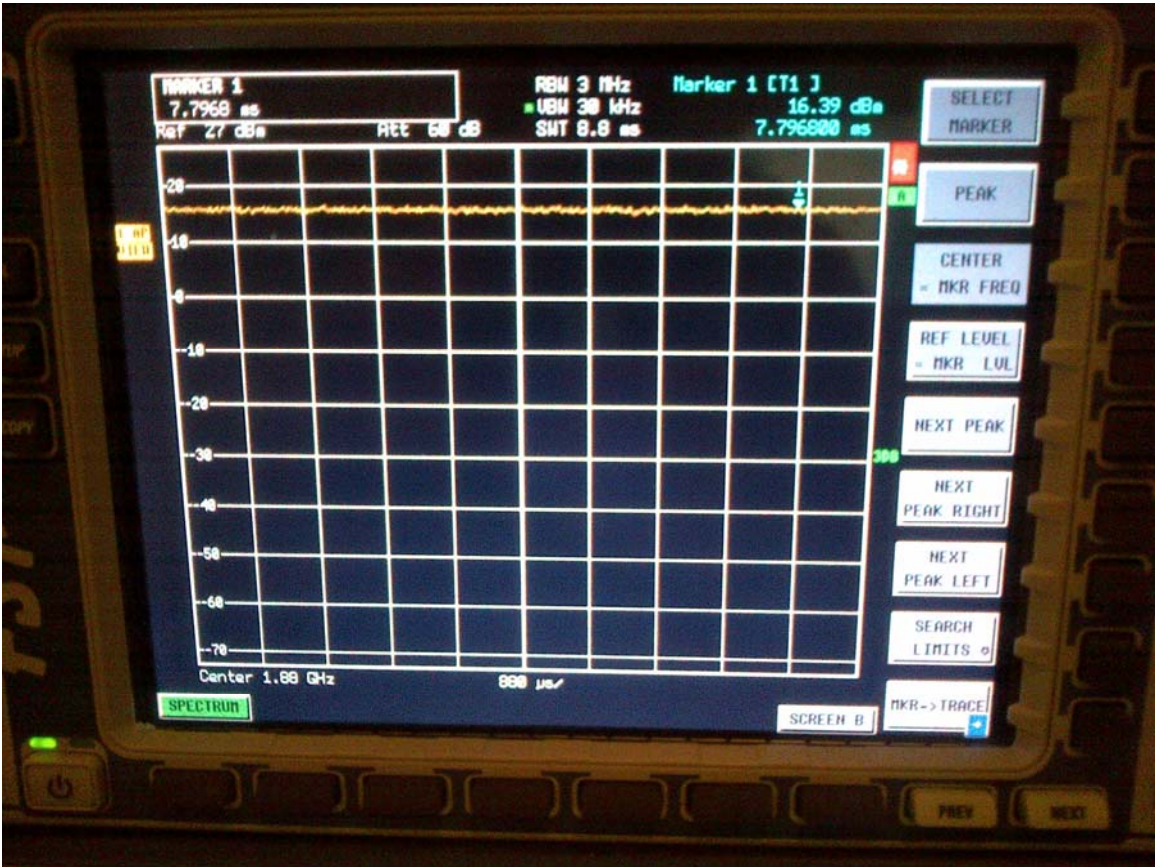
CW 1880 MHz

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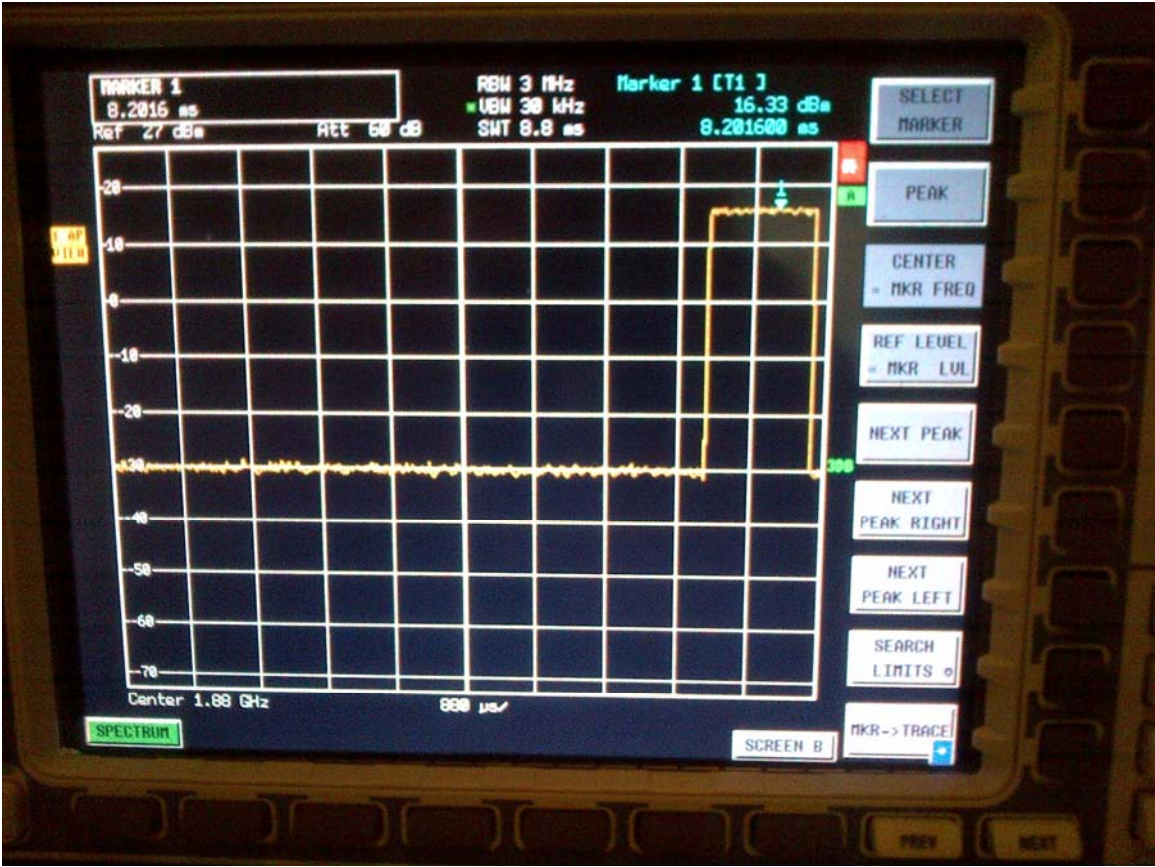
AM 80 % 1880 MHz

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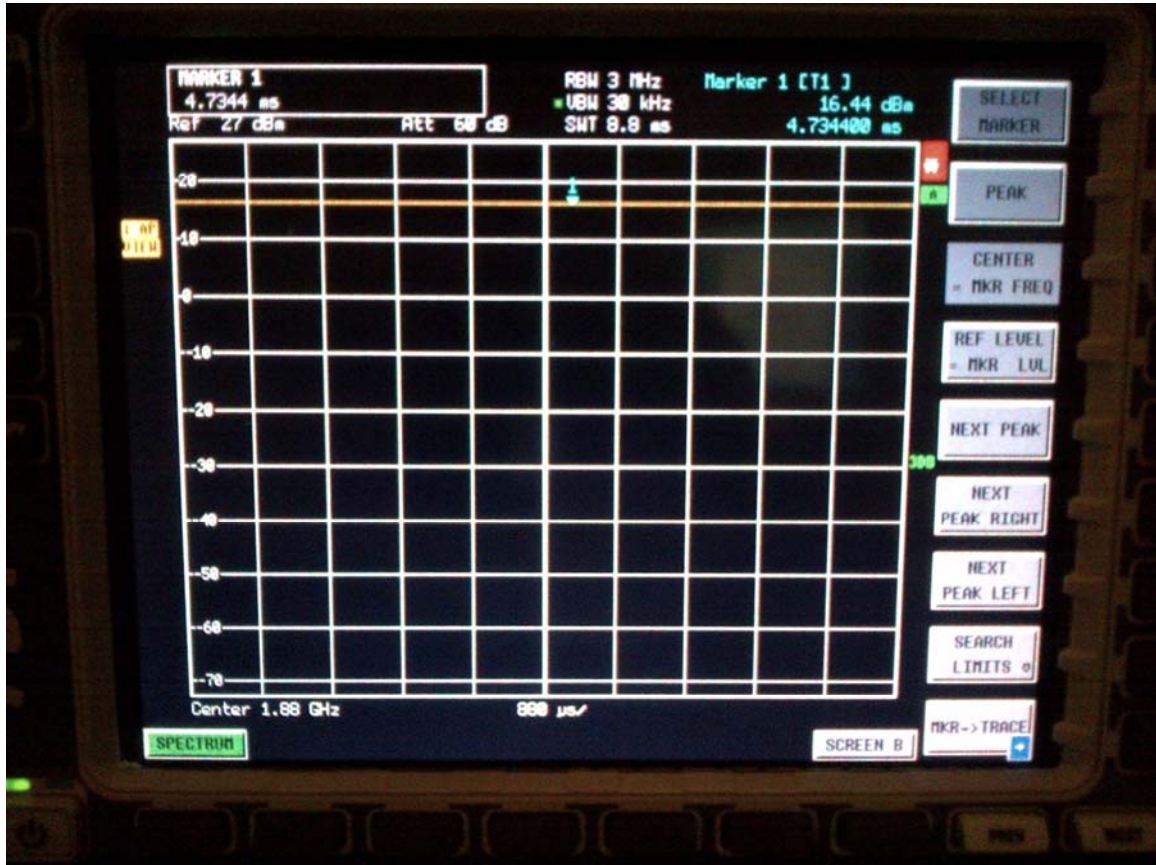
CDMA 1880 MHz (BC1)

		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 19 (158)
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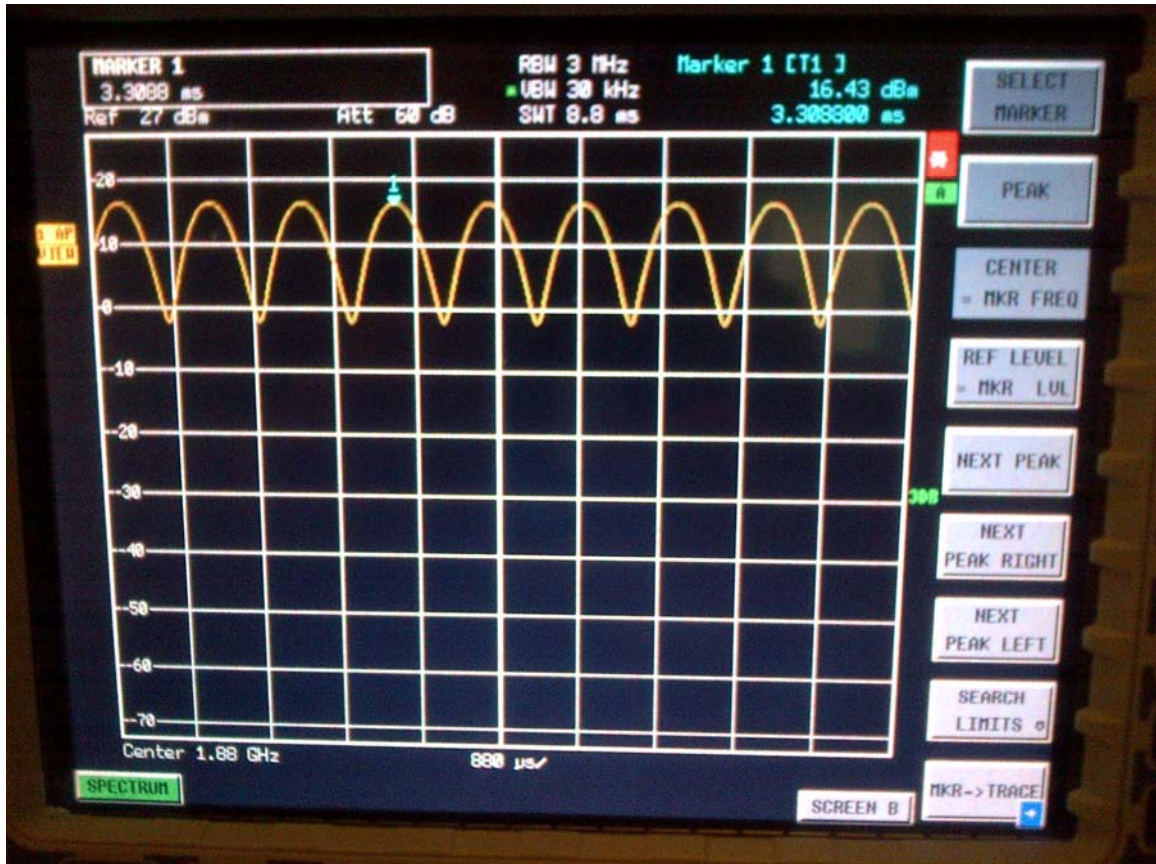
CDMA 1880 MHz (BC1) 1/8 th

	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 20 (158)
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CW 1880 MHz

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AM 80% 1880 MHz

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A.2 Dipole validation and probe modulation factor plots

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Date/Time: 4/24/2013 3:48:05 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_validation_835 MHz_04_24_13

DUT: HAC-Dipole 835 MHz; Type: CD835V3; Serial: 1011

Communication System: CW; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Dipole E-Field measurement/E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 106.1 V/m; Power Drift = -0.02 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 168.2 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 153.8 V/m	Grid 2 M4 164.4 V/m	Grid 3 M4 164.1 V/m
Grid 4 M4 81.96 V/m	Grid 5 M4 85.57 V/m	Grid 6 M4 84.27 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW

154.3 V/m

168.2 V/m

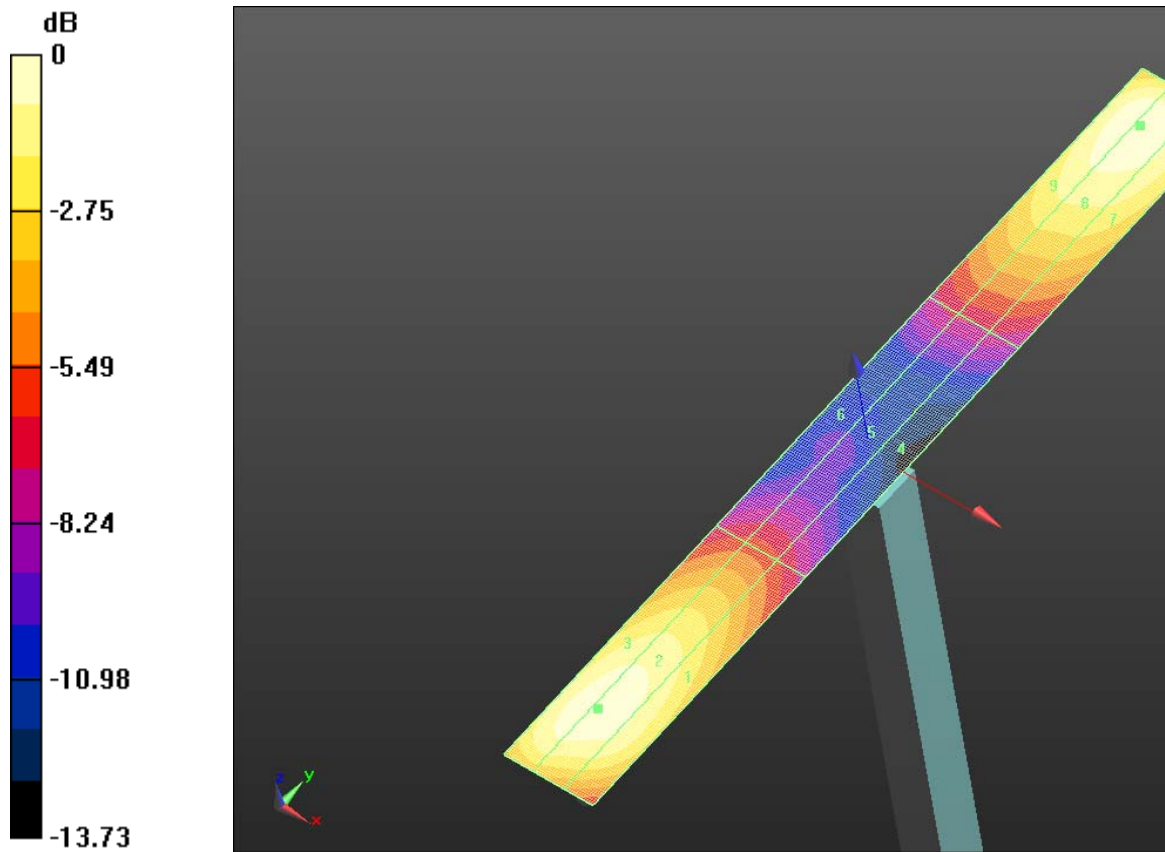
167.7 V/m

Cursor:

Total = 168.2 V/m

E Category: M4

Location: -2.5, 80, 4.7 mm



0 dB = 168.2 V/m = 44.52 dBV/m

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Date/Time: 6/28/2012 1:13:34 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_GSM835 MHz_06_28_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: GSM 835_PMF, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - GSM 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 34.76 V/m; Power Drift = -0.00 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 54.25 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 49.26 V/m	Grid 2 M4 51.48 V/m	Grid 3 M4 51.48 V/m
Grid 4 M4 27.95 V/m	Grid 5 M4 28.56 V/m	Grid 6 M4 28.13 V/m
Grid 7 M4 51.48 V/m	Grid 8 M4 54.25 V/m	Grid 9 M4 53.95 V/m

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Cursor:

Total = 54.247 V/m

E Category: M4

Location: -2.5, 80.5, 4.7 mm

**Dipole E-Field measurement/E Scan - CW 835_PMF/Hearing Aid
Compatibility Test (41x361x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 103.0 V/m; Power Drift = -0.02 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 162.8 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 148.5 V/m	Grid 2 M4 160.5 V/m	Grid 3 M4 160.4 V/m
Grid 4 M4 82.74 V/m	Grid 5 M4 86.24 V/m	Grid 6 M4 84.62 V/m
Grid 7 M4 158.1 V/m	Grid 8 M4 162.8 V/m	Grid 9 M4 155.2 V/m

Cursor:

Total = 162.8 V/m

E Category: M4

Location: 0.5, 79.5, 4.7 mm

**Dipole E-Field measurement/E Scan - AM80%_ 835_PMF/Hearing
Aid Compatibility Test (41x361x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 64.73 V/m; Power Drift = 0.02 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 102.0 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 93.30 V/m	Grid 2 M4 100.3 V/m	Grid 3 M4 100.3 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4

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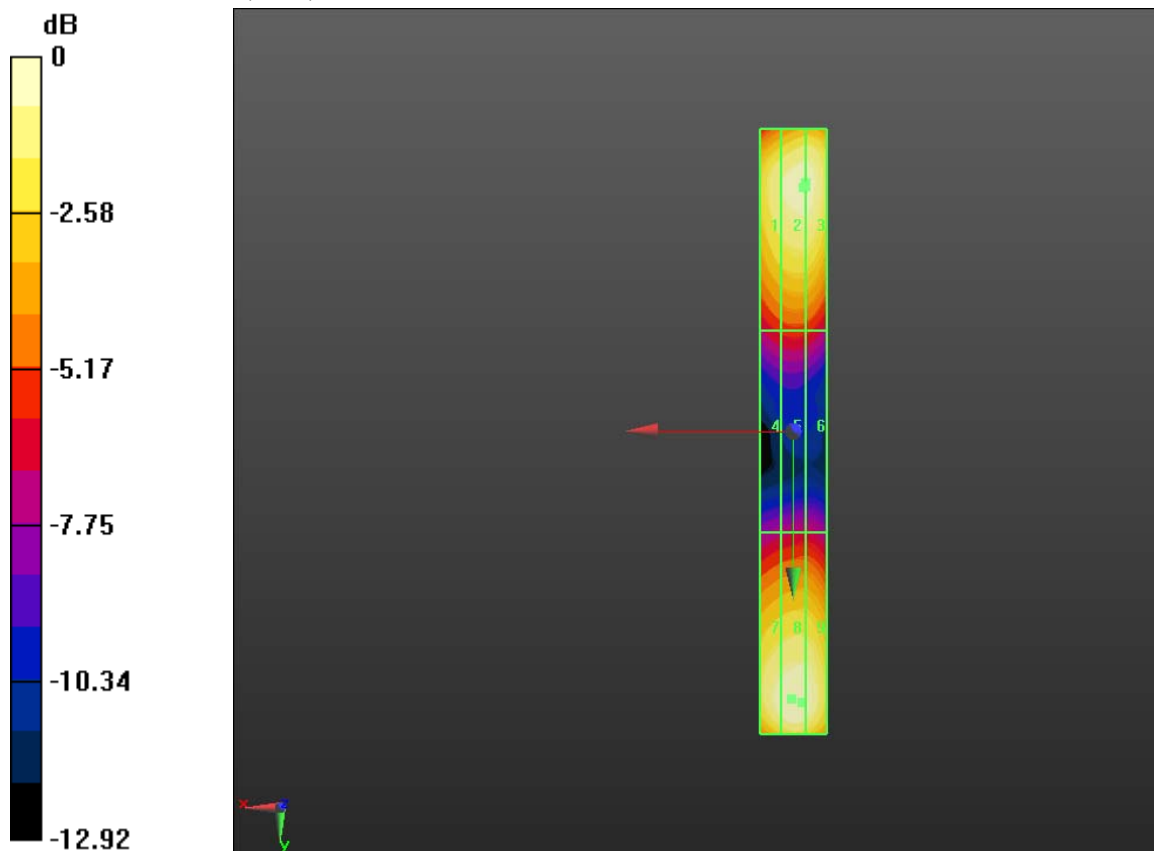
52.75 V/m	54.62 V/m	53.83 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
99.38 V/m	102.0 V/m	97.92 V/m

Cursor:

Total = 102.0 V/m

E Category: M4

Location: 0.5, 79.5, 4.7 mm



0 dB = 54.250V/m = 34.69 dB V/m

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Daoud Attayi	Feb. 17-29, June 28, 2012 April 24-26, 2013	RTS-6026-1304-52	L6ARFQ110LW	

Date/Time: 2/17/2012 12:24:15 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_UMTS835 MHz_02_17_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: WCDMA FDD V, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - UMTS 835_PMF/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 41.08 V/m; Power Drift = 0.03 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 64.41 V/m

Near-field category: M4 (AWF 0 dB)

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PMF scaled E-field

Grid 1 M4 53.11 V/m	Grid 2 M4 55.59 V/m	Grid 3 M4 55.40 V/m
Grid 4 M4 29.72 V/m	Grid 5 M4 30.66 V/m	Grid 6 M4 29.79 V/m
Grid 7 M4 61.55 V/m	Grid 8 M4 64.41 V/m	Grid 9 M4 63.22 V/m

Cursor:

Total = 64.412 V/m

E Category: M4

Location: -0.5, 79, 4.7 mm

**Dipole E-Field measurement/E Scan - CW 835_PMF/Hearing Aid
Compatibility Test (41x361x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 43.11 V/m; Power Drift = -0.14 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 68.64 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 58.55 V/m	Grid 2 M4 59.20 V/m	Grid 3 M4 57.13 V/m
Grid 4 M4 32.35 V/m	Grid 5 M4 32.63 V/m	Grid 6 M4 31.24 V/m
Grid 7 M4 61.85 V/m	Grid 8 M4 68.64 V/m	Grid 9 M4 68.56 V/m

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Cursor:

Total = 68.635 V/m

E Category: M4

Location: -3, 79.5, 4.7 mm

**Dipole E-Field measurement/E Scan - AM80%_ 835_PMF/Hearing
Aid Compatibility Test (41x361x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 28.41 V/m; Power Drift = 0.09 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 45.21 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 38.28 V/m	Grid 2 M4 38.73 V/m	Grid 3 M4 37.25 V/m
Grid 4 M4 21.72 V/m	Grid 5 M4 21.89 V/m	Grid 6 M4 20.80 V/m
Grid 7 M4 40.90 V/m	Grid 8 M4 45.21 V/m	Grid 9 M4 45.16 V/m

Cursor:

Total = 45.209 V/m

E Category: M4

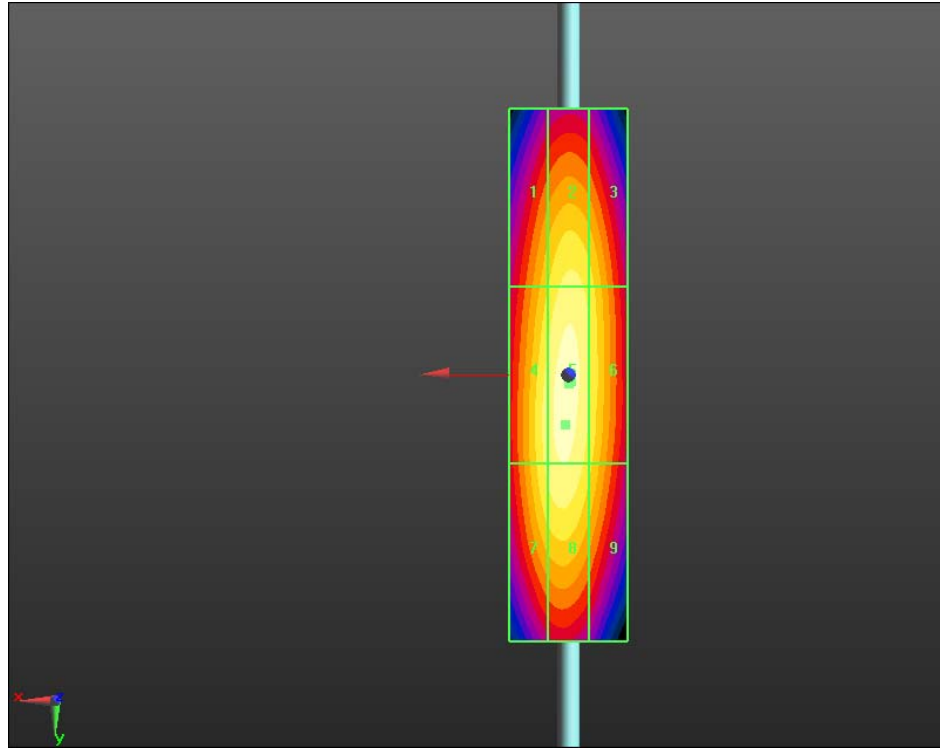
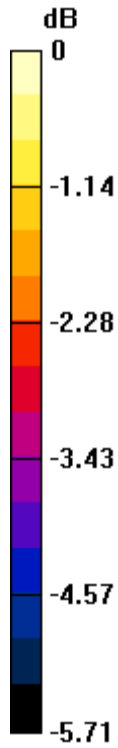
Location: -3, 79.5, 4.7 mm

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW



0 dB = 0.180A/m = -14.89 dB A/m

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Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_CDMA835 MHz_02_29_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: CDMA 850, Communication System: CDMA 850 1/8th,
Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - CDMA FR 835_PMF/Hearing Aid

Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 79.95 V/m; Power Drift = -0.18 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 118.9 V/m

Near-field category: M4 (AWF 0 dB)

		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 33 (158)
Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW	

PMF scaled E-field

Grid 1 M4 104.7 V/m	Grid 2 M4 108.7 V/m	Grid 3 M4 107.6 V/m
Grid 4 M4 56.56 V/m	Grid 5 M4 57.99 V/m	Grid 6 M4 56.06 V/m
Grid 7 M4 112.0 V/m	Grid 8 M4 118.9 V/m	Grid 9 M4 116.1 V/m

Cursor:

Total = 118.9 V/m

E Category: M4

Location: -0.5, 79, 4.7 mm

Dipole E-Field measurement/E Scan - CDMA 1/8th 835_PMF 2/Hearing Aid

Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 30.10 V/m; Power Drift = 0.23 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 43.21 V/m

Near-field category: **M4 (AWF 0 dB)**

PMF scaled E-field

Grid 1 M4 39.00 V/m	Grid 2 M4 41.81 V/m	Grid 3 M4 39.31 V/m
Grid 4 M4 20.47 V/m	Grid 5 M4 22.99 V/m	Grid 6 M4 20.34 V/m
Grid 7 M4 41.05 V/m	Grid 8 M4 43.21 V/m	Grid 9 M4 42.62 V/m

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Cursor:

Total = 43.214 V/m

E Category: M4

Location: -0.5, 84, 4.7 mm

Dipole E-Field measurement/E Scan - CW 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 82.56 V/m; Power Drift = -0.07 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 125.5 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 110.7 V/m	Grid 2 M4 114.9 V/m	Grid 3 M4 113.7 V/m
Grid 4 M4 60.24 V/m	Grid 5 M4 61.44 V/m	Grid 6 M4 59.31 V/m
Grid 7 M4 119.5 V/m	Grid 8 M4 125.5 V/m	Grid 9 M4 122.3 V/m

Cursor:

Total = 125.5 V/m

E Category: M4

Location: -0.5, 79, 4.7 mm

Dipole E-Field measurement/E Scan - AM80%_ 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 51.22 V/m; Power Drift = 0.06 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 78.06 V/m

Near-field category: M4 (AWF 0 dB)

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW

PMF scaled E-field

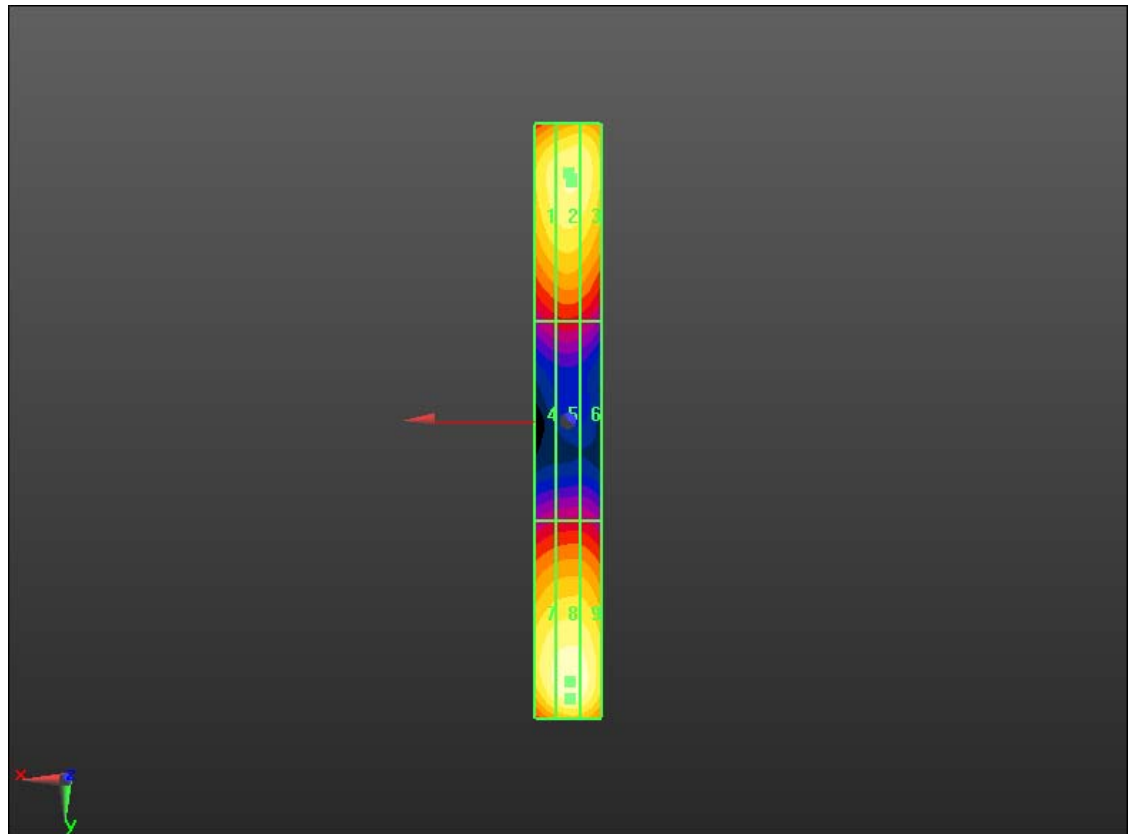
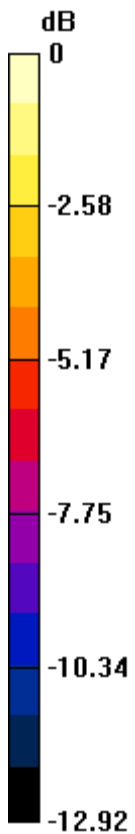
Grid 1 M4 69.60 V/m	Grid 2 M4 71.98 V/m	Grid 3 M4 71.35 V/m
Grid 4 M4 38.16 V/m	Grid 5 M4 38.79 V/m	Grid 6 M4 37.51 V/m
Grid 7 M4 74.44 V/m	Grid 8 M4 78.06 V/m	Grid 9 M4 76.37 V/m

Cursor:

Total = 78.060 V/m

E Category: M4

Location: -0.5, 79, 4.7 mm



0 dB = 118.9V/m = 41.50 dB V/m

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Date/Time: 4/24/2013 3:08:00 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_validation_1880 MHz_04_24_13

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CW; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Dipole E-Field measurement/E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 142.0 V/m; Power Drift = -0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 131.0 V/m

Near-field category: M2 (AWF 0 dB)

PMF scaled E-field

Grid 1 M2 121.1 V/m	Grid 2 M2 130.6 V/m	Grid 3 M2 130.4 V/m
Grid 4 M3 82.22 V/m	Grid 5 M3 87.04 V/m	Grid 6 M3 85.72 V/m
Grid 7 M2	Grid 8 M2	Grid 9 M2

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Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW

118.4 V/m

131.0 V/m

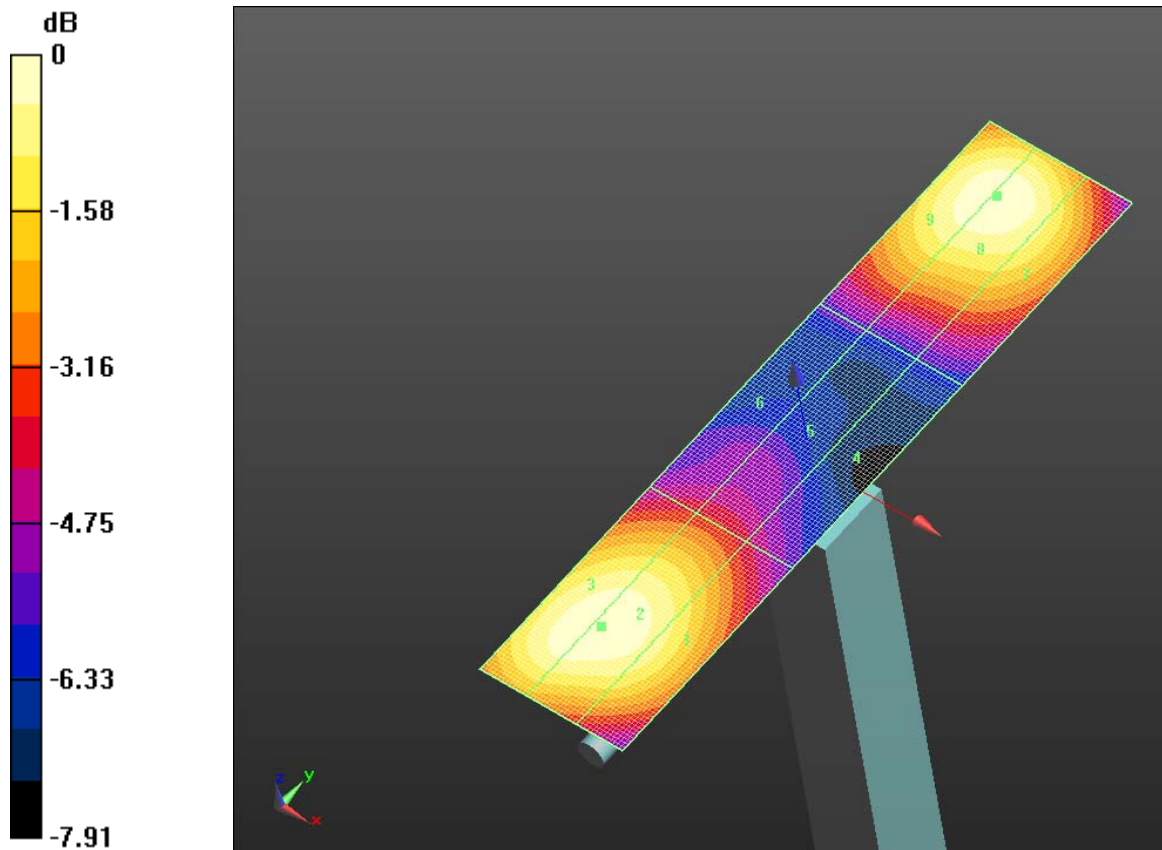
130.8 V/m

Cursor:

Total = 131.0 V/m

E Category: M2

Location: -3, 37.5, 4.7 mm



0 dB = 131.0 V/m = 42.35 dBV/m

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Date/Time: 6/28/2012 12:54:33 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_GSM1880 MHz_06_28_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: GSM 1880, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - GSM 1880_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 33.26 V/m; Power Drift = 0.00 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 29.81 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 27.34 V/m	Grid 2 M4 28.65 V/m	Grid 3 M4 28.59 V/m
Grid 4 M4 19.83 V/m	Grid 5 M4 20.51 V/m	Grid 6 M4 20.10 V/m
Grid 7 M4 28.20 V/m	Grid 8 M4 29.81 V/m	Grid 9 M4 29.37 V/m

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Cursor:

Total = 29.810 V/m

E Category: M4

Location: -1, 38.5, 4.7 mm

**Dipole E-Field measurement/E Scan- CW 1800_PMF/Hearing Aid
Compatibility Test (41x181x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 95.34 V/m; Power Drift = 0.01 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 84.88 V/m

Near-field category: M3 (AWF 0 dB)

PMF scaled E-field

Grid 1 M3 78.80 V/m	Grid 2 M3 82.95 V/m	Grid 3 M3 82.43 V/m
Grid 4 M4 56.84 V/m	Grid 5 M4 58.53 V/m	Grid 6 M4 56.53 V/m
Grid 7 M3 80.11 V/m	Grid 8 M3 84.88 V/m	Grid 9 M3 83.31 V/m

Cursor:

Total = 84.885 V/m

E Category: M3

Location: -0.5, 38.5, 4.7 mm

**Dipole E-Field measurement/E Scan - AM80%_ 1880_PMF/Hearing
Aid Compatibility Test (41x181x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 60.62 V/m; Power Drift = -0.03 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 53.60 V/m

Near-field category: M4 (AWF 0 dB)

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
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FCC ID
L6ARFQ110LW

PMF scaled E-field

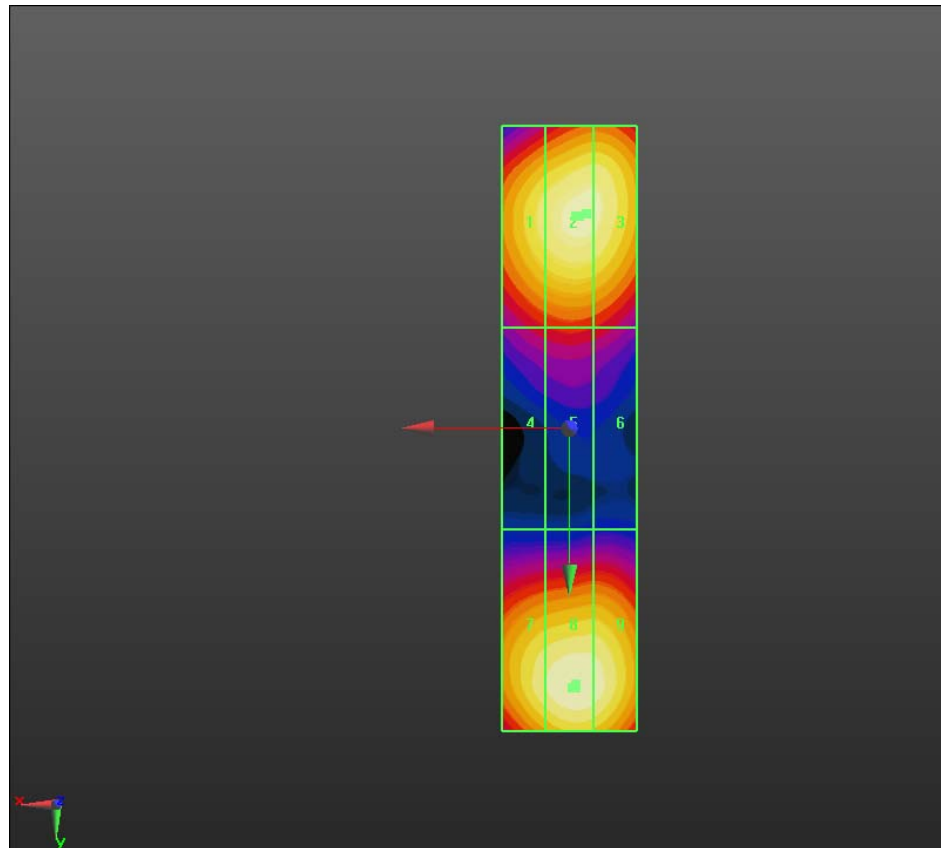
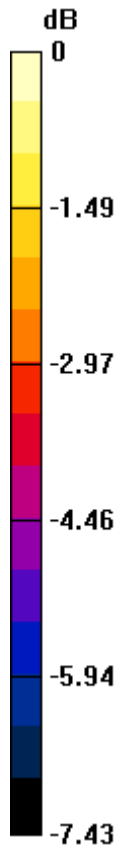
Grid 1 M4 49.75 V/m	Grid 2 M4 52.55 V/m	Grid 3 M4 52.06 V/m
Grid 4 M4 35.78 V/m	Grid 5 M4 36.92 V/m	Grid 6 M4 36.02 V/m
Grid 7 M4 50.66 V/m	Grid 8 M4 53.60 V/m	Grid 9 M4 52.63 V/m

Cursor:

Total = 53.599 V/m

E Category: M4

Location: -1, 38, 4.7 mm



0 dB = 29.810V/m = 29.49 dB V/m

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Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW	

Date/Time: 2/17/2012 2:20:23 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_UMTS1880 MHz_02_17_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: WCDMA FDD II, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - UMTS 1880_PMF/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 47.02 V/m; Power Drift = 0.01 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 42.43 V/m

Near-field category: M4 (AWF 0 dB)

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PMF scaled E-field

Grid 1 M4 37.98 V/m	Grid 2 M4 39.42 V/m	Grid 3 M4 39.04 V/m
Grid 4 M4 26.86 V/m	Grid 5 M4 27.50 V/m	Grid 6 M4 26.70 V/m
Grid 7 M4 39.63 V/m	Grid 8 M4 42.43 V/m	Grid 9 M4 41.87 V/m

Cursor:

Total = 42.427 V/m

E Category: M4

Location: -1, 38, 4.7 mm

**Dipole E-Field measurement/E Scan- CW 1800_PMF/Hearing Aid
Compatibility Test (41x181x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 47.33 V/m; Power Drift = -0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 42.41 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 38.23 V/m	Grid 2 M4 39.51 V/m	Grid 3 M4 39.41 V/m
Grid 4 M4 26.94 V/m	Grid 5 M4 27.41 V/m	Grid 6 M4 26.77 V/m
Grid 7 M4 40.02 V/m	Grid 8 M4 42.41 V/m	Grid 9 M4 41.99 V/m

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Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW	

Cursor:

Total = 42.409 V/m

E Category: M4

Location: -1.5, 38, 4.7 mm

**Dipole E-Field measurement/E Scan - AM80%_ 1880_PMF/Hearing
Aid Compatibility Test (41x181x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 30.18 V/m; Power Drift = 0.06 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 27.40 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 24.40 V/m	Grid 2 M4 25.26 V/m	Grid 3 M4 24.95 V/m
Grid 4 M4 17.20 V/m	Grid 5 M4 17.65 V/m	Grid 6 M4 17.12 V/m
Grid 7 M4 25.54 V/m	Grid 8 M4 27.40 V/m	Grid 9 M4 27.02 V/m

Cursor:

Total = 27.402 V/m

E Category: M4

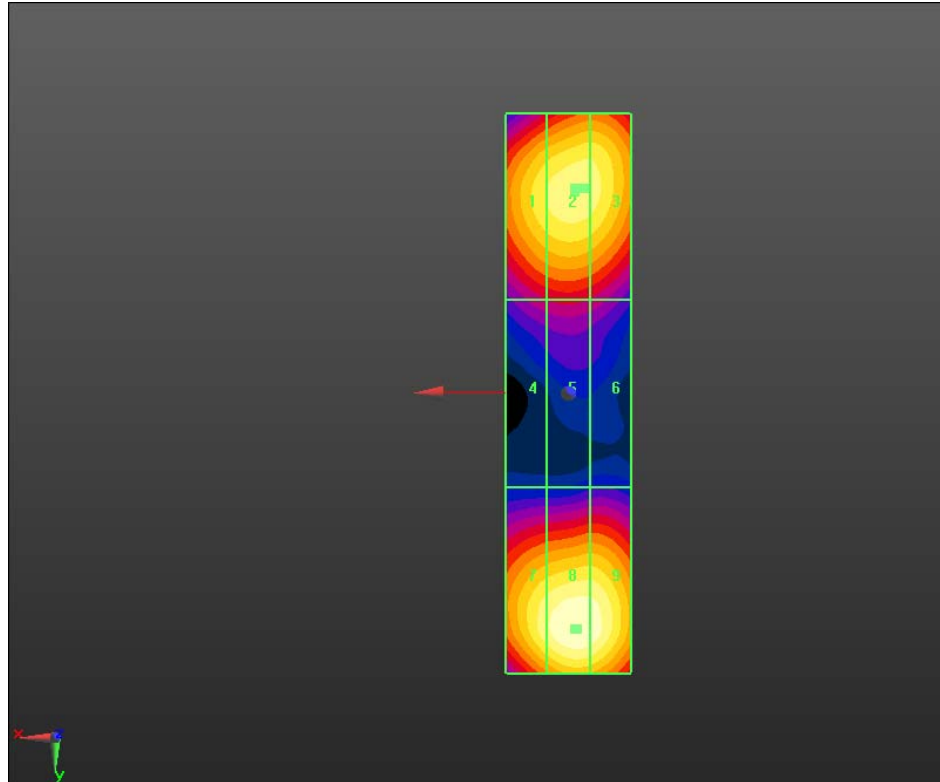
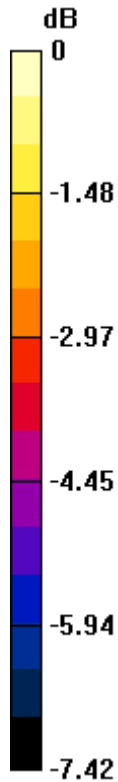
Location: -1, 38, 4.7 mm

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW



0 dB = 42.430V/m = 32.55 dB V/m

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Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_CDMA1880 MHz_02_29_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CDMA 1900, Communication System: CDMA 1900 1/8th,

Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- DASYS 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - CDMA FR 1880_PMF/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 87.80 V/m; Power Drift = 0.04 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 80.60 V/m

Near-field category: M3 (AWF 0 dB)

		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 46 (158)
Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW	

PMF scaled E-field

Grid 1 M3 73.45 V/m	Grid 2 M3 76.11 V/m	Grid 3 M3 74.97 V/m
Grid 4 M4 50.62 V/m	Grid 5 M4 51.75 V/m	Grid 6 M4 50.16 V/m
Grid 7 M3 76.91 V/m	Grid 8 M3 80.60 V/m	Grid 9 M3 78.58 V/m

Cursor:

Total = 80.601 V/m

E Category: M3

Location: -0.5, 37.5, 4.7 mm

Dipole E-Field measurement/E Scan - CDMA 1/8th 1880_PMF 2/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 30.81 V/m; Power Drift = 0.09 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 30.61 V/m

Near-field category: **M4 (AWF 0 dB)**

PMF scaled E-field

Grid 1 M4 28.31 V/m	Grid 2 M4 30.22 V/m	Grid 3 M4 28.54 V/m
Grid 4 M4 18.23 V/m	Grid 5 M4 20.72 V/m	Grid 6 M4 18.32 V/m
Grid 7 M4 26.79 V/m	Grid 8 M4 30.61 V/m	Grid 9 M4 30.61 V/m

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Cursor:

Total = 30.614 V/m

E Category: M4

Location: -3.5, 36, 4.7 mm

Dipole E-Field measurement/E Scan- CW 1880_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 90.26 V/m; Power Drift = -0.02 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 81.58 V/m

Near-field category: M3 (AWF 0 dB)

PMF scaled E-field

Grid 1 M3 75.79 V/m	Grid 2 M3 78.08 V/m	Grid 3 M3 77.27 V/m
Grid 4 M4 52.44 V/m	Grid 5 M4 53.31 V/m	Grid 6 M4 51.71 V/m
Grid 7 M3 78.00 V/m	Grid 8 M3 81.58 V/m	Grid 9 M3 79.79 V/m

Cursor:

Total = 81.580 V/m

E Category: M3

Location: -0.5, 37.5, 4.7 mm

Dipole E-Field measurement/E Scan - AM80%_ 1880_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 56.79 V/m; Power Drift = 0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 52.04 V/m

Near-field category: M4 (AWF 0 dB)

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PMF scaled E-field

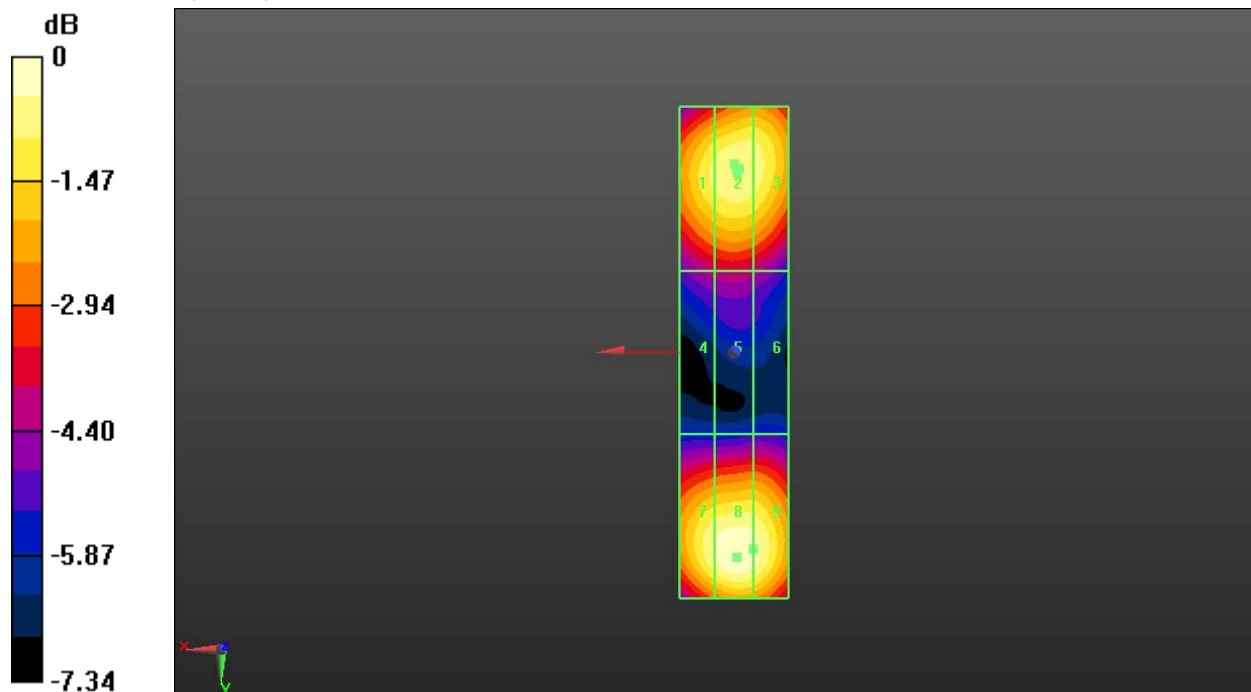
Grid 1 M4 47.54 V/m	Grid 2 M4 49.44 V/m	Grid 3 M4 48.95 V/m
Grid 4 M4 33.05 V/m	Grid 5 M4 33.87 V/m	Grid 6 M4 32.89 V/m
Grid 7 M4 49.67 V/m	Grid 8 M4 52.04 V/m	Grid 9 M4 50.92 V/m

Cursor:

Total = 52.041 V/m

E Category: M4

Location: -0.5, 37.5, 4.7 mm



0 dB = 80.600V/m = 38.13 dB V/m

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Date/Time: 4/24/2013 4:14:18 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_validation_835 MHz_04_24_13

DUT: HAC-Dipole 835 MHz; Type: CD835V3; Serial: 1011

Communication System: CW; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Dipole H-Field measurement with H3DV6 probe/H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid

Compatibility Test (41x181x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.5000 A/m; Power Drift = -0.04 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.4745 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.416 A/m	Grid 2 M4 0.459 A/m	Grid 3 M4 0.452 A/m
Grid 4 M4 0.431 A/m	Grid 5 M4 0.474 A/m	Grid 6 M4 0.465 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW

0.425 A/m

0.462 A/m

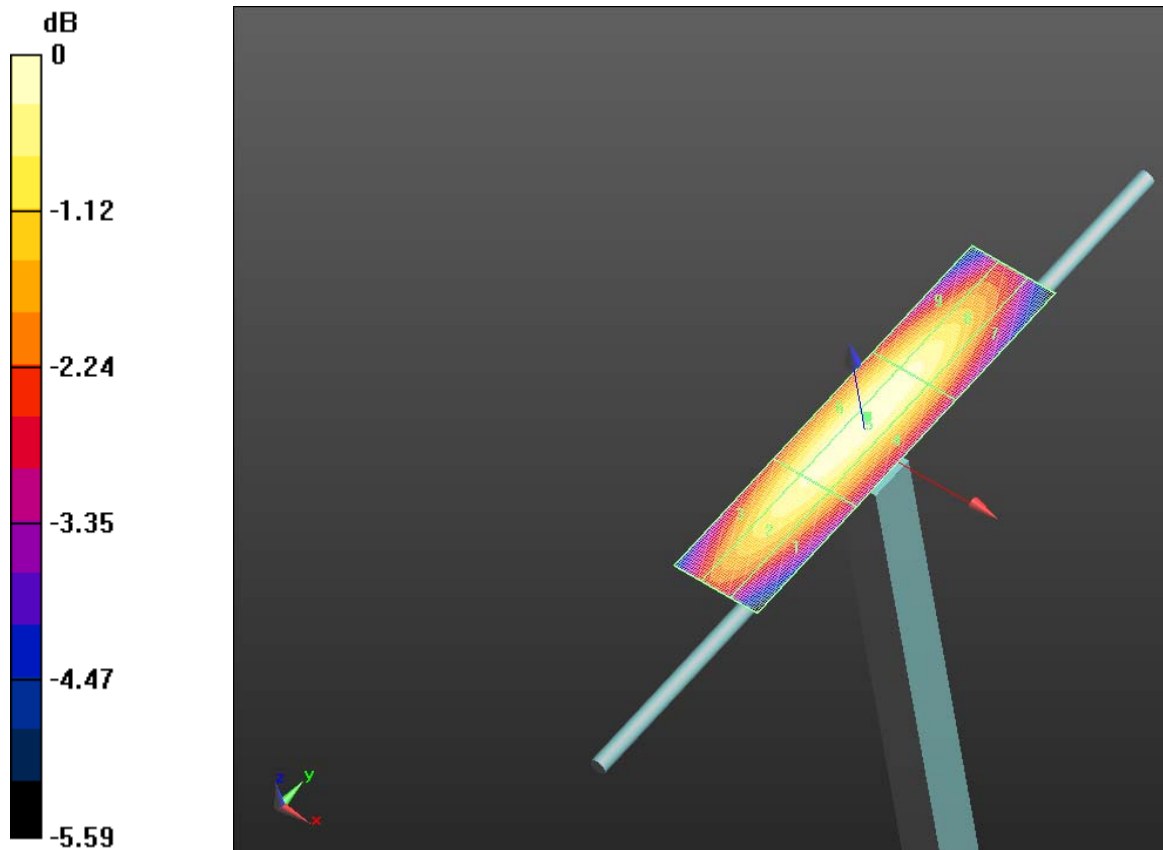
0.449 A/m

Cursor:

Total = 0.4744 A/m

H Category: M4

Location: -1.5, 2.5, 4.7 mm



0 dB = 0.4744 A/m = -6.48 dBA/m

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Date/Time: 6/28/2012 11:48:13 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_GSM835 MHz_06_28_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: GSM 835_PMF, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - GSM

835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.17 V/m; Power Drift = -0.01 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.16 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.15 A/m	Grid 2 M4 0.16 A/m	Grid 3 M4 0.15 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4

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Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW

0.16 A/m	0.16 A/m	0.16 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.15 A/m	0.16 A/m	0.15 A/m

Cursor:

Total = 0.163 A/m

H Category: M4

Location: 0, 8.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW

835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid:

dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.28 V/m; Power Drift = 0.08 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.47 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.44 A/m	0.46 A/m	0.44 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.45 A/m	0.47 A/m	0.45 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.45 A/m	0.47 A/m	0.44 A/m

Cursor:

Total = 0.471 A/m

H Category: M4

Location: 0, 8, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan -

AM80%_PMF/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.32 V/m; Power Drift = 0.12 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.30 A/m

Near-field category: M4 (AWF 0 dB)

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

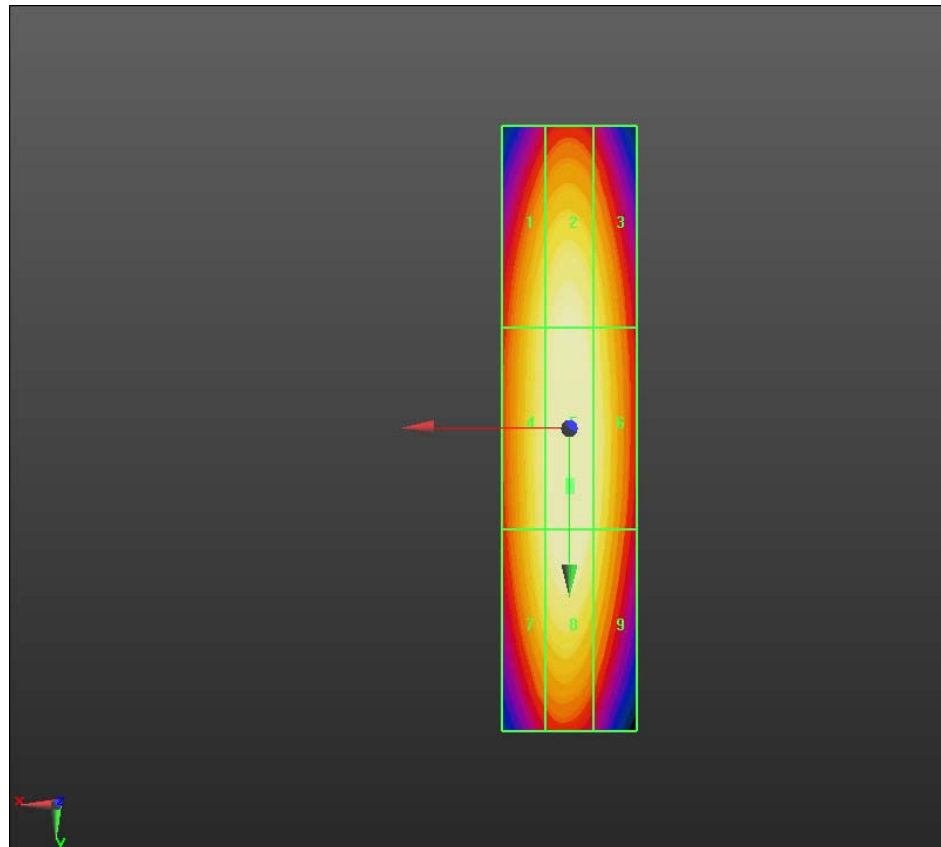
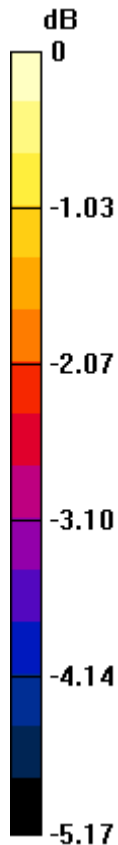
Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW

PMF scaled H-field

Grid 1 M4 0.28 A/m	Grid 2 M4 0.29 A/m	Grid 3 M4 0.28 A/m
Grid 4 M4 0.29 A/m	Grid 5 M4 0.30 A/m	Grid 6 M4 0.29 A/m
Grid 7 M4 0.29 A/m	Grid 8 M4 0.30 A/m	Grid 9 M4 0.28 A/m

Cursor:
 Total = 0.304 A/m
 H Category: M4
 Location: 0, 9, 4.7 mm



0 dB = 0.160A/m = -15.92 dB A/m

		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 54 (158)
Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW	

Date/Time: 2/17/2012 4:08:25 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_UMTS835 MHz_02_17_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: WCDMA FDD V, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - UMTS

835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.19 V/m; Power Drift = 0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.18 A/m

Near-field category: M4 (AWF 0 dB)

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Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW	

PMF scaled H-field

Grid 1 M4 0.16 A/m	Grid 2 M4 0.17 A/m	Grid 3 M4 0.16 A/m
Grid 4 M4 0.17 A/m	Grid 5 M4 0.18 A/m	Grid 6 M4 0.17 A/m
Grid 7 M4 0.17 A/m	Grid 8 M4 0.18 A/m	Grid 9 M4 0.17 A/m

Cursor:

Total = 0.181 A/m

H Category: M4

Location: 0.5, 8.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW

835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid:

dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.11 V/m; Power Drift = 0.08 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.20 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.17 A/m	Grid 2 M4 0.19 A/m	Grid 3 M4 0.18 A/m
Grid 4 M4 0.18 A/m	Grid 5 M4 0.20 A/m	Grid 6 M4 0.19 A/m
Grid 7 M4 0.18 A/m	Grid 8 M4 0.19 A/m	Grid 9 M4 0.18 A/m

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Cursor:

Total = 0.197 A/m

H Category: M4

Location: -0.5, 1, 4.7 mm

**Dipole H-Field measurement with H3DV6 probe/H Scan -
AM80%_PMF/Hearing Aid Compatibility Test (41x181x1):**

Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.14 V/m; Power Drift = 0.10 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.13 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.11 A/m	Grid 2 M4 0.12 A/m	Grid 3 M4 0.12 A/m
Grid 4 M4 0.12 A/m	Grid 5 M4 0.13 A/m	Grid 6 M4 0.12 A/m
Grid 7 M4 0.12 A/m	Grid 8 M4 0.12 A/m	Grid 9 M4 0.12 A/m

Cursor:

Total = 0.127 A/m

H Category: M4

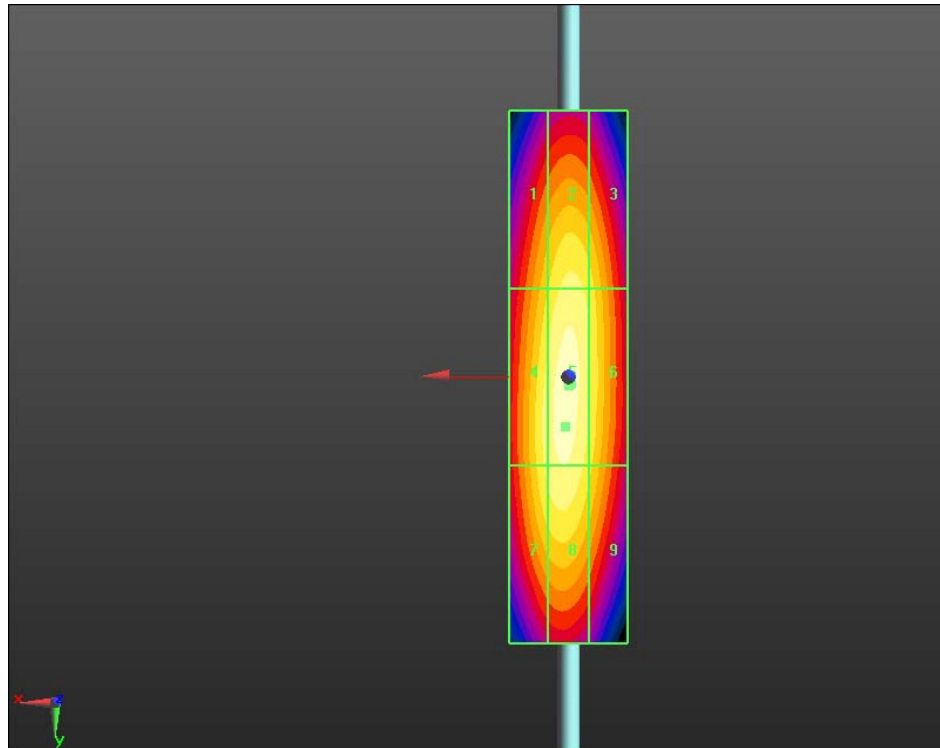
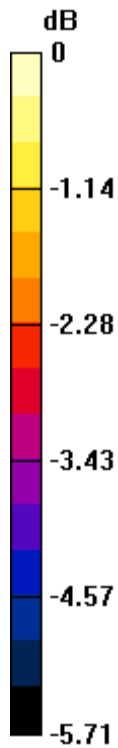
Location: 0, 1.5, 4.7 mm

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW



0 dB = 0.180A/m = -14.89 dB A/m

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Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW	

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_CDMA835 MHz_02_29_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: CDMA 850, Communication System: CDMA 850 1/8th,

Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - CDMA FR

835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid:

dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.37 V/m; Power Drift = 0.11 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.34 A/m

Near-field category: M4 (AWF 0 dB)

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PMF scaled H-field

Grid 1 M4 0.32 A/m	Grid 2 M4 0.33 A/m	Grid 3 M4 0.32 A/m
Grid 4 M4 0.33 A/m	Grid 5 M4 0.34 A/m	Grid 6 M4 0.33 A/m
Grid 7 M4 0.32 A/m	Grid 8 M4 0.34 A/m	Grid 9 M4 0.32 A/m

Cursor:

Total = 0.344 A/m

H Category: M4

Location: 0, 1.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CDMA 1/8th

835_PMF 2/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.13 V/m; Power Drift = 0.09 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.13 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.12 A/m	Grid 2 M4 0.12 A/m	Grid 3 M4 0.12 A/m
Grid 4 M4 0.13 A/m	Grid 5 M4 0.13 A/m	Grid 6 M4 0.12 A/m
Grid 7 M4 0.12 A/m	Grid 8 M4 0.13 A/m	Grid 9 M4 0.12 A/m

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Cursor:

Total = 0.134 A/m

H Category: M4

Location: 0, 0, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW

835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.39 V/m; Power Drift = 0.08 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.35 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.32 A/m	Grid 2 M4 0.34 A/m	Grid 3 M4 0.32 A/m
Grid 4 M4 0.34 A/m	Grid 5 M4 0.35 A/m	Grid 6 M4 0.33 A/m
Grid 7 M4 0.33 A/m	Grid 8 M4 0.35 A/m	Grid 9 M4 0.33 A/m

Cursor:

Total = 0.355 A/m

H Category: M4

Location: 0, 5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan -

AM80%_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.24 V/m; Power Drift = -0.02 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.23 A/m

Near-field category: M4 (AWF 0 dB)

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PMF scaled H-field

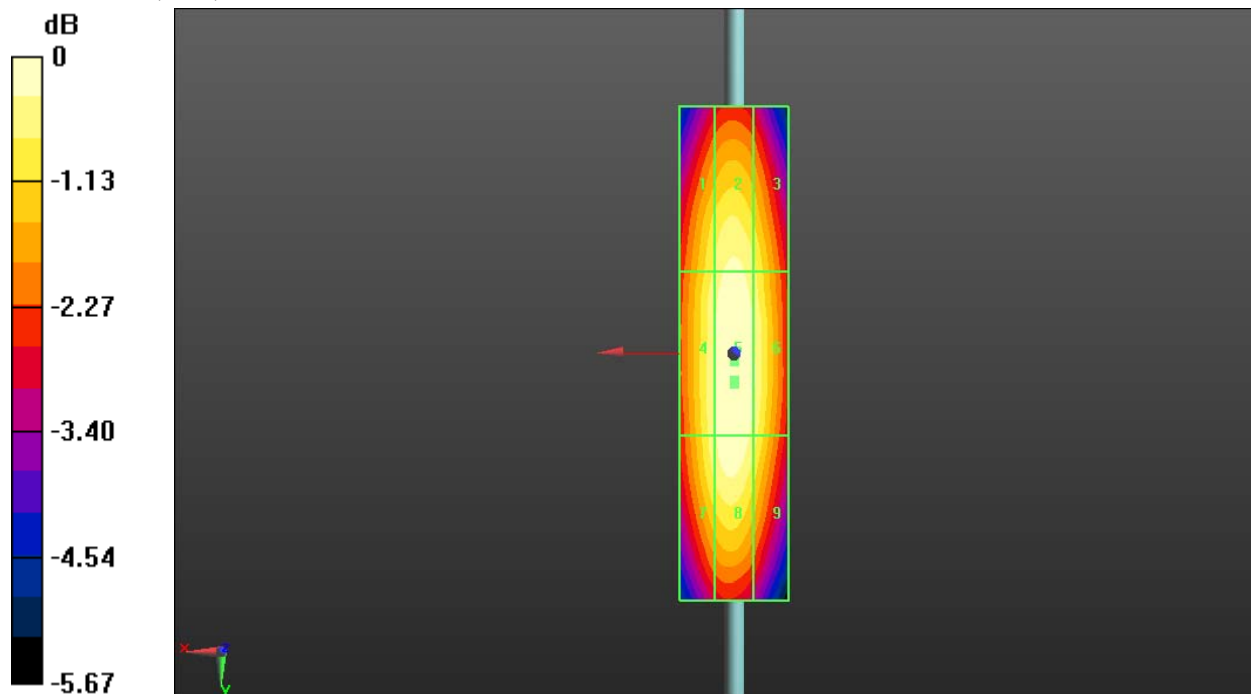
Grid 1 M4 0.20 A/m	Grid 2 M4 0.21 A/m	Grid 3 M4 0.20 A/m
Grid 4 M4 0.21 A/m	Grid 5 M4 0.23 A/m	Grid 6 M4 0.22 A/m
Grid 7 M4 0.21 A/m	Grid 8 M4 0.22 A/m	Grid 9 M4 0.21 A/m

Cursor:

Total = 0.227 A/m

H Category: M4

Location: 0, 5.5, 4.7 mm



0 dB = 0.340A/m = -9.37 dB A/m

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Date/Time: 4/24/2013 4:30:53 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_validation_1880 MHz_04_24_13

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CW; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Dipole H-Field measurement with H3DV6 probe/H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid

Compatibility Test (41x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.5110 A/m; Power Drift = -0.06 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.4847 A/m

Near-field category: M2 (AWF 0 dB)

PMF scaled H-field

Grid 1 M2 0.427 A/m	Grid 2 M2 0.473 A/m	Grid 3 M2 0.467 A/m
Grid 4 M2 0.438 A/m	Grid 5 M2 0.485 A/m	Grid 6 M2 0.479 A/m
Grid 7 M2	Grid 8 M2	Grid 9 M2

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Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW

0.427 A/m

0.470 A/m

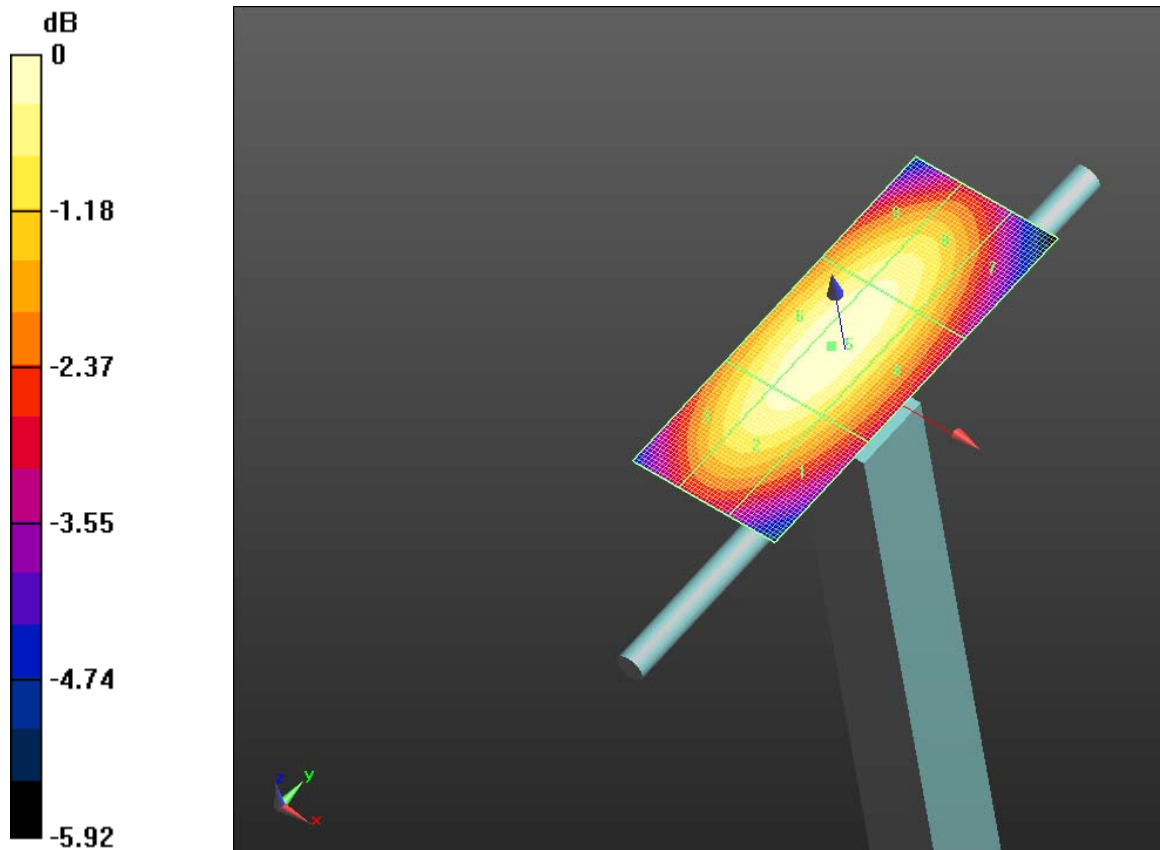
0.463 A/m

Cursor:

Total = 0.4847 A/m

H Category: M2

Location: -1.5, -0.5, 4.7 mm



0 dB = 0.4847 A/m = -6.29 dBA/m

		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 64 (158)
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Date/Time: 6/28/2012 12:25:06 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_GSM1880 MHz_06_28_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: GSM 1880_PMF, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan -GSM

1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.11 V/m; Power Drift = -0.01 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.11 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.10 A/m	Grid 2 M4 0.10 A/m	Grid 3 M4 0.10 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4

		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 65 (158)
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0.10 A/m	0.11 A/m	0.10 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.10 A/m	0.10 A/m	0.10 A/m

Cursor:

Total = 0.105 A/m

H Category: M4

Location: 0, 0.5, 4.7 mm

**Dipole H-Field measurement with H3DV6 probe/H Scan - CW
1800_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement**

grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.32 V/m; Power Drift = 0.00 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.30 A/m

Near-field category: M3 (AWF 0 dB)

PMF scaled H-field

Grid 1 M3 0.28 A/m	Grid 2 M3 0.29 A/m	Grid 3 M3 0.28 A/m
Grid 4 M3 0.29 A/m	Grid 5 M3 0.30 A/m	Grid 6 M3 0.29 A/m
Grid 7 M3 0.28 A/m	Grid 8 M3 0.29 A/m	Grid 9 M3 0.28 A/m

Cursor:

Total = 0.300 A/m

H Category: M3

Location: 0, 1, 4.7 mm

**Dipole H-Field measurement with H3DV6 probe/H Scan -
AM80%_1880_PMF/Hearing Aid Compatibility Test (41x101x1):**

Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.21 V/m; Power Drift = 0.02 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.19 A/m

Near-field category: M3 (AWF 0 dB)

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW

PMF scaled H-field

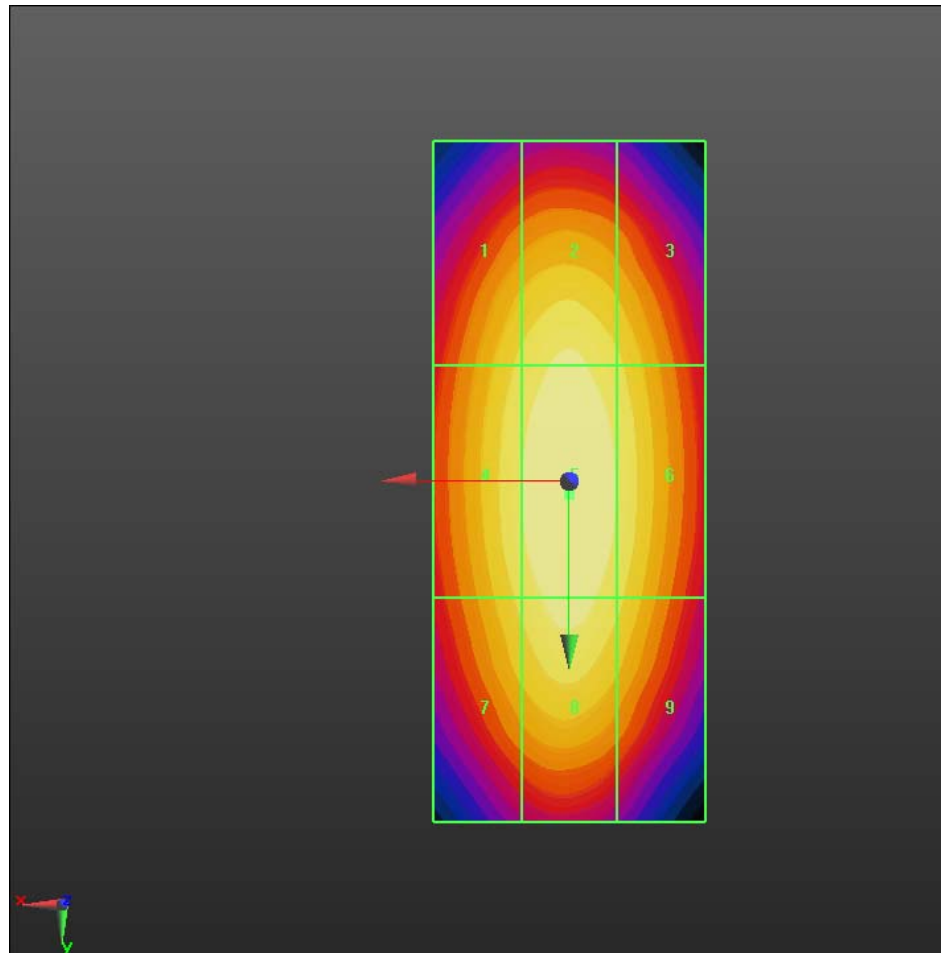
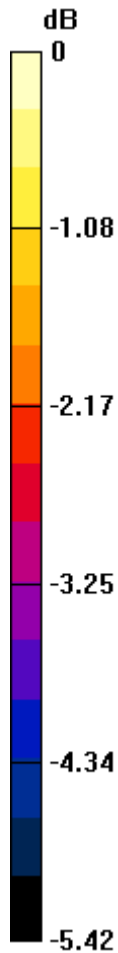
Grid 1 M4 0.18 A/m	Grid 2 M4 0.19 A/m	Grid 3 M4 0.18 A/m
Grid 4 M4 0.19 A/m	Grid 5 M3 0.19 A/m	Grid 6 M4 0.19 A/m
Grid 7 M4 0.18 A/m	Grid 8 M3 0.19 A/m	Grid 9 M4 0.18 A/m

Cursor:

Total = 0.194 A/m

H Category: M3

Location: 0, 0.5, 4.7 mm



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		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		67 (158)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Feb. 17-29, June 28, 2012 April 24-26, 2013	RTS-6026-1304-52	L6ARFQ110LW	

$$0 \text{ dB} = 0.110 \text{ A/m} = -19.17 \text{ dB A/m}$$

Date/Time: 2/17/2012 3:56:44 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_UMTS1880 MHz_02_17_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: WCDMA FDD II, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan -UMTS

1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid: $dx=5\text{mm}$, $dy=5\text{mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.16 V/m; Power Drift = 0.06 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.15 A/m

Near-field category: M4 (AWF 0 dB)

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PMF scaled H-field

Grid 1 M4 0.14 A/m	Grid 2 M4 0.14 A/m	Grid 3 M4 0.14 A/m
Grid 4 M4 0.14 A/m	Grid 5 M4 0.15 A/m	Grid 6 M4 0.14 A/m
Grid 7 M4 0.14 A/m	Grid 8 M4 0.15 A/m	Grid 9 M4 0.14 A/m

Cursor:

Total = 0.150 A/m

H Category: M4

Location: 0, 0.5, 4.7 mm

**Dipole H-Field measurement with H3DV6 probe/H Scan - CW
1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement**

grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.16 V/m; Power Drift = -0.01 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.15 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.14 A/m	Grid 2 M4 0.14 A/m	Grid 3 M4 0.14 A/m
Grid 4 M4 0.14 A/m	Grid 5 M4 0.15 A/m	Grid 6 M4 0.14 A/m
Grid 7 M4 0.14 A/m	Grid 8 M4 0.15 A/m	Grid 9 M4 0.14 A/m

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Cursor:

Total = 0.149 A/m

H Category: M4

Location: 0, 0.5, 4.7 mm

**Dipole H-Field measurement with H3DV6 probe/H Scan -
AM80%_1880_PMF/Hearing Aid Compatibility Test (41x101x1):**

Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.10 V/m; Power Drift = -0.07 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.10 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.09 A/m	Grid 2 M4 0.09 A/m	Grid 3 M4 0.09 A/m
Grid 4 M4 0.09 A/m	Grid 5 M4 0.10 A/m	Grid 6 M4 0.09 A/m
Grid 7 M4 0.09 A/m	Grid 8 M4 0.09 A/m	Grid 9 M4 0.09 A/m

Cursor:

Total = 0.096 A/m

H Category: M4

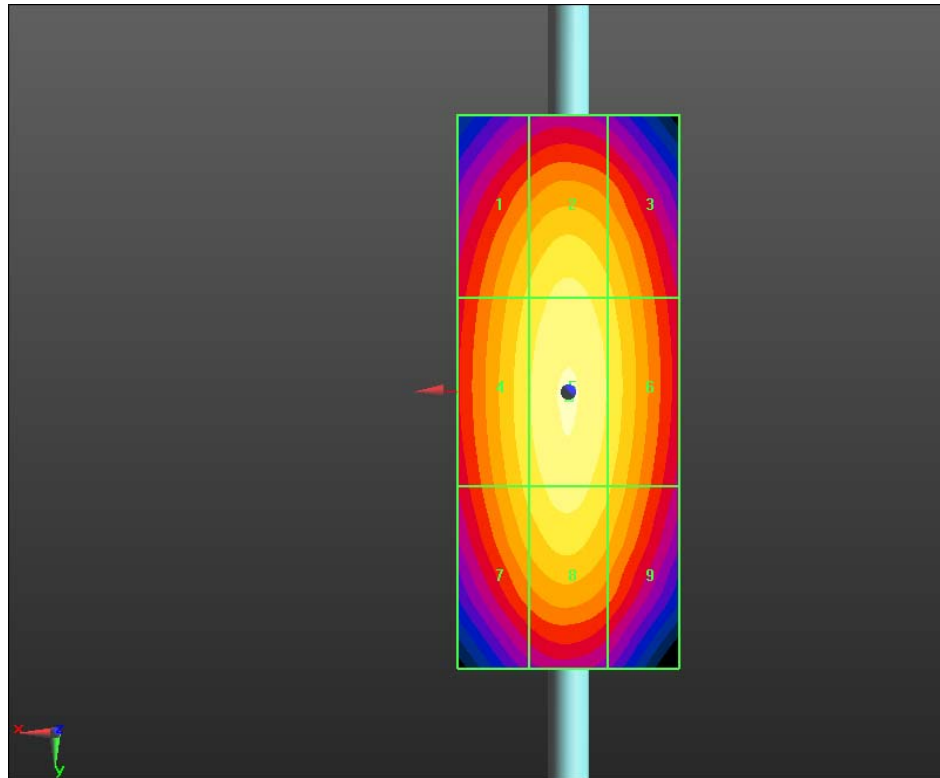
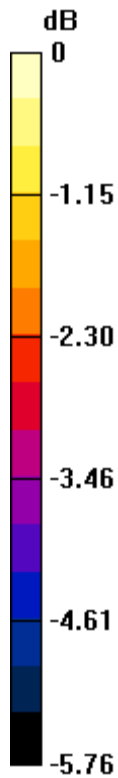
Location: 0, 0, 4.7 mm

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW



0 dB = 0.150A/m = -16.48 dB A/m

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Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_CDMA1880 MHz_02_29_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CDMA 1900, Communication System: CDMA 1900 1/8th,

Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), $z = 4.7$
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan -CDMA FR

1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid:

$dx=5\text{mm}$, $dy=5\text{mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.31 V/m; Power Drift = -0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.29 A/m

Near-field category: M3 (AWF 0 dB)

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PMF scaled H-field

Grid 1 M3 0.27 A/m	Grid 2 M3 0.28 A/m	Grid 3 M3 0.27 A/m
Grid 4 M3 0.28 A/m	Grid 5 M3 0.29 A/m	Grid 6 M3 0.28 A/m
Grid 7 M3 0.27 A/m	Grid 8 M3 0.28 A/m	Grid 9 M3 0.27 A/m

Cursor:

Total = 0.293 A/m

H Category: M3

Location: 0, -0.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan -CDMA 1/8th

1880_PMF 2/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.12 V/m; Power Drift = -0.90 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.11 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.10 A/m	Grid 2 M4 0.10 A/m	Grid 3 M4 0.09 A/m
Grid 4 M4 0.10 A/m	Grid 5 M4 0.11 A/m	Grid 6 M4 0.10 A/m
Grid 7 M4 0.09 A/m	Grid 8 M4 0.11 A/m	Grid 9 M4 0.09 A/m

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Cursor:

Total = 0.111 A/m

H Category: M4

Location: 0, 0, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW

1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.31 V/m; Power Drift = -0.01 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.29 A/m

Near-field category: M3 (AWF 0 dB)

PMF scaled H-field

Grid 1 M3 0.27 A/m	Grid 2 M3 0.28 A/m	Grid 3 M3 0.27 A/m
Grid 4 M3 0.28 A/m	Grid 5 M3 0.29 A/m	Grid 6 M3 0.28 A/m
Grid 7 M3 0.27 A/m	Grid 8 M3 0.28 A/m	Grid 9 M3 0.26 A/m

Cursor:

Total = 0.289 A/m

H Category: M3

Location: 0, 0, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan -

AM80%_1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.20 V/m; Power Drift = 0.04 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.19 A/m

Near-field category: M4 (AWF 0 dB)

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PMF scaled H-field

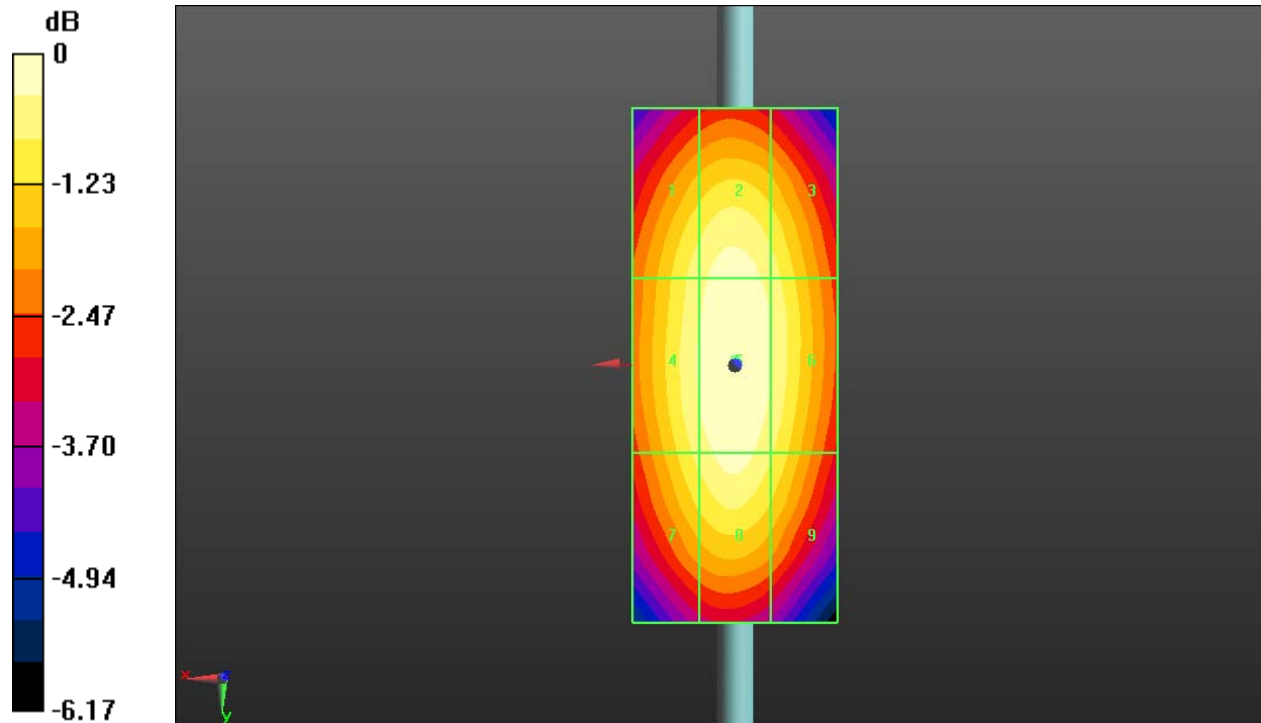
Grid 1 M4 0.17 A/m	Grid 2 M4 0.18 A/m	Grid 3 M4 0.17 A/m
Grid 4 M4 0.18 A/m	Grid 5 M4 0.19 A/m	Grid 6 M4 0.18 A/m
Grid 7 M4 0.17 A/m	Grid 8 M4 0.18 A/m	Grid 9 M4 0.17 A/m

Cursor:

Total = 0.187 A/m

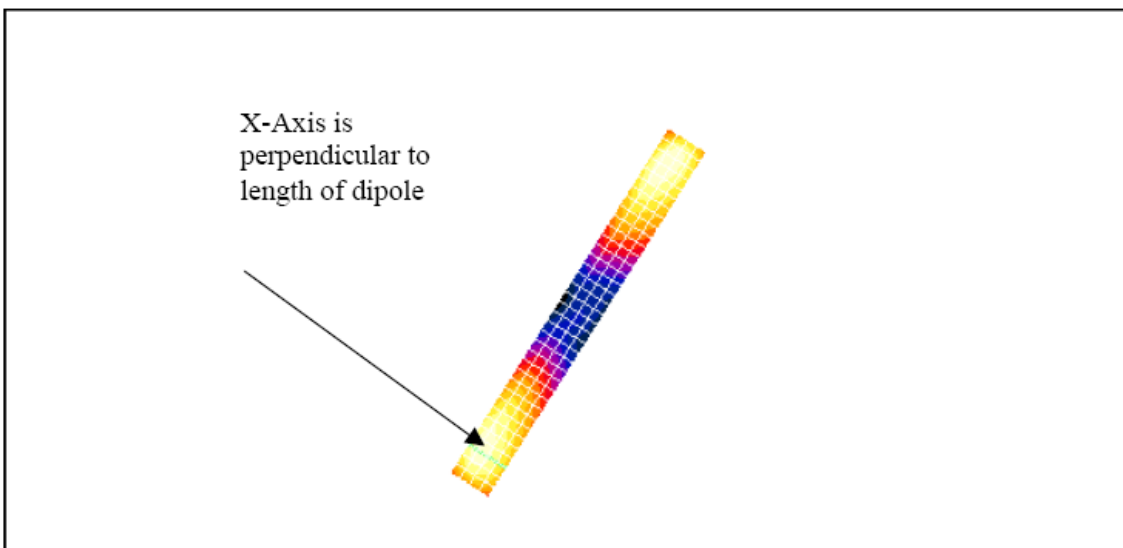
H Category: M4

Location: 0, 0, 4.7 mm



0 dB = 0.290A/m = -10.75 dB A/m

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The green line in this figure shows the axis along which the points lie.

Comparison of 5mm and 2mm step sizes

An additional set of measurements was taken: dipole validations were performed using 5mm and 2mm step sizes. The delta between the two readings is insignificant for both field types ($< 0.4\%$ for E and 0% for H), demonstrating that 5mm is sufficient. The plots follow.

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Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1
Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³
Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface) Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):

Measurement grid: dx=5mm, dy=5mm
Maximum value of Total (measured) = 134.8 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm
Maximum value of Total field (slot averaged) = 131.0 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

E in V/m (Time averaged) E in V/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
123.2	138.1	138.4	123.2	138.1	138.4
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
80.9	92.3	92.2	80.9	92.3	92.2
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
119.8	131.0	130.7	119.8	131.0	130.7

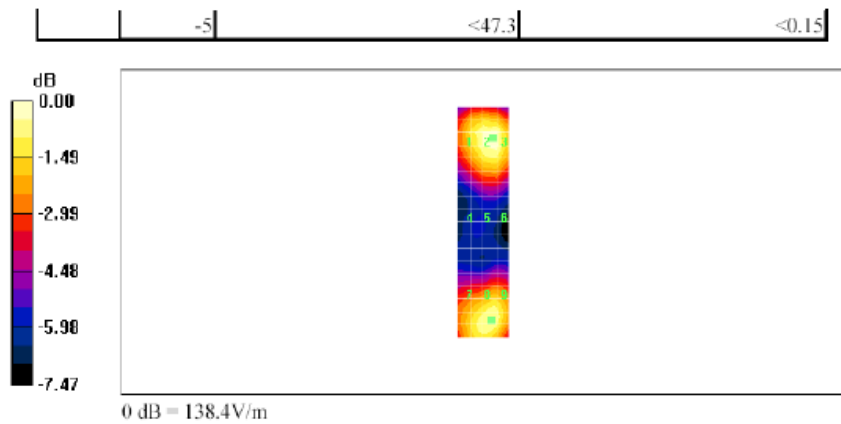
Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_2mm step_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1
Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³
Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface) Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):

Measurement grid: dx=2mm, dy=2mm
Maximum value of Total (measured) = 138.0 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Measurement grid: dx=2mm, dy=2mm
Maximum value of Total field (slot averaged) = 131.2 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

E in V/m (Time averaged) E in V/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
123.1	138.6	138.6	123.1	138.6	138.6
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
81.4	92.1	91.6	81.4	92.1	91.6
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
121.3	131.2	131.0	121.3	131.2	131.0

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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Author Data

Daoud Attayi

Dates of Test

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Lab: RIM Testing Services (RTS)**HAC_H_Dipole_CW 1880_5 mm step_07_14_05****DUT: HAC Dipole 1880 MHz; Type: CD1880V3**

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/12/2004

- Sensor-Surface: 0mm (Fix Surface) Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/01/2005

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of Total field (slot averaged) = 0.406 A/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged) H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
0.342	0.359	0.344	0.342	0.359	0.344
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
0.389	0.406	0.389	0.389	0.406	0.389
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
0.363	0.378	0.363	0.363	0.378	0.363

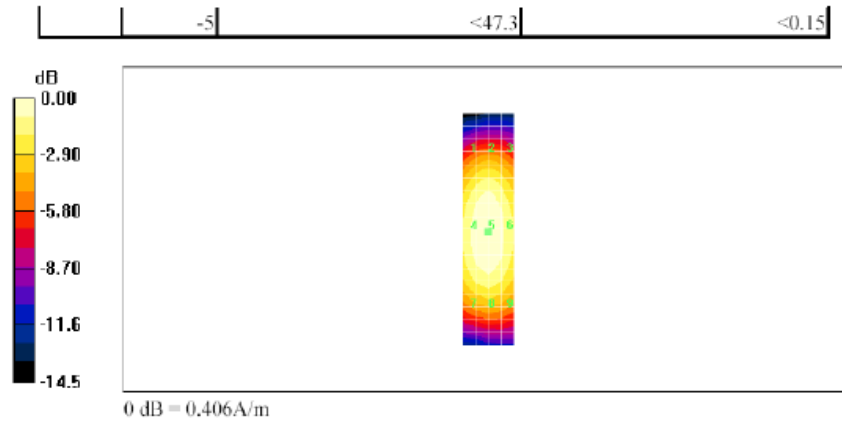
Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_2 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1
Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³
Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface) Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):

Measurement grid: dx=2mm, dy=2mm
Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Measurement grid: dx=2mm, dy=2mm
Maximum value of Total field (slot averaged) = 0.406 A/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged) H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
0.347	0.361	0.348	0.347	0.361	0.348
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
0.394	0.406	0.391	0.394	0.406	0.391
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
0.367	0.380	0.365	0.367	0.380	0.365

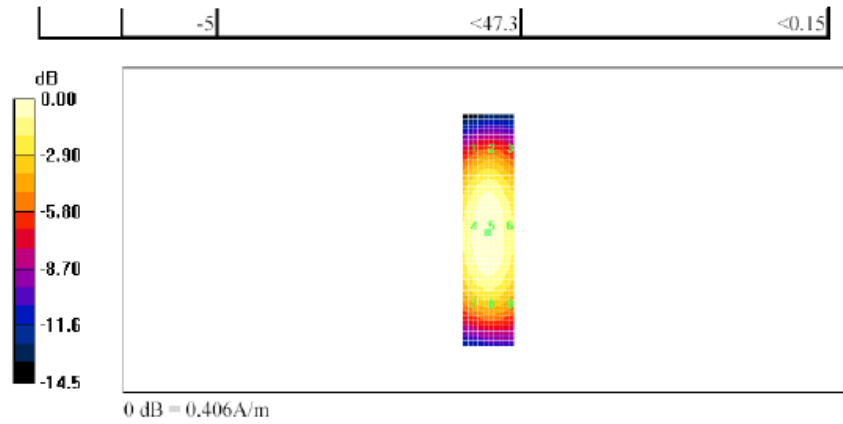
Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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A.3 RF emission field plots

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Date/Time: 4/26/2013 3:29:20 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM850

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 333CB445

Communication System: GSM 850; Frequency: 824.2 MHz, Frequency: 836.8 MHz, Frequency: 848.8 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 67.32 V/m; Power Drift = -0.09 dB

PMR not calibrated. PMF = 3.000 is applied.

E-field emissions = 174.1 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M4 144.3 V/m	Grid 2 M3 170.0 V/m	Grid 3 M3 170.2 V/m
Grid 4 M4 142.8 V/m	Grid 5 M3 174.1 V/m	Grid 6 M3 174.3 V/m

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Grid 7 M4 142.2 V/m	Grid 8 M3 171.3 V/m	Grid 9 M3 171.4 V/m
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Cursor:

Total = 174.3 V/m

E Category: M3

Location: -9, 0.5, 8.7 mm

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007:
15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid**

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 73.61 V/m; Power Drift = 0.01 dB

PMR not calibrated. PMF = 3.000 is applied.

E-field emissions = 196.9 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M3 156.7 V/m	Grid 2 M3 192.3 V/m	Grid 3 M3 193.4 V/m
Grid 4 M3 153.9 V/m	Grid 5 M3 196.9 V/m	Grid 6 M3 197.7 V/m
Grid 7 M3 151.8 V/m	Grid 8 M3 193.9 V/m	Grid 9 M3 194.3 V/m

Cursor:

Total = 197.7 V/m

E Category: M3

Location: -10, 0.5, 8.7 mm

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007:
15 mm from Probe Center to the Device_High_Chan/Hearing Aid**

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 69.50 V/m; Power Drift = 0.04 dB

PMR not calibrated. PMF = 3.000 is applied.

E-field emissions = 187.2 V/m

Near-field category: M3 (AWF -5 dB)

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PMF scaled E-field

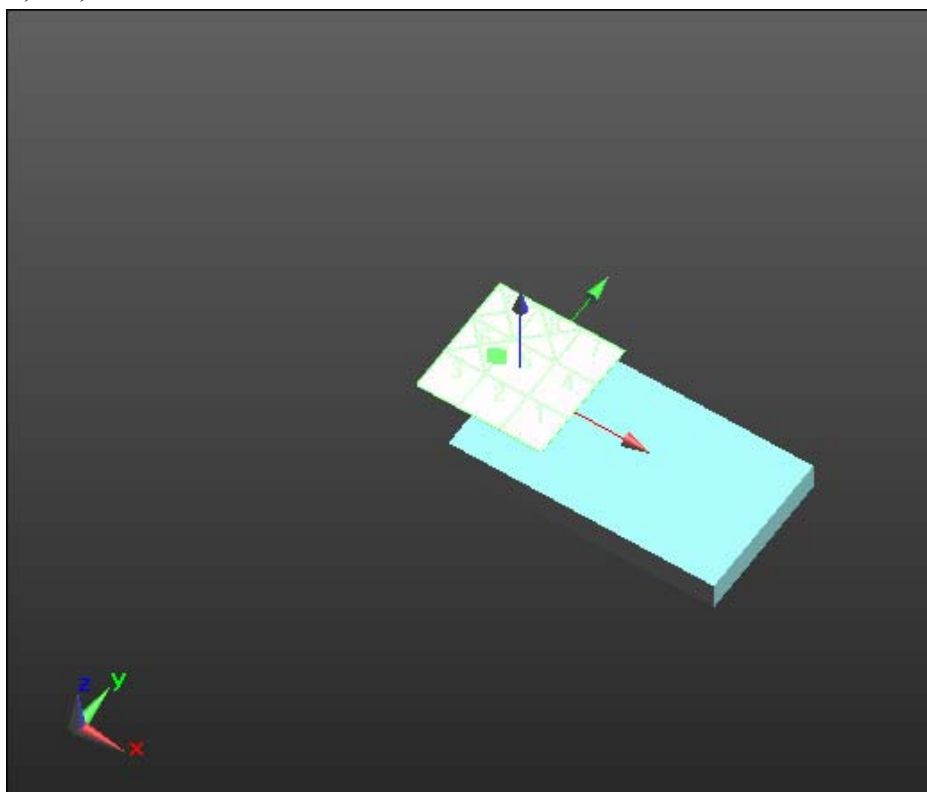
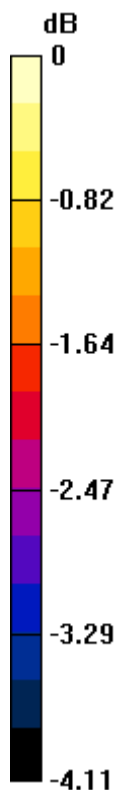
Grid 1 M4 149.4 V/m	Grid 2 M3 184.6 V/m	Grid 3 M3 185.4 V/m
Grid 4 M4 144.5 V/m	Grid 5 M3 187.2 V/m	Grid 6 M3 188.1 V/m
Grid 7 M4 139.0 V/m	Grid 8 M3 182.6 V/m	Grid 9 M3 183.2 V/m

Cursor:

Total = 188.1 V/m

E Category: M3

Location: -10, -0.5, 8.7 mm



0 dB = 167.4 V/m = 44.48 dBV/m

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Date/Time: 4/26/2013 3:54:49 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM850_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 333CB445

Communication System: GSM 850; Frequency: 836.8 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 73.03 V/m; Power Drift = -0.07 dB

PMR not calibrated. PMF = 3.000 is applied.

E-field emissions = 187.7 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M4 146.7 V/m	Grid 2 M3 182.7 V/m	Grid 3 M3 188.6 V/m
Grid 4 M4 142.4 V/m	Grid 5 M3 187.7 V/m	Grid 6 M3 194.2 V/m
Grid 7 M4 141.6 V/m	Grid 8 M3 187.6 V/m	Grid 9 M3 194.0 V/m

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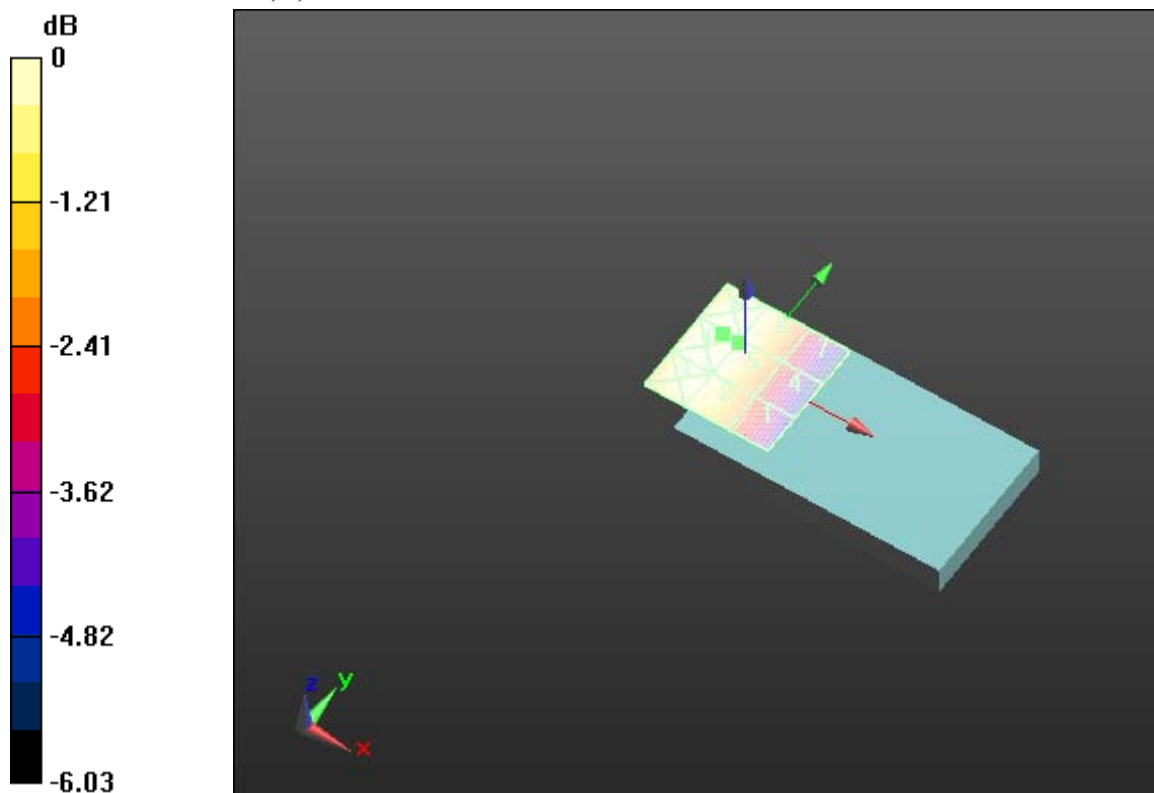
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Cursor:

Total = 194.2 V/m

E Category: M3

Location: -10.5, 2, 8.7 mm



0 dB = 186.5 V/m = 45.41 dBV/m

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Date/Time: 4/26/2013 5:29:13 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_Band_V

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 333CB445

Communication System: WCDMA FDD V; Frequency: 826.4 MHz, Frequency: 836.4 MHz,
Frequency: 846.6 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 64.33 V/m; Power Drift = 0.07 dB

PMR not calibrated. PMF = 1.070 is applied.

E-field emissions = 59.88 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 49.13 V/m	Grid 2 M4 58.38 V/m	Grid 3 M4 58.43 V/m
Grid 4 M4 49.02 V/m	Grid 5 M4 59.88 V/m	Grid 6 M4 59.94 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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48.81 V/m	58.97 V/m	59.00 V/m
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Cursor:

Total = 59.94 V/m

E Category: M4

Location: -9.5, 1, 8.7 mm

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007:
15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid**

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 80.62 V/m; Power Drift = 0.01 dB

PMR not calibrated. PMF = 1.070 is applied.

E-field emissions = 76.92 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 61.03 V/m	Grid 2 M4 75.11 V/m	Grid 3 M4 75.43 V/m
Grid 4 M4 60.36 V/m	Grid 5 M4 76.92 V/m	Grid 6 M4 77.21 V/m
Grid 7 M4 59.88 V/m	Grid 8 M4 75.85 V/m	Grid 9 M4 76.00 V/m

Cursor:

Total = 77.21 V/m

E Category: M4

Location: -10, 1.5, 8.7 mm

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007:
15 mm from Probe Center to the Device_High_Chan/Hearing Aid**

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 77.75 V/m; Power Drift = 0.14 dB

PMR not calibrated. PMF = 1.070 is applied.

E-field emissions = 74.61 V/m

Near-field category: M4 (AWF 0 dB)

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PMF scaled E-field

Grid 1 M4 61.15 V/m	Grid 2 M4 73.29 V/m	Grid 3 M4 73.67 V/m
Grid 4 M4 58.84 V/m	Grid 5 M4 74.61 V/m	Grid 6 M4 75.09 V/m
Grid 7 M4 56.67 V/m	Grid 8 M4 72.56 V/m	Grid 9 M4 72.90 V/m

Cursor:

Total = 75.09 V/m

E Category: M4

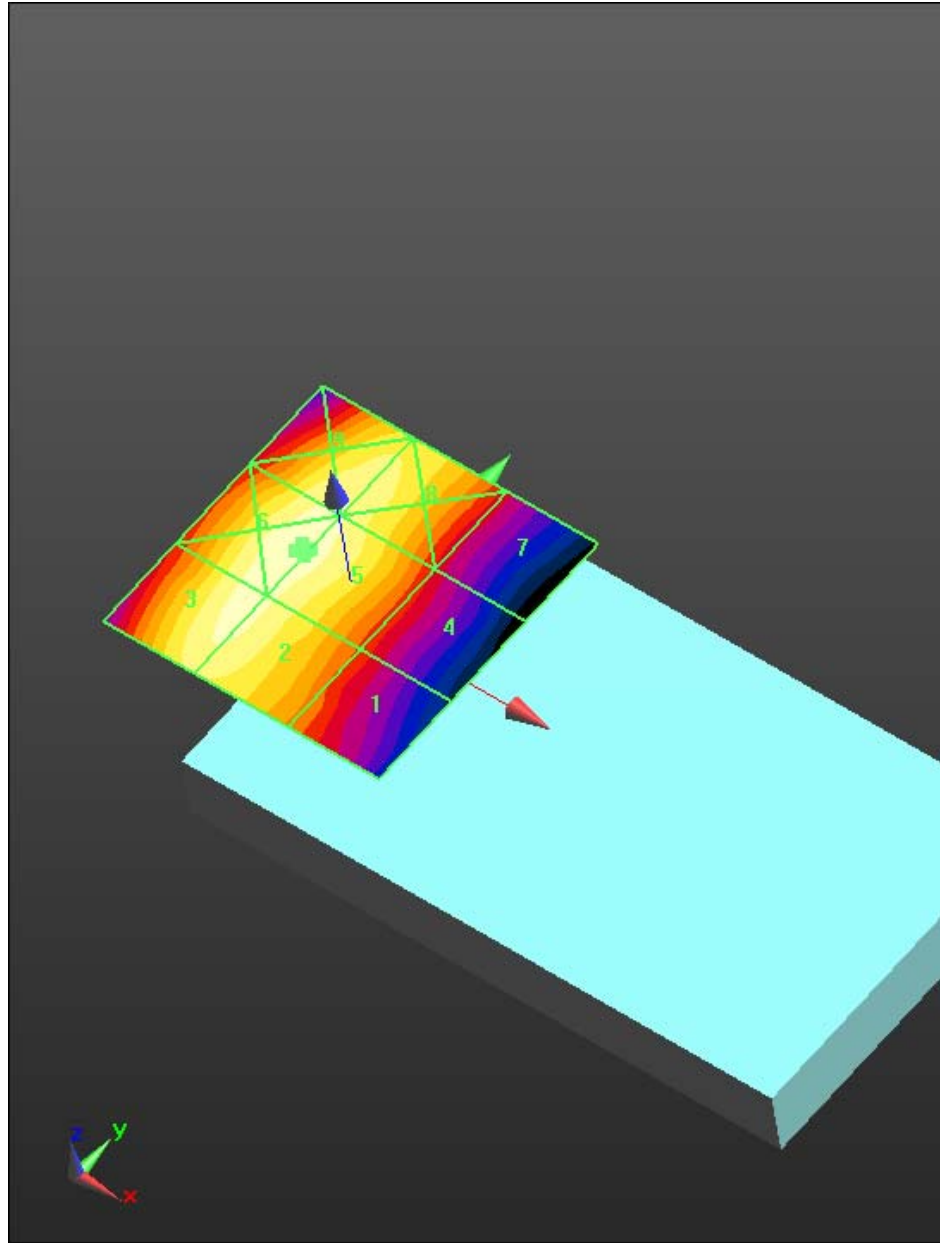
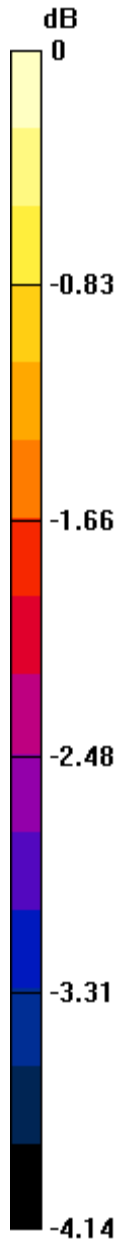
Location: -10, 0, 8.7 mm

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
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0 dB = 59.94 V/m = 35.55 dBV/m

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Date/Time: 4/26/2013 5:33:49 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_Band_V_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 333CB445

Communication System: WCDMA FDD V; Frequency: 836.4 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: **Not Specified**
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 80.99 V/m; Power Drift = 0.00 dB

PMR not calibrated. PMF = 1.070 is applied.

E-field emissions = 74.64 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 57.77 V/m	Grid 2 M4 72.23 V/m	Grid 3 M4 74.67 V/m
Grid 4 M4 56.45 V/m	Grid 5 M4 74.64 V/m	Grid 6 M4 77.59 V/m
Grid 7 M4 56.24 V/m	Grid 8 M4 74.55 V/m	Grid 9 M4 77.46 V/m

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Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

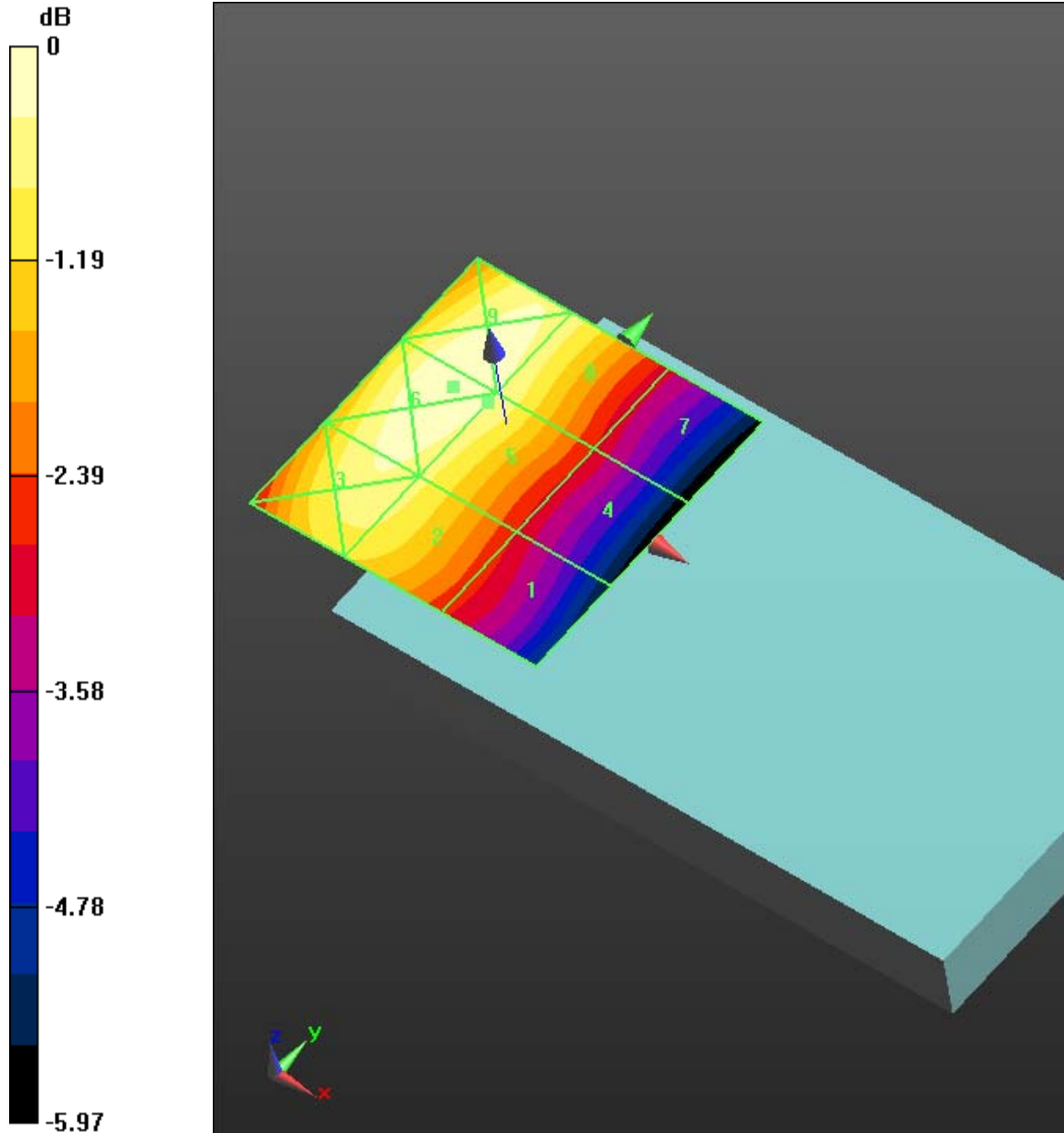
FCC ID
L6ARFQ110LW

Cursor:

Total = 77.59 V/m

E Category: M4

Location: -10, 1, 8.7 mm



0 dB = 77.59 V/m = 37.80 dBV/m

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Date/Time: 4/26/2013 4:05:12 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM1900

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 333CB445

Communication System: GSM 1900; Frequency: 1850.2 MHz, Frequency: 1880 MHz,
Frequency: 1909.8 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 11.05 V/m; Power Drift = 0.11 dB

PMR not calibrated. PMF = 2.850 is applied.

E-field emissions = 53.51 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M3 48.50 V/m	Grid 2 M3 53.51 V/m	Grid 3 M3 52.34 V/m
Grid 4 M4 30.61 V/m	Grid 5 M4 44.75 V/m	Grid 6 M4 45.14 V/m

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Grid 7 M3 55.63 V/m	Grid 8 M3 69.11 V/m	Grid 9 M3 68.44 V/m
--------------------------------------	--------------------------------------	--------------------------------------

Cursor:

Total = 69.11 V/m

E Category: M3

Location: -6, 25, 8.7 mm

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007:
15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid**

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 8.576 V/m; Power Drift = 0.15 dB

PMR not calibrated. PMF = 2.850 is applied.

E-field emissions = 54.98 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M3 49.69 V/m	Grid 2 M3 54.98 V/m	Grid 3 M3 54.48 V/m
Grid 4 M4 27.48 V/m	Grid 5 M4 42.90 V/m	Grid 6 M4 44.27 V/m
Grid 7 M3 54.60 V/m	Grid 8 M3 71.25 V/m	Grid 9 M3 71.00 V/m

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Cursor:

Total = 71.25 V/m

E Category: M3

Location: -7, 25, 8.7 mm

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007:
15 mm from Probe Center to the Device_High_Chan/Hearing Aid
Compatibility Test (101x101x1):** Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 7.786 V/m; Power Drift = 0.01 dB

PMR not calibrated. PMF = 2.850 is applied.

E-field emissions = 50.67 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M4 40.87 V/m	Grid 2 M3 50.67 V/m	Grid 3 M3 50.64 V/m
Grid 4 M4 22.34 V/m	Grid 5 M4 38.28 V/m	Grid 6 M4 39.79 V/m
Grid 7 M4 47.07 V/m	Grid 8 M3 64.14 V/m	Grid 9 M3 64.14 V/m

Cursor:

Total = 64.14 V/m

E Category: M3

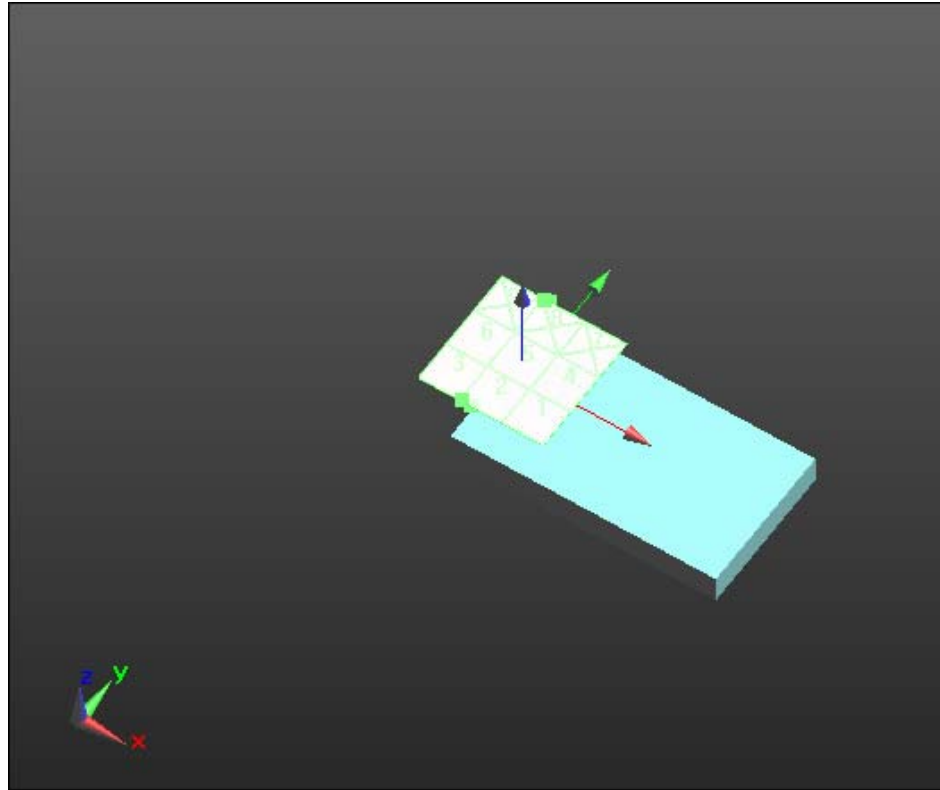
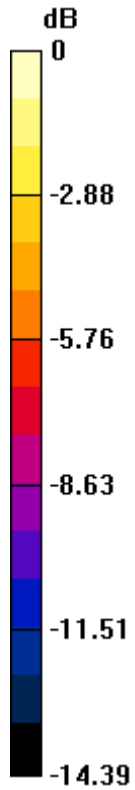
Location: -8, 25, 8.7 mm

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
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0 dB = 69.86 V/m = 36.88 dBV/m

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Date/Time: 4/26/2013 4:38:11 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM1900_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 333CB445

Communication System: GSM 1900; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 8.846 V/m; Power Drift = -0.09 dB

PMR not calibrated. PMF = 2.850 is applied.

E-field emissions = 57.92 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M3 50.67 V/m	Grid 2 M3 57.92 V/m	Grid 3 M3 57.92 V/m
Grid 4 M4 28.11 V/m	Grid 5 M4 36.67 V/m	Grid 6 M4 37.99 V/m
Grid 7 M4 38.79 V/m	Grid 8 M3 60.40 V/m	Grid 9 M3 61.69 V/m

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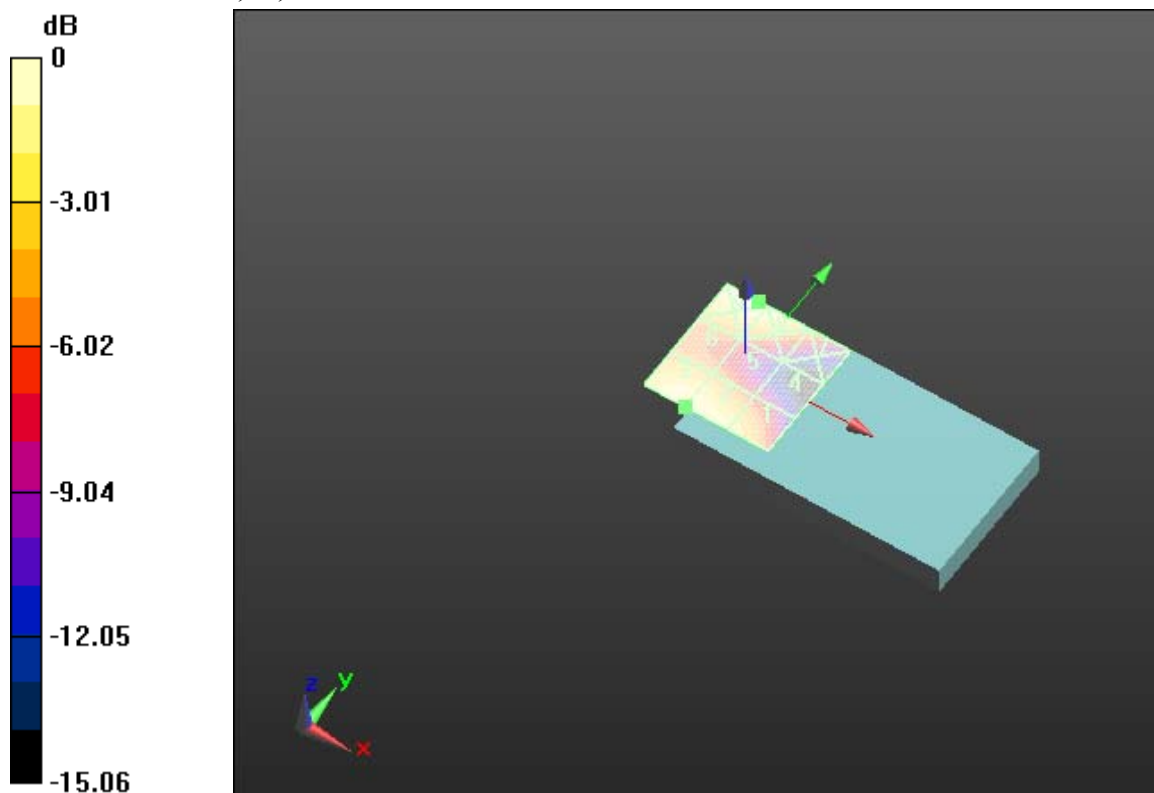
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Cursor:

Total = 61.69 V/m

E Category: M3

Location: -8, 20, 8.7 mm



0 dB = 62.36 V/m = 35.90 dBV/m

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Date/Time: 4/26/2013 4:56:24 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_Band_II

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 333CB445

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz, Frequency: 1880 MHz,
Frequency: 1907.6 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 16.55 V/m; Power Drift = 0.01 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 28.77 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 26.07 V/m	Grid 2 M4 28.77 V/m	Grid 3 M4 28.15 V/m
Grid 4 M4 16.74 V/m	Grid 5 M4 23.35 V/m	Grid 6 M4 23.61 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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29.16 V/m	35.61 V/m	35.44 V/m
------------------	------------------	------------------

Cursor:

Total = 35.61 V/m

E Category: M4

Location: -6, 25, 8.7 mm

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007:
15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid**

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 14.60 V/m; Power Drift = -0.15 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 28.01 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 24.97 V/m	Grid 2 M4 28.01 V/m	Grid 3 M4 27.83 V/m
Grid 4 M4 14.93 V/m	Grid 5 M4 22.90 V/m	Grid 6 M4 23.39 V/m
Grid 7 M4 28.44 V/m	Grid 8 M4 37.03 V/m	Grid 9 M4 36.96 V/m

Cursor:

Total = 37.03 V/m

E Category: M4

Location: -7.5, 25, 8.7 mm

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007:
15 mm from Probe Center to the Device_High_Chan/Hearing Aid**

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 13.13 V/m; Power Drift = -0.09 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 26.13 V/m

Near-field category: M4 (AWF 0 dB)

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PMF scaled E-field

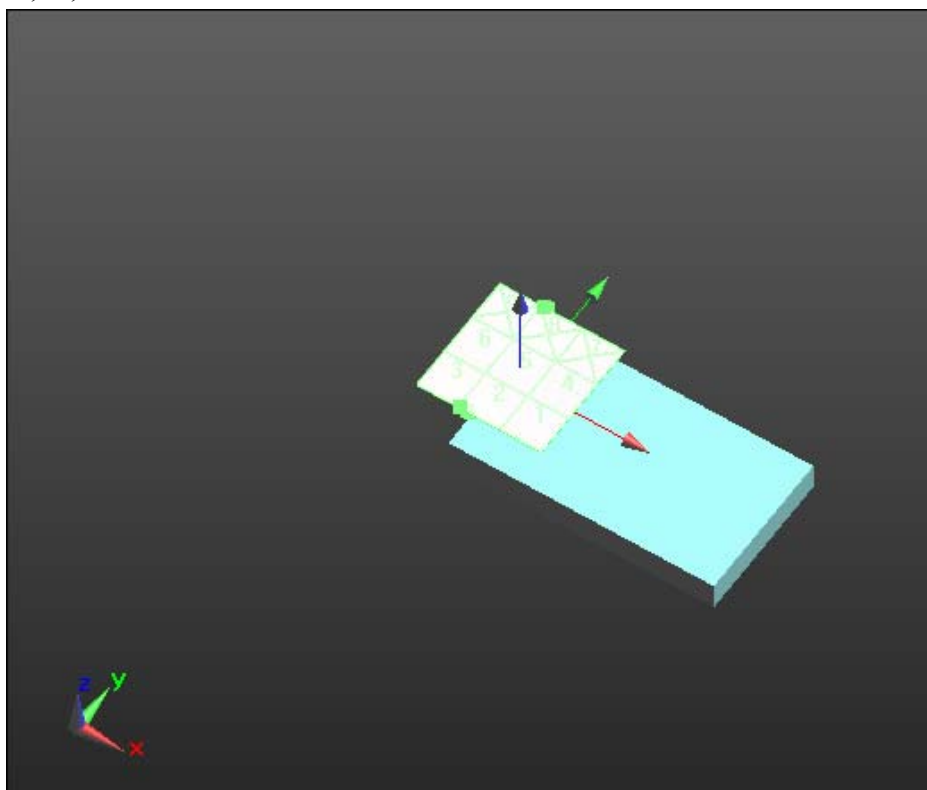
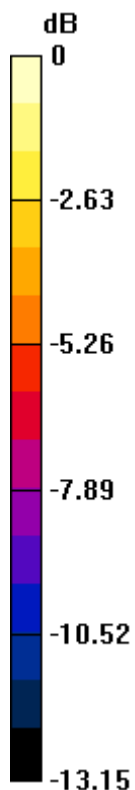
Grid 1 M4 21.80 V/m	Grid 2 M4 26.13 V/m	Grid 3 M4 26.11 V/m
Grid 4 M4 12.66 V/m	Grid 5 M4 20.16 V/m	Grid 6 M4 20.67 V/m
Grid 7 M4 24.70 V/m	Grid 8 M4 32.81 V/m	Grid 9 M4 32.75 V/m

Cursor:

Total = 32.81 V/m

E Category: M4

Location: -7.5, 25, 8.7 mm



0 dB = 35.61 V/m = 31.03 dBV/m

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Date/Time: 4/26/2013 11:38:47 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_Band_II_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 333CB445

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 17.27 V/m; Power Drift = -0.18 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 29.49 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 27.03 V/m	Grid 2 M4 29.49 V/m	Grid 3 M4 29.40 V/m
Grid 4 M4 15.14 V/m	Grid 5 M4 19.57 V/m	Grid 6 M4 20.02 V/m
Grid 7 M4 22.33 V/m	Grid 8 M4 31.12 V/m	Grid 9 M4 31.36 V/m

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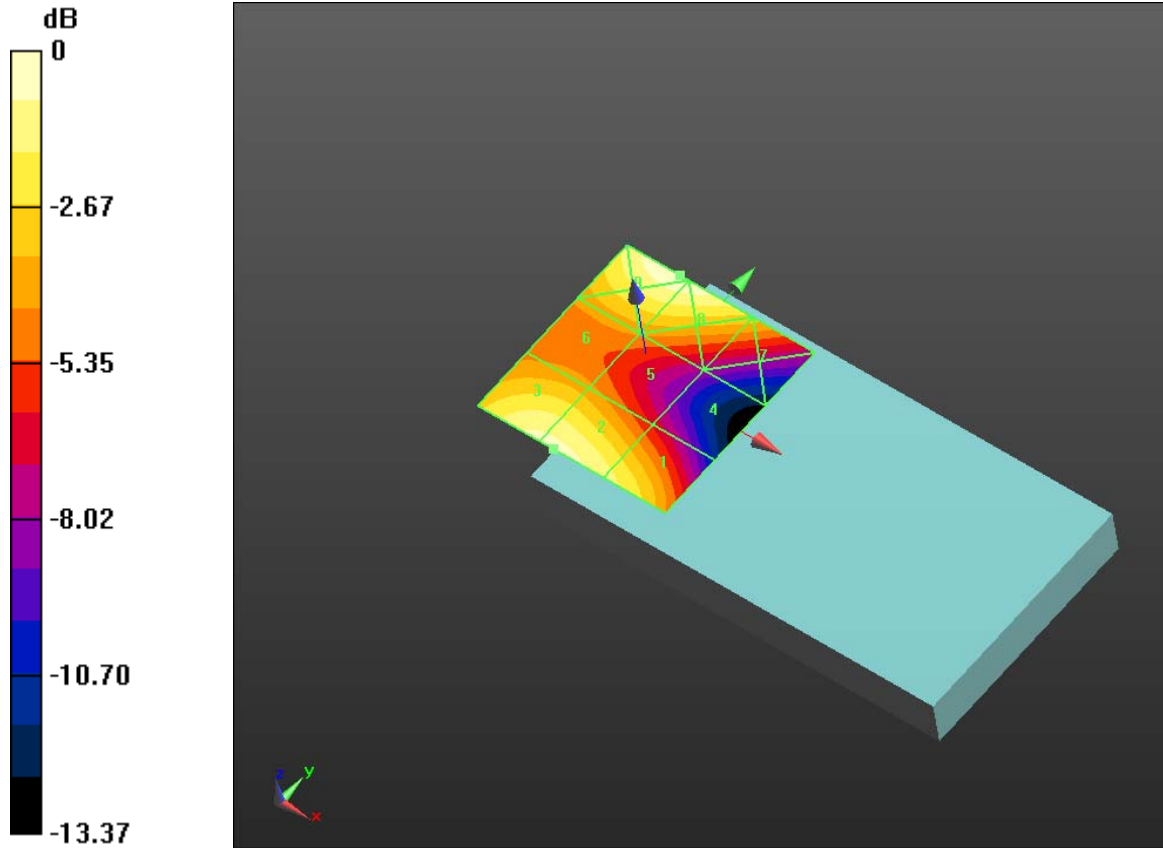
		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 106 (158)
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Cursor:

Total = 31.36 V/m

E Category: M4

Location: -7, 20, 8.7 mm



0 dB = 31.36 V/m = 29.93 dBV/m

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Date/Time: 4/26/2013 10:18:46 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_CDMA850

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 333CB445

Communication System: CDMA 850, Communication System: CDMA 850 1/8th Rate;

Frequency: 824.7 MHz, Frequency: 836.52 MHz, Frequency: 848.52 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chann_Full_Rate/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 55.05 V/m; Power Drift = 0.10 dB

PMR not calibrated. PMF = 1.060 is applied.

E-field emissions = 49.89 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 44.38 V/m	Grid 2 M4 49.40 V/m	Grid 3 M4 49.28 V/m
Grid 4 M4 42.34 V/m	Grid 5 M4 49.89 V/m	Grid 6 M4 49.89 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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41.10 V/m	48.62 V/m	48.62 V/m
------------------	------------------	------------------

Cursor:

Total = 49.89 V/m

E Category: M4

Location: -8, -0.5, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007:

15 mm from Probe Center to the

Device_Mid_Chan_Full_Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 60.95 V/m; Power Drift = -0.03 dB

PMR not calibrated. PMF = 1.060 is applied.

E-field emissions = 56.99 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 46.57 V/m	Grid 2 M4 55.15 V/m	Grid 3 M4 55.17 V/m
Grid 4 M4 45.55 V/m	Grid 5 M4 56.99 V/m	Grid 6 M4 57.14 V/m
Grid 7 M4 44.95 V/m	Grid 8 M4 56.26 V/m	Grid 9 M4 56.35 V/m

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Cursor:

Total = 57.14 V/m

E Category: M4

Location: -9.5, 1, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007:

15 mm from Probe Center to the

Device_High_Chan_Full_Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 72.50 V/m; Power Drift = 0.06 dB

PMR not calibrated. PMF = 1.060 is applied.

E-field emissions = 67.18 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 55.38 V/m	Grid 2 M4 65.92 V/m	Grid 3 M4 66.03 V/m
Grid 4 M4 53.74 V/m	Grid 5 M4 67.18 V/m	Grid 6 M4 67.30 V/m
Grid 7 M4 52.26 V/m	Grid 8 M4 66.51 V/m	Grid 9 M4 66.69 V/m

Cursor:

Total = 67.30 V/m

E Category: M4

Location: -9.5, 0.5, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007:

15 mm from Probe Center to the

Device_High_Chan_1/8th_Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 25.80 V/m; Power Drift = 0.24 dB

PMR not calibrated. PMF = 2.900 is applied.

E-field emissions = 74.78 V/m

Near-field category: M4 (AWF 0 dB)

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PMF scaled E-field

Grid 1 M4 61.33 V/m	Grid 2 M4 73.02 V/m	Grid 3 M4 67.44 V/m
Grid 4 M4 60.26 V/m	Grid 5 M4 74.78 V/m	Grid 6 M4 76.77 V/m
Grid 7 M4 56.97 V/m	Grid 8 M4 73.83 V/m	Grid 9 M4 73.67 V/m

Cursor:

Total = 76.77 V/m

E Category: M4

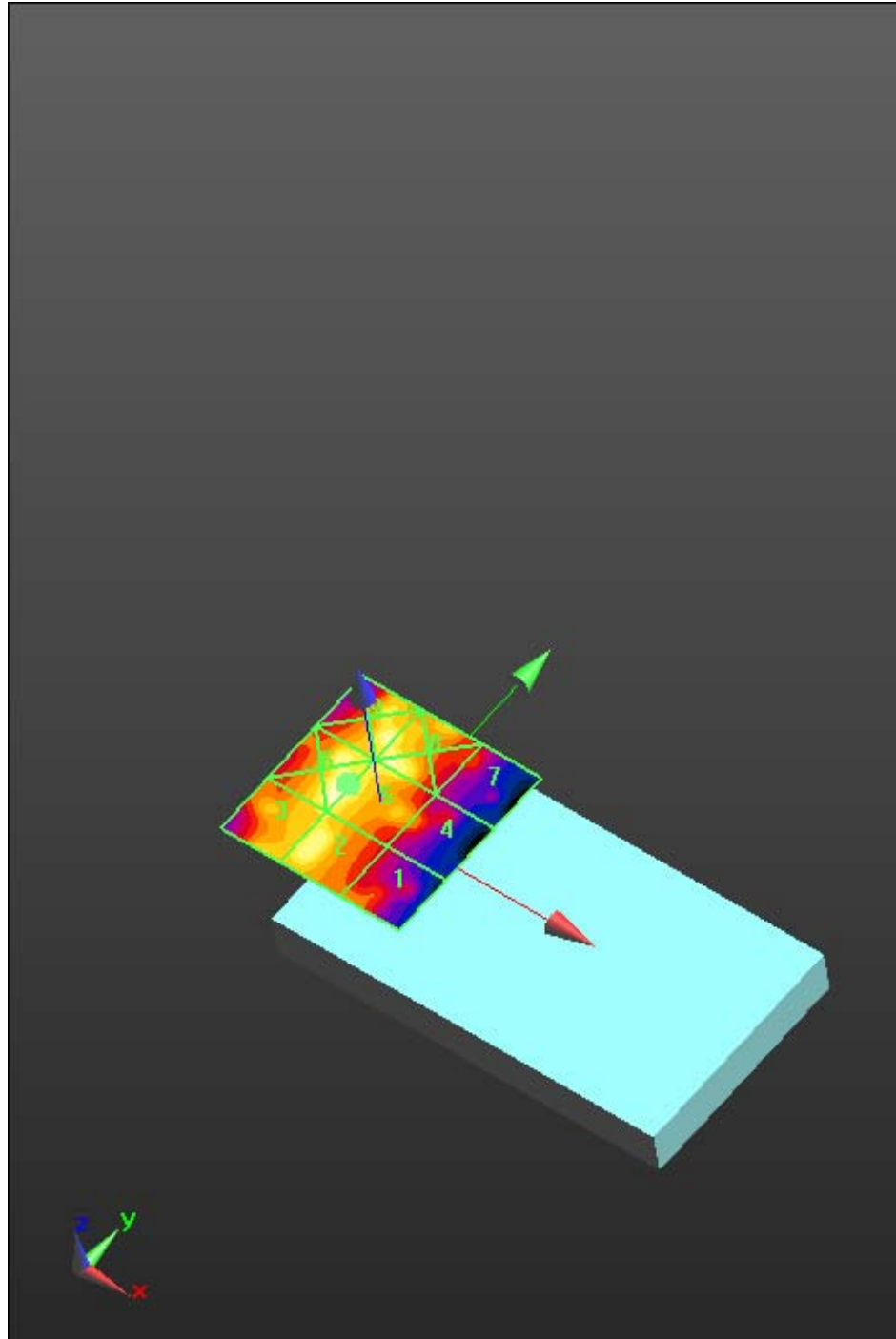
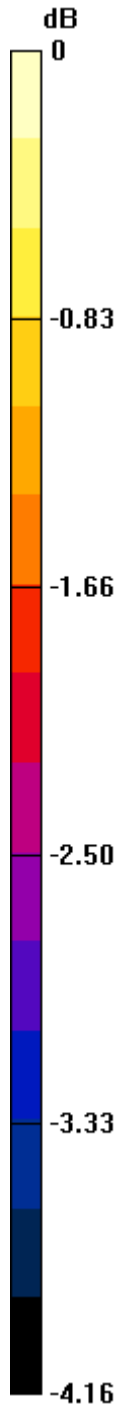
Location: -10, -0.5, 8.7 mm

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW



0 dB = 49.89 V/m = 33.96 dBV/m

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Date/Time: 4/26/2013 11:21:31 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_CDMA850_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 333CB445

Communication System: CDMA 850 1/8th Rate; Frequency: 848.52 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from
Probe Center to the_Device_High_Chan_1/8th_Rate_Telecoil/Hearing Aid
Compatibility Test (101x101x1):** Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 30.68 V/m; Power Drift = -1.10 dB

PMR not calibrated. PMF = 2.900 is applied.

E-field emissions = 72.82 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 60.59 V/m	Grid 2 M4 72.61 V/m	Grid 3 M4 68.83 V/m
Grid 4 M4 57.06 V/m	Grid 5 M4 72.81 V/m	Grid 6 M4 77.14 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW

51.08 V/m

72.56 V/m

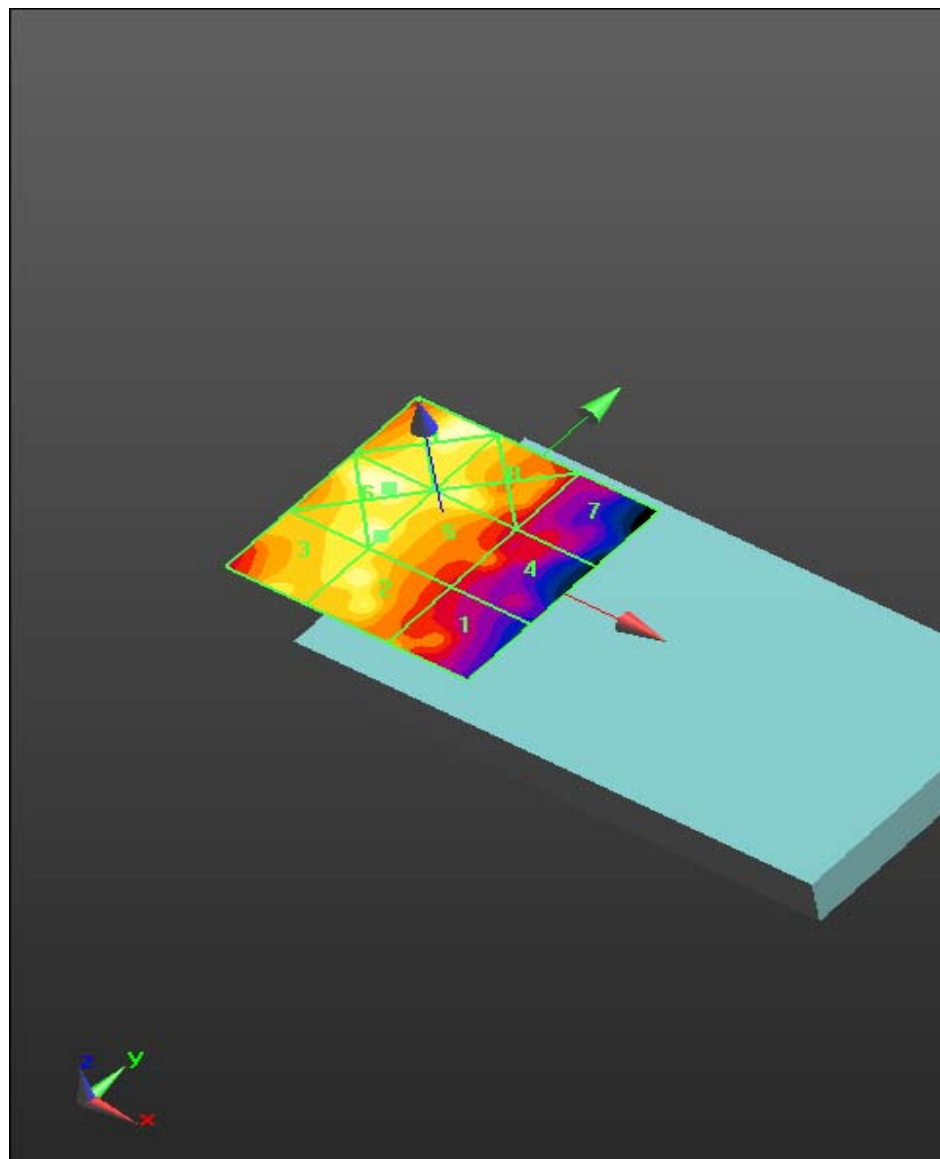
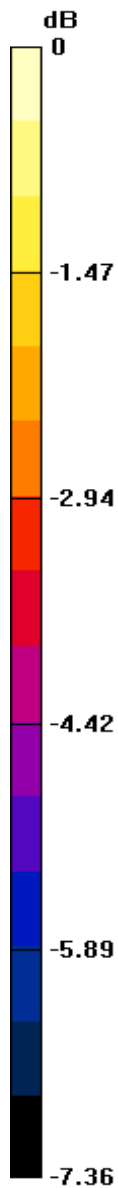
76.02 V/m

Cursor:

Total = 77.14 V/m

E Category: M4

Location: -11, 0, 8.7 mm



0 dB = 77.13 V/m = 37.74 dBV/m

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Date/Time: 4/26/2013 5:50:59 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_CDMA1900

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 333CB445

Communication System: CDMA 1900, Communication System: CDMA 1900 1/8th Rate;

Frequency: 1851.25 MHz, Frequency: 1880 MHz, Frequency: 1908.5 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from
Probe Center to Device_Low_Chann_Full_Rate/Hearing Aid Compatibility Test
(101x101x1):** Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 20.20 V/m; Power Drift = -0.07 dB

PMR not calibrated. PMF = 1.010 is applied.

E-field emissions = 24.64 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 22.84 V/m	Grid 2 M4 24.64 V/m	Grid 3 M4 23.92 V/m
Grid 4 M4 15.48 V/m	Grid 5 M4 22.32 V/m	Grid 6 M4 22.85 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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19.39 V/m	28.55 V/m	28.54 V/m
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Cursor:

Total = 28.55 V/m

E Category: M4

Location: -8, 25, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007:

15 mm from Probe Center to the

Device_Mid_Chan_Full_Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 18.42 V/m; Power Drift = -0.02 dB

PMR not calibrated. PMF = 1.010 is applied.

E-field emissions = 23.42 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 22.23 V/m	Grid 2 M4 23.42 V/m	Grid 3 M4 22.95 V/m
Grid 4 M4 13.70 V/m	Grid 5 M4 21.97 V/m	Grid 6 M4 22.88 V/m
Grid 7 M4 19.17 V/m	Grid 8 M4 29.15 V/m	Grid 9 M4 29.20 V/m

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Cursor:

Total = 29.20 V/m

E Category: M4

Location: -9.5, 25, 8.7 mm

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007:
15 mm from Probe Center to the
Device_High_Chan_Full_Rate/Hearing Aid Compatibility Test**

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 19.76 V/m; Power Drift = -0.20 dB

PMR not calibrated. PMF = 1.010 is applied.

E-field emissions = 28.70 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 26.31 V/m	Grid 2 M4 28.70 V/m	Grid 3 M4 28.23 V/m
Grid 4 M4 16.59 V/m	Grid 5 M4 23.15 V/m	Grid 6 M4 24.03 V/m
Grid 7 M4 20.91 V/m	Grid 8 M4 32.82 V/m	Grid 9 M4 32.91 V/m

Cursor:

Total = 32.91 V/m

E Category: M4

Location: -9.5, 25, 8.7 mm

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007:
15 mm from Probe Center to the
Device_High_Chan_1/8th_Rate/Hearing Aid Compatibility Test**

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 6.951 V/m; Power Drift = -0.28 dB

PMR not calibrated. PMF = 2.670 is applied.

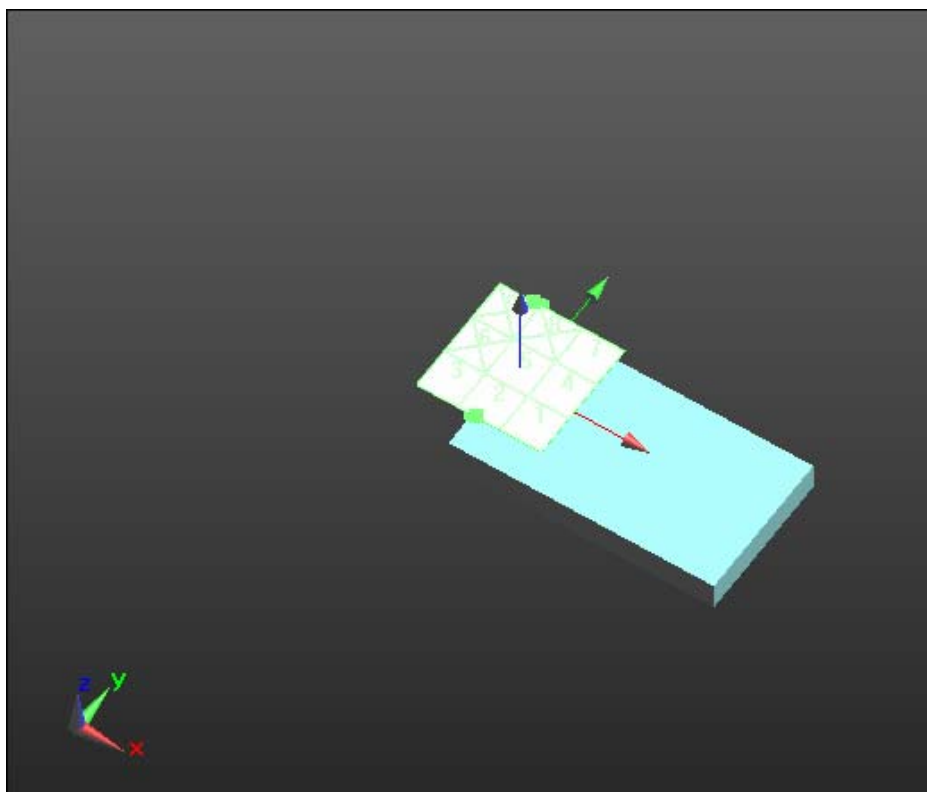
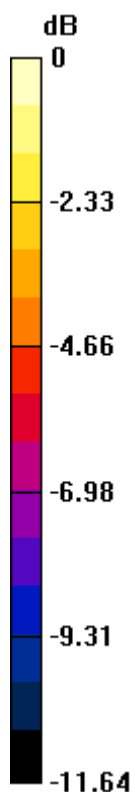
E-field emissions = 26.31 V/m

Near-field category: M4 (AWF 0 dB)

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PMF scaled E-field

Grid 1 M4 24.31 V/m	Grid 2 M4 26.31 V/m	Grid 3 M4 26.12 V/m
Grid 4 M4 15.49 V/m	Grid 5 M4 20.76 V/m	Grid 6 M4 21.89 V/m
Grid 7 M4 18.52 V/m	Grid 8 M4 32.51 V/m	Grid 9 M4 33.86 V/m



0 dB = 28.26 V/m = 29.02 dBV/m

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Date/Time: 4/26/2013 6:14:05 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_CDMA1900_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 333CB445

Communication System: CDMA 1900; Frequency: 1908.5 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from
Probe Center to the_Device_High_Chan_Full_Rate_Telecoil/Hearing Aid
Compatibility Test (101x101x1):** Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 19.23 V/m; Power Drift = 0.00 dB

PMR not calibrated. PMF = 1.010 is applied.

E-field emissions = 30.45 V/m

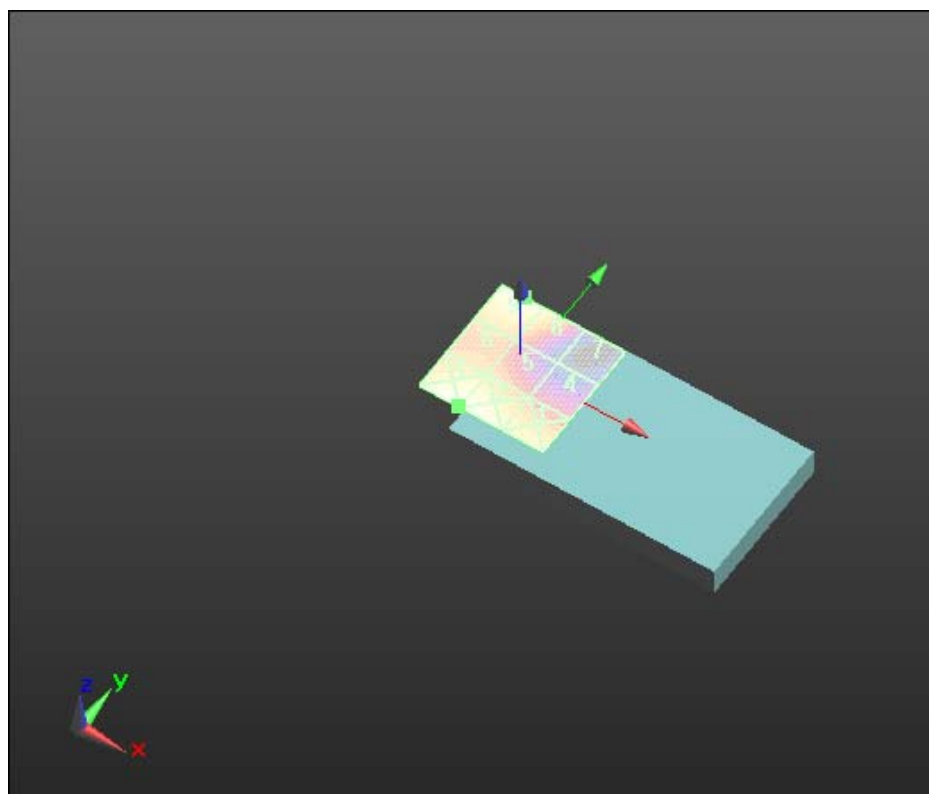
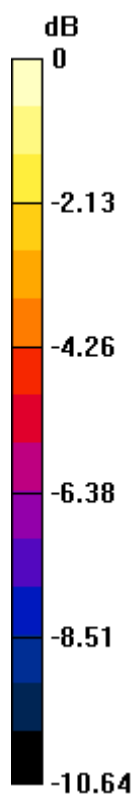
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 27.33 V/m	Grid 2 M4 30.70 V/m	Grid 3 M4 30.71 V/m
Grid 4 M4 17.91 V/m	Grid 5 M4 22.05 V/m	Grid 6 M4 22.23 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

	Document		Page
	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		119 (158)
Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW

14.08 V/m	28.18 V/m	30.45 V/m
------------------	------------------	------------------



0 dB = 30.40 V/m = 29.66 dBV/m

		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 120 (158)
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Date/Time: 4/26/2013 12:02:31 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM1900_2100mA_Battery

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 333CB445

Communication System: GSM 1900; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_telecoil_2100mA_Battery/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 7.944 V/m; Power Drift = 0.53 dB

PMR not calibrated. PMF = 2.850 is applied.

E-field emissions = 57.05 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M3 49.23 V/m	Grid 2 M3 57.05 V/m	Grid 3 M3 56.95 V/m
Grid 4 M4 27.25 V/m	Grid 5 M4 36.45 V/m	Grid 6 M4 37.20 V/m
Grid 7 M4	Grid 8 M3	Grid 9 M3

		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 121 (158)
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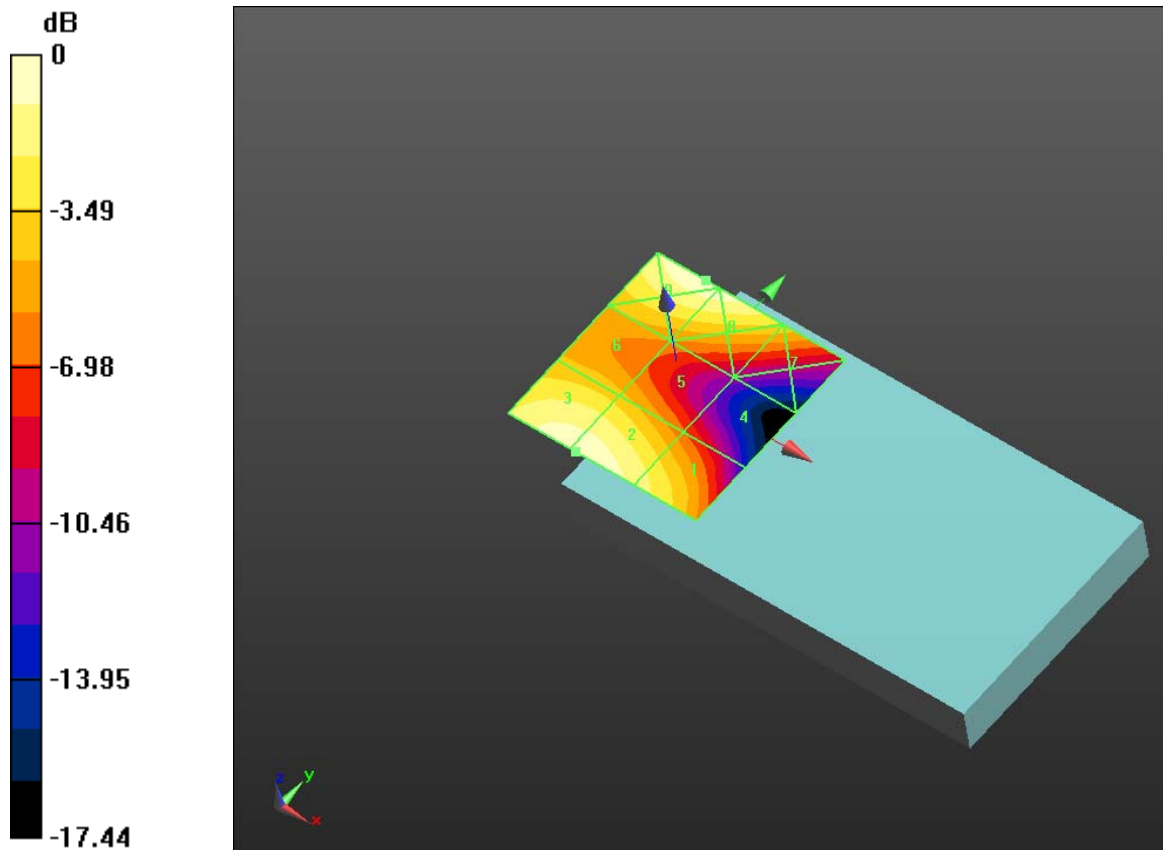
39.03 V/m	57.46 V/m	58.35 V/m
------------------	------------------	------------------

Cursor:

Total = 58.35 V/m

E Category: M3

Location: -8, 20, 8.7 mm



0 dB = 58.99 V/m = 35.42 dBV/m

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Date/Time: 4/28/2013 1:54:21 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_850

DUT: BlackBerry Smartphone; Type: Sample; Serial: 333CB445

Communication System: GSM 850; Frequency: 824.2 MHz, Frequency: 836.8 MHz, Frequency: 848.8 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06800 A/m; Power Drift = -0.02 dB

PMR not calibrated. PMF = 2.890 is applied.

H-field emissions = 0.3059 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

Grid 1 M4 0.306 A/m	Grid 2 M4 0.226 A/m	Grid 3 M4 0.145 A/m
Grid 4 M4 0.336 A/m	Grid 5 M4 0.249 A/m	Grid 6 M4 0.173 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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0.399 A/m	0.296 A/m	0.204 A/m
------------------	------------------	------------------

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07300 A/m; Power Drift = 0.13 dB

PMR not calibrated. PMF = 2.890 is applied.

H-field emissions = 0.3397 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

Grid 1 M4 0.340 A/m	Grid 2 M4 0.249 A/m	Grid 3 M4 0.154 A/m
Grid 4 M4 0.367 A/m	Grid 5 M4 0.274 A/m	Grid 6 M4 0.184 A/m
Grid 7 M4 0.440 A/m	Grid 8 M4 0.326 A/m	Grid 9 M4 0.222 A/m

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07800 A/m; Power Drift = 0.09 dB

PMR not calibrated. PMF = 2.890 is applied.

H-field emissions = 0.3347 A/m

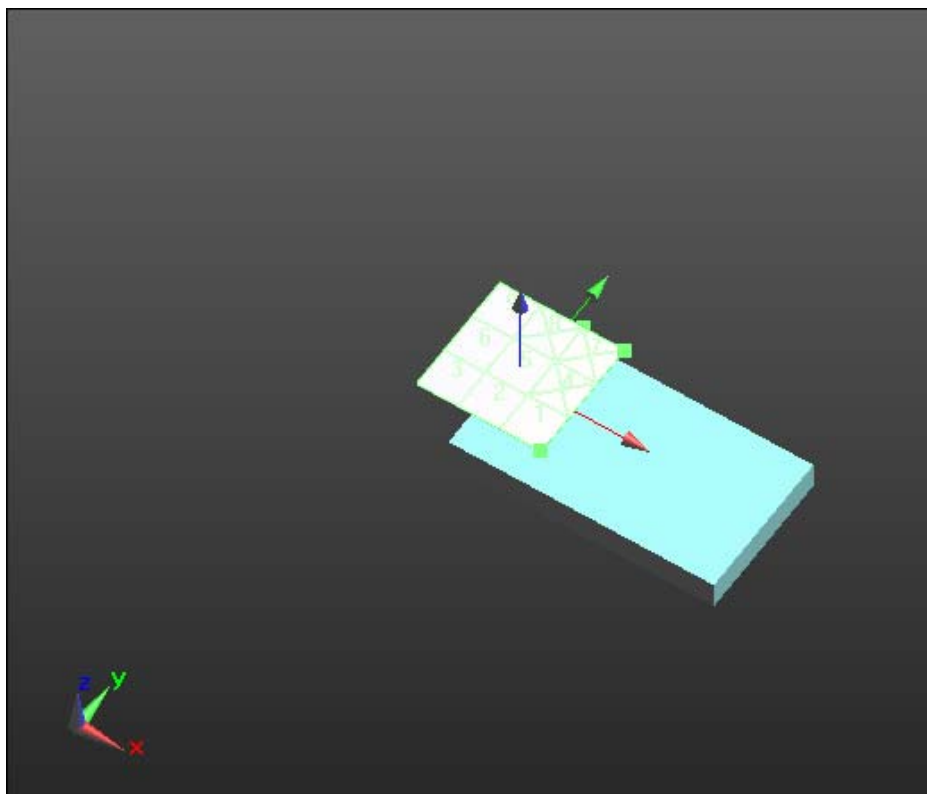
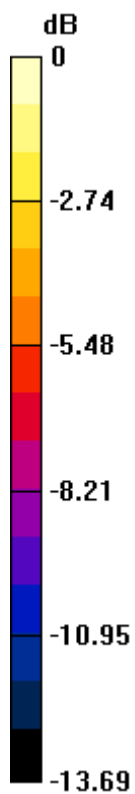
Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

Grid 1 M4 0.335 A/m	Grid 2 M4 0.259 A/m	Grid 3 M4 0.178 A/m
--------------------------------------	--------------------------------------	--------------------------------------

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Grid 4 M4 0.362 A/m	Grid 5 M4 0.285 A/m	Grid 6 M4 0.206 A/m
Grid 7 M4 0.431 A/m	Grid 8 M4 0.336 A/m	Grid 9 M4 0.246 A/m



0 dB = 0.3974 A/m = -8.02 dBA/m

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Date/Time: 4/28/2013 2:13:10 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_850_Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 333CB445

Communication System: GSM 850; Frequency: 836.8 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07200 A/m; Power Drift = 0.12 dB

PMR not calibrated. PMF = 2.890 is applied.

H-field emissions = 0.3672 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

Grid 1 M4 0.367 A/m	Grid 2 M4 0.277 A/m	Grid 3 M4 0.179 A/m
Grid 4 M4 0.366 A/m	Grid 5 M4 0.282 A/m	Grid 6 M4 0.190 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

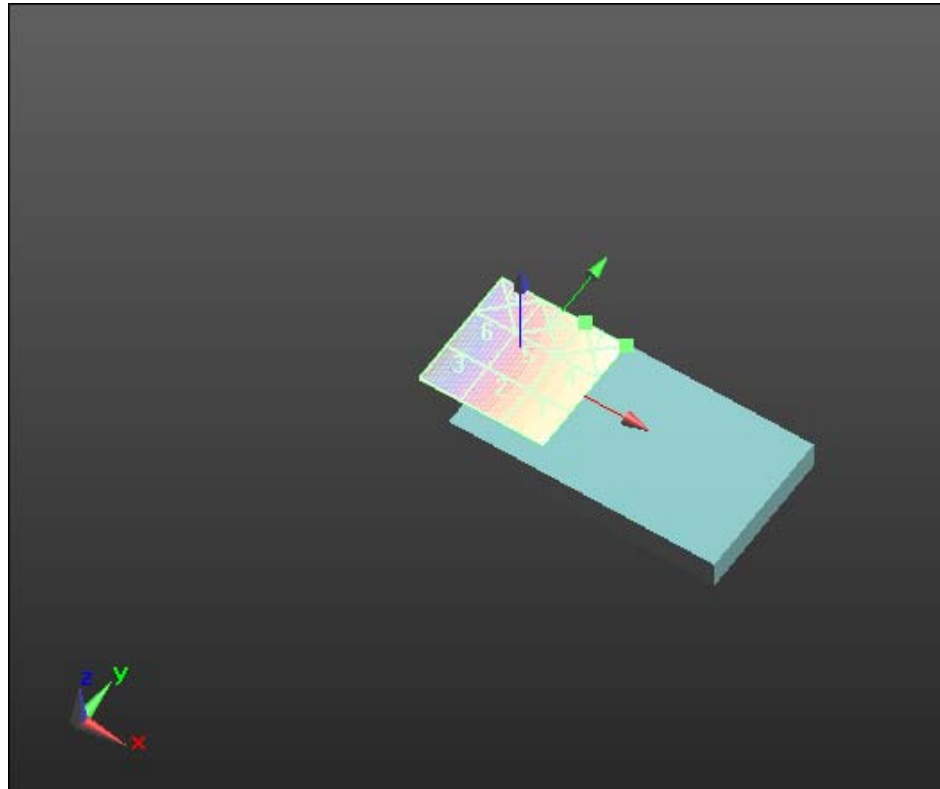
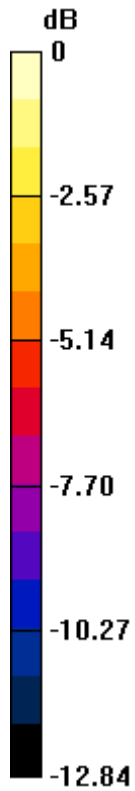
Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW

0.428 A/m

0.326 A/m

0.222 A/m



0 dB = 0.4267 A/m = -7.40 dBA/m

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Date/Time: 4/28/2013 1:16:48 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_V

DUT: BlackBerry Smartphone; Type: Sample; Serial: 333CB445

Communication System: WCDMA FDD V; Frequency: 826.4 MHz, Frequency: 836.4 MHz,
Frequency: 846.6 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

**Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm
from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test
(101x101x1):** Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06700 A/m; Power Drift = 0.13 dB

PMR not calibrated. PMF = 1.090 is applied.

H-field emissions = 0.1128 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.113 A/m	Grid 2 M4 0.084 A/m	Grid 3 M4 0.055 A/m
Grid 4 M4 0.126 A/m	Grid 5 M4 0.094 A/m	Grid 6 M4 0.066 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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0.152 A/m	0.113 A/m	0.079 A/m
------------------	------------------	------------------

Cursor:

Total = 0.1521 A/m

H Category: M4

Location: 25, 25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08000 A/m; Power Drift = 0.05 dB

PMR not calibrated. PMF = 1.090 is applied.

H-field emissions = 0.1420 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.142 A/m	Grid 2 M4 0.105 A/m	Grid 3 M4 0.065 A/m
Grid 4 M4 0.150 A/m	Grid 5 M4 0.113 A/m	Grid 6 M4 0.076 A/m
Grid 7 M4 0.180 A/m	Grid 8 M4 0.134 A/m	Grid 9 M4 0.092 A/m

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Cursor:

Total = 0.1799 A/m

H Category: M4

Location: 25, 25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08800 A/m; Power Drift = 0.00 dB

PMR not calibrated. PMF = 1.090 is applied.

H-field emissions = 0.1408 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.141 A/m	Grid 2 M4 0.109 A/m	Grid 3 M4 0.073 A/m
Grid 4 M4 0.156 A/m	Grid 5 M4 0.122 A/m	Grid 6 M4 0.086 A/m
Grid 7 M4 0.187 A/m	Grid 8 M4 0.145 A/m	Grid 9 M4 0.103 A/m

Cursor:

Total = 0.1873 A/m

H Category: M4

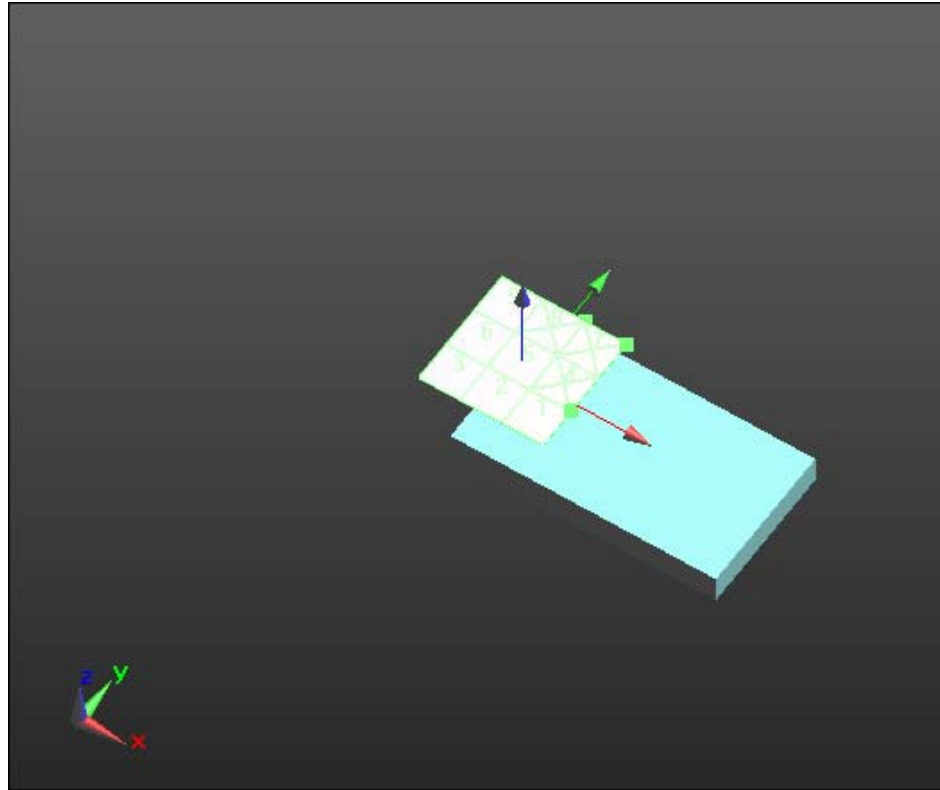
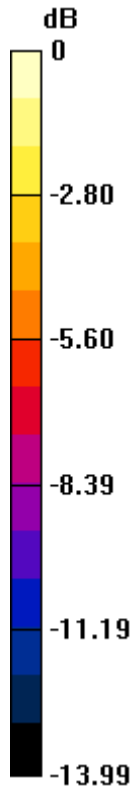
Location: 25, 25, 8.7 mm

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

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0 dB = 0.1521 A/m = -16.36 dBA/m

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Date/Time: 4/28/2013 1:30:12 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_V_Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 333CB445

Communication System: WCDMA FDD V; Frequency: 836.4 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08000 A/m; Power Drift = 0.01 dB

PMR not calibrated. PMF = 1.090 is applied.

H-field emissions = 0.1533 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.153 A/m	Grid 2 M4 0.116 A/m	Grid 3 M4 0.075 A/m
Grid 4 M4 0.153 A/m	Grid 5 M4 0.119 A/m	Grid 6 M4 0.080 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW	

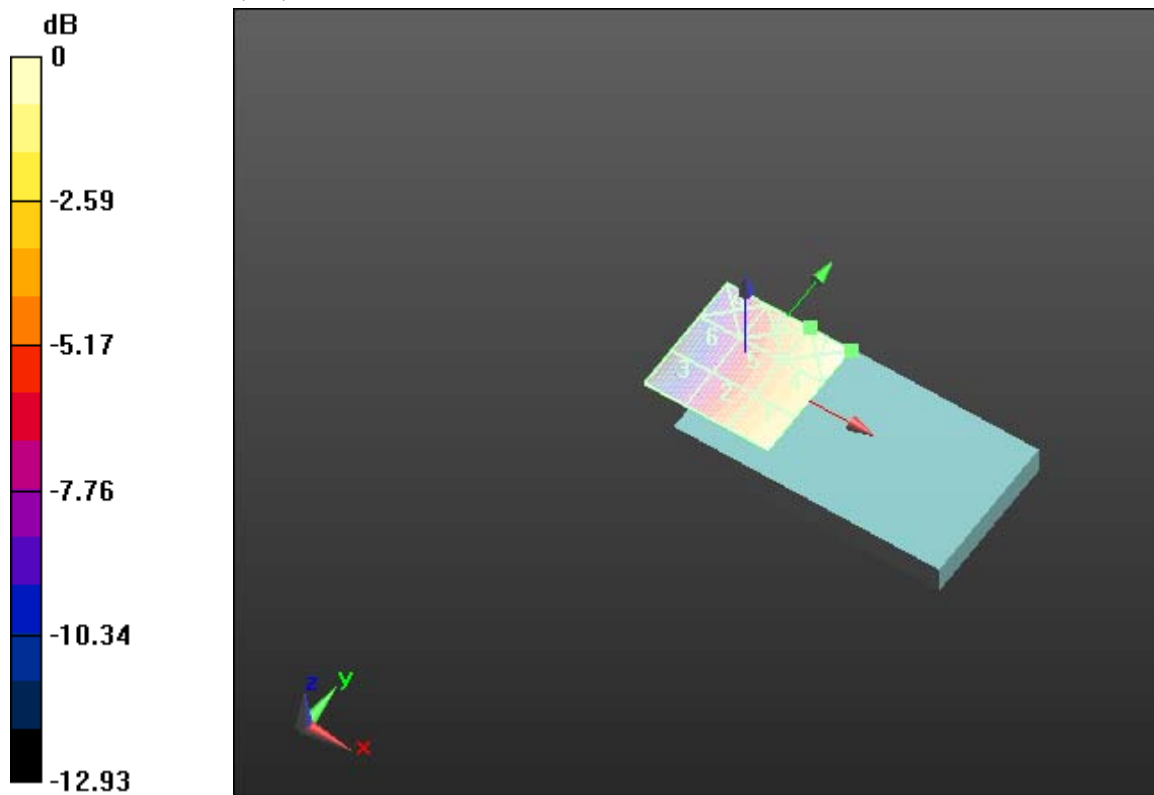
0.180 A/m	0.138 A/m	0.095 A/m
------------------	------------------	------------------

Cursor:

Total = 0.1802 A/m

H Category: M4

Location: 29, 20, 8.7 mm



0 dB = 0.1802 A/m = -14.88 dBA/m

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Date/Time: 4/28/2013 1:35:31 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_1900

DUT: BlackBerry Smartphone; Type: Sample; Serial: 333CB445

Communication System: GSM 1900; Frequency: 1850.2 MHz, Frequency: 1880 MHz,
Frequency: 1909.8 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

**Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm
from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test
(101x101x1):** Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05100 A/m; Power Drift = -0.10 dB

PMR not calibrated. PMF = 2.860 is applied.

H-field emissions = 0.1488 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

Grid 1 M4 0.105 A/m	Grid 2 M3 0.144 A/m	Grid 3 M3 0.145 A/m
Grid 4 M4 0.116 A/m	Grid 5 M3 0.148 A/m	Grid 6 M3 0.149 A/m
Grid 7 M3	Grid 8 M3	Grid 9 M3

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0.169 A/m	0.141 A/m	0.142 A/m
------------------	------------------	------------------

Cursor:

Total = 0.1685 A/m

H Category: M3

Location: 25, 25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05300 A/m; Power Drift = 0.19 dB

PMR not calibrated. PMF = 2.860 is applied.

H-field emissions = 0.1602 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

Grid 1 M4 0.105 A/m	Grid 2 M3 0.152 A/m	Grid 3 M3 0.153 A/m
Grid 4 M4 0.119 A/m	Grid 5 M3 0.159 A/m	Grid 6 M3 0.160 A/m
Grid 7 M3 0.163 A/m	Grid 8 M3 0.154 A/m	Grid 9 M3 0.155 A/m

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05500 A/m; Power Drift = -0.07 dB

PMR not calibrated. PMF = 2.860 is applied.

H-field emissions = 0.1635 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

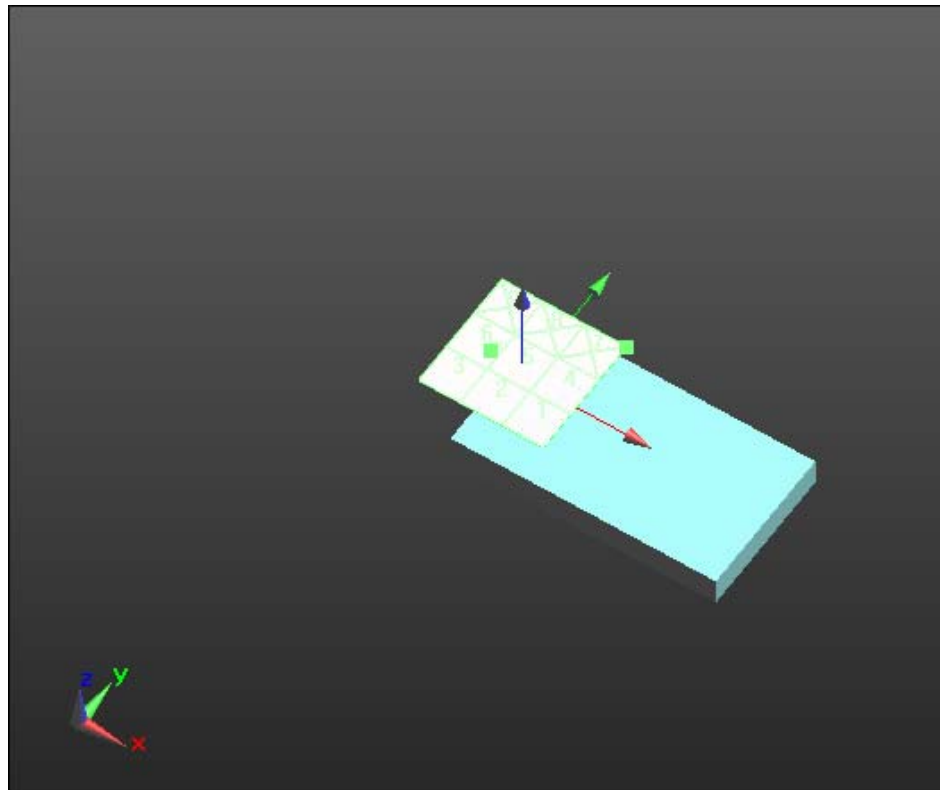
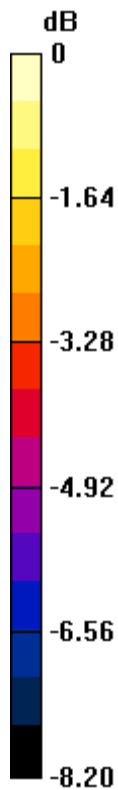
Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW

Grid 1 M4 0.108 A/m	Grid 2 M3 0.156 A/m	Grid 3 M3 0.159 A/m
Grid 4 M4 0.126 A/m	Grid 5 M3 0.161 A/m	Grid 6 M3 0.163 A/m
Grid 7 M3 0.175 A/m	Grid 8 M3 0.156 A/m	Grid 9 M3 0.157 A/m



0 dB = 0.1697 A/m = -15.41 dBA/m

		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFQ111LW		Page 136 (158)
Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW	

Date/Time: 4/28/2013 1:48:38 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_1900_Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 333CB445

Communication System: GSM 1900; Frequency: 1909.8 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05400 A/m; Power Drift = 0.06 dB

PMR not calibrated. PMF = 2.860 is applied.

H-field emissions = 0.1545 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

Grid 1 M4 0.127 A/m	Grid 2 M4 0.138 A/m	Grid 3 M3 0.148 A/m
Grid 4 M4 0.108 A/m	Grid 5 M3 0.151 A/m	Grid 6 M3 0.160 A/m
Grid 7 M3	Grid 8 M3	Grid 9 M3

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Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013		Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW

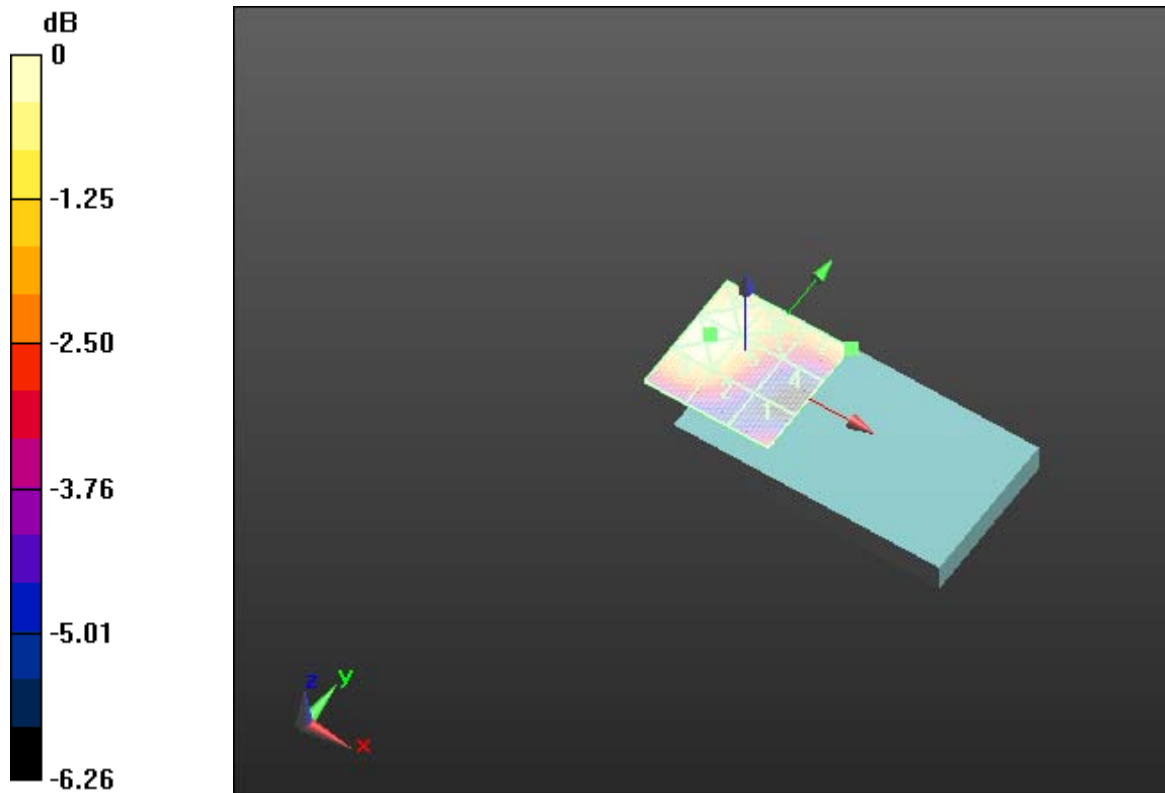
0.155 A/m	0.150 A/m	0.158 A/m
------------------	------------------	------------------

Cursor:

Total = 0.1599 A/m

H Category: M3

Location: -13, -1.5, 8.7 mm



0 dB = 0.1610 A/m = -15.86 dBA/m

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Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW	

Date/Time: 4/28/2013 12:56:43 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_II

DUT: BlackBerry Smartphone; Type: Sample; Serial: 333CB445

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz, Frequency: 1880 MHz,
Frequency: 1907.6 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

**Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm
from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test
(101x101x1):** Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07900 A/m; Power Drift = 0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.08345 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.058 A/m	Grid 2 M4 0.081 A/m	Grid 3 M4 0.082 A/m
Grid 4 M4 0.060 A/m	Grid 5 M4 0.083 A/m	Grid 6 M4 0.083 A/m

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Grid 7 M4 0.085 A/m	Grid 8 M4 0.079 A/m	Grid 9 M4 0.079 A/m
--------------------------------------	--------------------------------------	--------------------------------------

Cursor:

Total = 0.08488 A/m

H Category: M4

Location: 25, 25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07900 A/m; Power Drift = 0.00 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.08192 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.054 A/m	Grid 2 M4 0.078 A/m	Grid 3 M4 0.079 A/m
Grid 4 M4 0.062 A/m	Grid 5 M4 0.081 A/m	Grid 6 M4 0.082 A/m
Grid 7 M4 0.089 A/m	Grid 8 M4 0.079 A/m	Grid 9 M4 0.080 A/m

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Cursor:

Total = 0.08854 A/m

H Category: M4

Location: 25, 25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08000 A/m; Power Drift = 0.11 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.08486 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.054 A/m	Grid 2 M4 0.081 A/m	Grid 3 M4 0.083 A/m
Grid 4 M4 0.065 A/m	Grid 5 M4 0.083 A/m	Grid 6 M4 0.085 A/m
Grid 7 M4 0.091 A/m	Grid 8 M4 0.081 A/m	Grid 9 M4 0.081 A/m

Cursor:

Total = 0.09057 A/m

H Category: M4

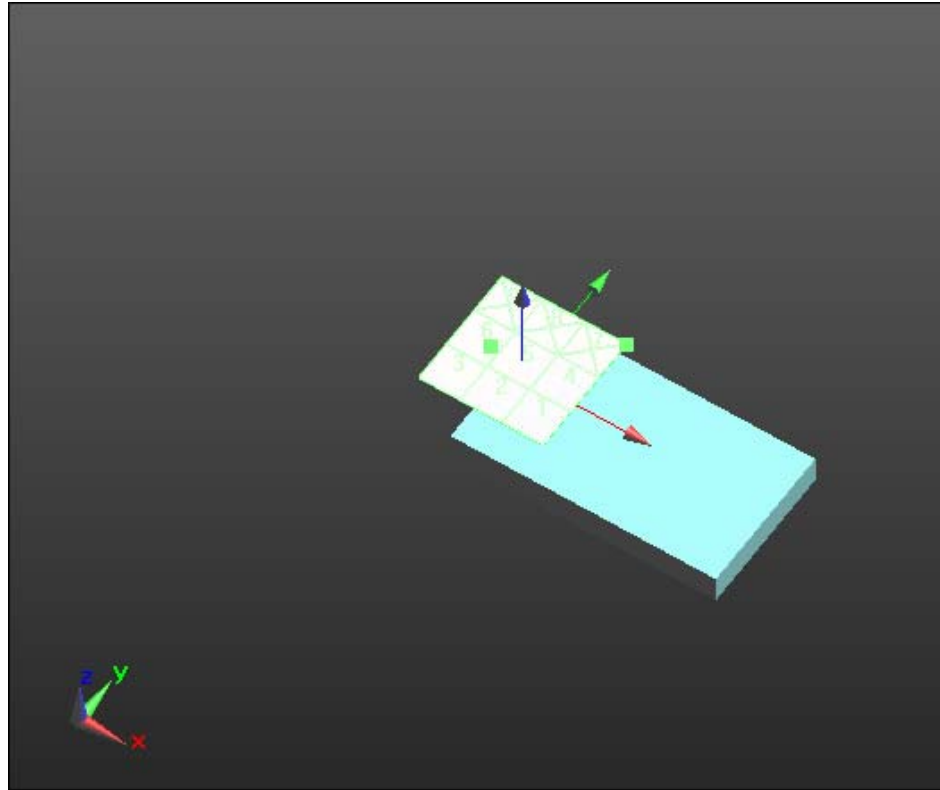
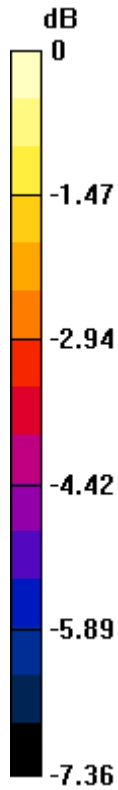
Location: 25, 25, 8.7 mm

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW



0 dB = 0.08488 A/m = -21.42 dBA/m

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Date/Time: 4/28/2013 1:12:09 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_II_Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 333CB445

Communication System: WCDMA FDD II; Frequency: 1907.6 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08100 A/m; Power Drift = -0.03 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.08220 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.063 A/m	Grid 2 M4 0.072 A/m	Grid 3 M4 0.078 A/m
Grid 4 M4 0.057 A/m	Grid 5 M4 0.079 A/m	Grid 6 M4 0.084 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012 April 24-26, 2013	Report No RTS-6026-1304-52	FCC ID L6ARFQ110LW	

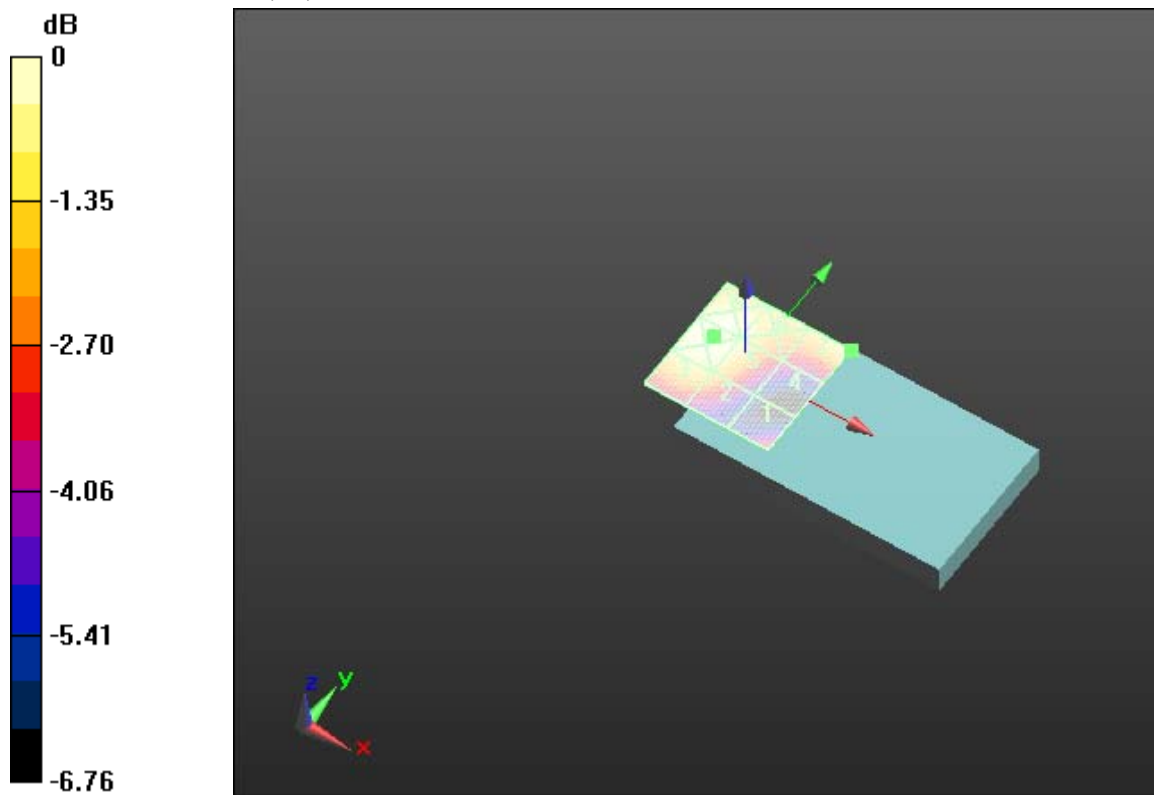
0.082 A/m	0.079 A/m	0.083 A/m
------------------	------------------	------------------

Cursor:

Total = 0.08413 A/m

H Category: M4

Location: -12.5, -1, 8.7 mm



0 dB = 0.08413 A/m = -21.50 dBA/m

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Date/Time: 4/28/2013 2:51:43 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_CDMA850

DUT: BlackBerry Smartphone; Type: Sample; Serial: 333CB445

Communication System: CDMA 850, Communication System: CDMA 850 1/8th Rate;

Frequency: 824.7 MHz, Frequency: 836.52 MHz, Frequency: 848.52 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

**Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm
from Probe Center to the Device_low_chan_Full_Rate/Hearing Aid**

Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05500 A/m; Power Drift = 0.00 dB

PMR not calibrated. PMF = 1.030 is applied.

H-field emissions = 0.1231 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.123 A/m	Grid 2 M4 0.089 A/m	Grid 3 M4 0.062 A/m
Grid 4 M4 0.101 A/m	Grid 5 M4 0.074 A/m	Grid 6 M4 0.051 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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0.088 A/m	0.065 A/m	0.042 A/m
------------------	------------------	------------------

Cursor:

Total = 0.1231 A/m

H Category: M4

Location: 25, -25, 8.7 mm

**Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 -
2007: 15 mm from Probe Center to the**

Device_mid_chan_Full_Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06500 A/m; Power Drift = -0.12 dB

PMR not calibrated. PMF = 1.030 is applied.

H-field emissions = 0.1304 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.130 A/m	Grid 2 M4 0.097 A/m	Grid 3 M4 0.069 A/m
Grid 4 M4 0.109 A/m	Grid 5 M4 0.083 A/m	Grid 6 M4 0.057 A/m
Grid 7 M4 0.100 A/m	Grid 8 M4 0.076 A/m	Grid 9 M4 0.049 A/m

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Cursor:

Total = 0.1304 A/m

H Category: M4

Location: 25, -25, 8.7 mm

**Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 -
2007: 15 mm from Probe Center to the
Device_high_chan_Full_Rate/Hearing Aid Compatibility Test**

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08200 A/m; Power Drift = 0.01 dB

PMR not calibrated. PMF = 1.030 is applied.

H-field emissions = 0.1551 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.155 A/m	Grid 2 M4 0.120 A/m	Grid 3 M4 0.084 A/m
Grid 4 M4 0.135 A/m	Grid 5 M4 0.106 A/m	Grid 6 M4 0.074 A/m
Grid 7 M4 0.131 A/m	Grid 8 M4 0.102 A/m	Grid 9 M4 0.072 A/m

Cursor:

Total = 0.1551 A/m

H Category: M4

Location: 25, -25, 8.7 mm

**Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 -
2007: 15 mm from Probe Center to the
Device_high_chan_1/8th_Rate/Hearing Aid Compatibility Test**

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.03000 A/m; Power Drift = 0.19 dB

PMR not calibrated. PMF = 2.650 is applied.

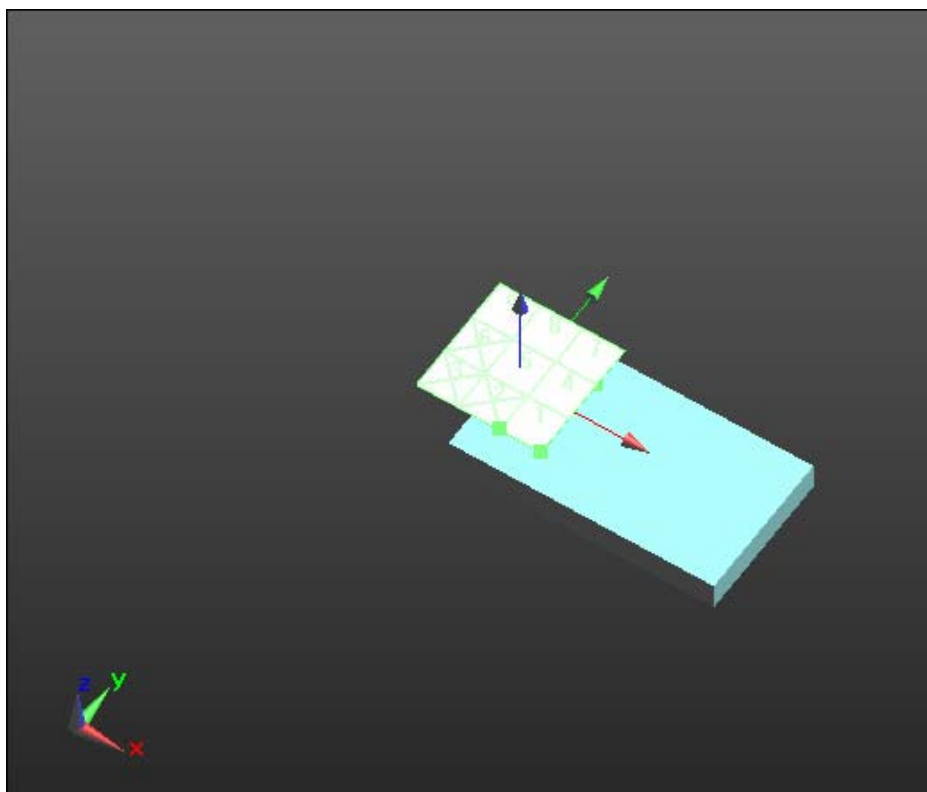
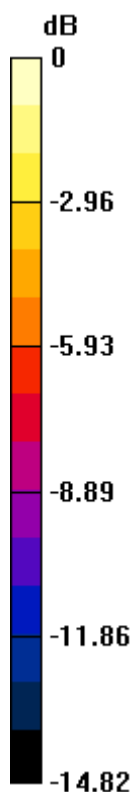
H-field emissions = 0.1488 A/m

Near-field category: M4 (AWF 0 dB)

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PMF scaled H-field

Grid 1 M4 0.149 A/m	Grid 2 M4 0.111 A/m	Grid 3 M4 0.079 A/m
Grid 4 M4 0.128 A/m	Grid 5 M4 0.099 A/m	Grid 6 M4 0.068 A/m
Grid 7 M4 0.122 A/m	Grid 8 M4 0.096 A/m	Grid 9 M4 0.067 A/m



0 dB = 0.1231 A/m = -18.19 dBA/m

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Date/Time: 4/28/2013 3:10:29 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_CDMA850_Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 333CB445

Communication System: CDMA 850; Frequency: 848.52 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_telecoil_Full_Rate/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08500 A/m; Power Drift = -0.18 dB

PMR not calibrated. PMF = 1.060 is applied.

H-field emissions = 0.1793 A/m

Near-field category: M4 (AWF 0 dB)

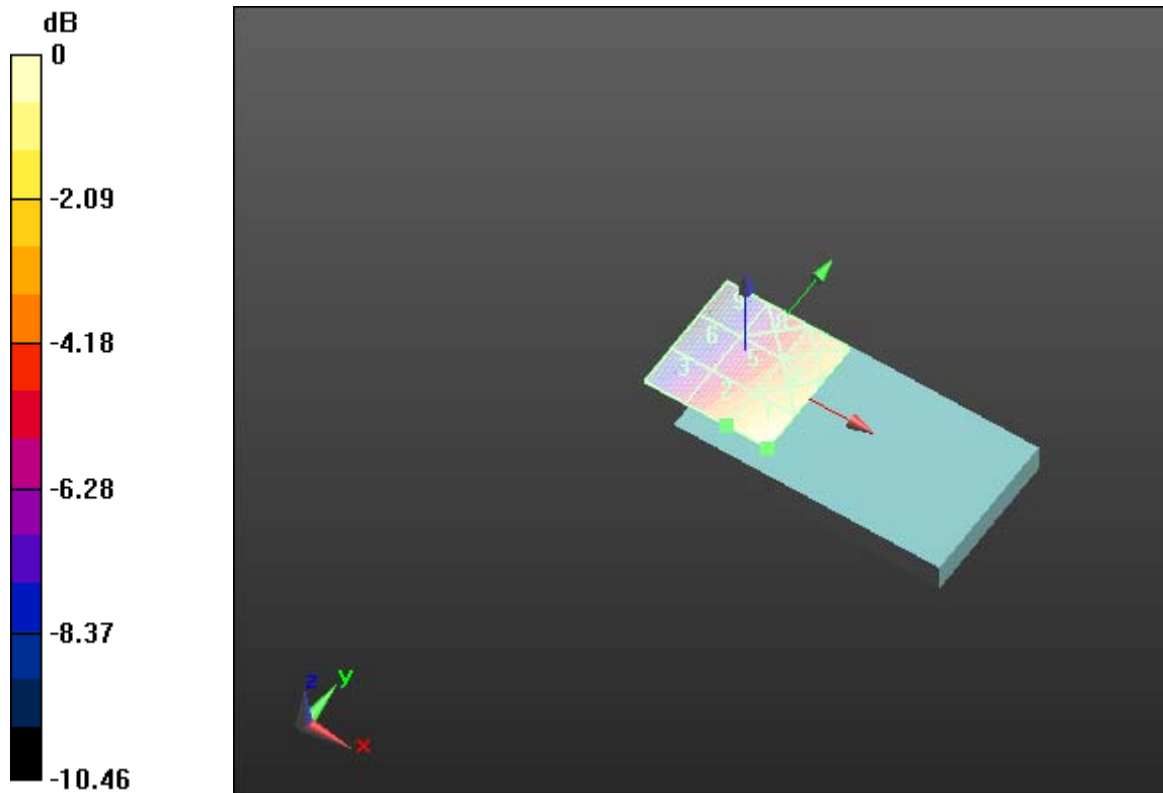
PMF scaled H-field

Grid 1 M4 0.179 A/m	Grid 2 M4 0.141 A/m	Grid 3 M4 0.098 A/m
Grid 4 M4 0.156 A/m	Grid 5 M4 0.122 A/m	Grid 6 M4 0.086 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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0.142 A/m	0.112 A/m	0.080 A/m
------------------	------------------	------------------

Cursor:
Total = 0.1793 A/m
H Category: M4
Location: 29, -30, 8.7 mm



0 dB = 0.1793 A/m = -14.93 dBA/m

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Date/Time: 4/28/2013 2:21:18 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_CDMA1900

DUT: BlackBerry Smartphone; Type: Sample; Serial: 333CB445

Communication System: CDMA 1900, Communication System: CDMA 1900 1/8th Rate;

Frequency: 1851.25 MHz, Frequency: 1880 MHz, Frequency: 1908.5 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

**Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm
from Probe Center to the Device_low_chan_Full_Rate/Hearing Aid**

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06000 A/m; Power Drift = -0.06 dB

PMR not calibrated. PMF = 0.9900 is applied.

H-field emissions = 0.07762 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.078 A/m	Grid 2 M4 0.061 A/m	Grid 3 M4 0.061 A/m
Grid 4 M4 0.055 A/m	Grid 5 M4 0.060 A/m	Grid 6 M4 0.061 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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0.060 A/m	0.052 A/m	0.052 A/m
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Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan_Full_Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06800 A/m; Power Drift = -0.06 dB

PMR not calibrated. PMF = 0.9900 is applied.

H-field emissions = 0.07666 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.077 A/m	Grid 2 M4 0.065 A/m	Grid 3 M4 0.065 A/m
Grid 4 M4 0.056 A/m	Grid 5 M4 0.065 A/m	Grid 6 M4 0.065 A/m
Grid 7 M4 0.067 A/m	Grid 8 M4 0.058 A/m	Grid 9 M4 0.058 A/m

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan_Full_Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08400 A/m; Power Drift = -0.01 dB

PMR not calibrated. PMF = 0.9900 is applied.

H-field emissions = 0.08337 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.079 A/m	Grid 2 M4 0.082 A/m	Grid 3 M4 0.083 A/m
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Grid 4 M4 0.066 A/m	Grid 5 M4 0.082 A/m	Grid 6 M4 0.083 A/m
Grid 7 M4 0.083 A/m	Grid 8 M4 0.076 A/m	Grid 9 M4 0.076 A/m

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan_1/8th_Rate/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.02600 A/m; Power Drift = 0.18 dB

PMR not calibrated. PMF = 2.600 is applied.

H-field emissions = 0.07824 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

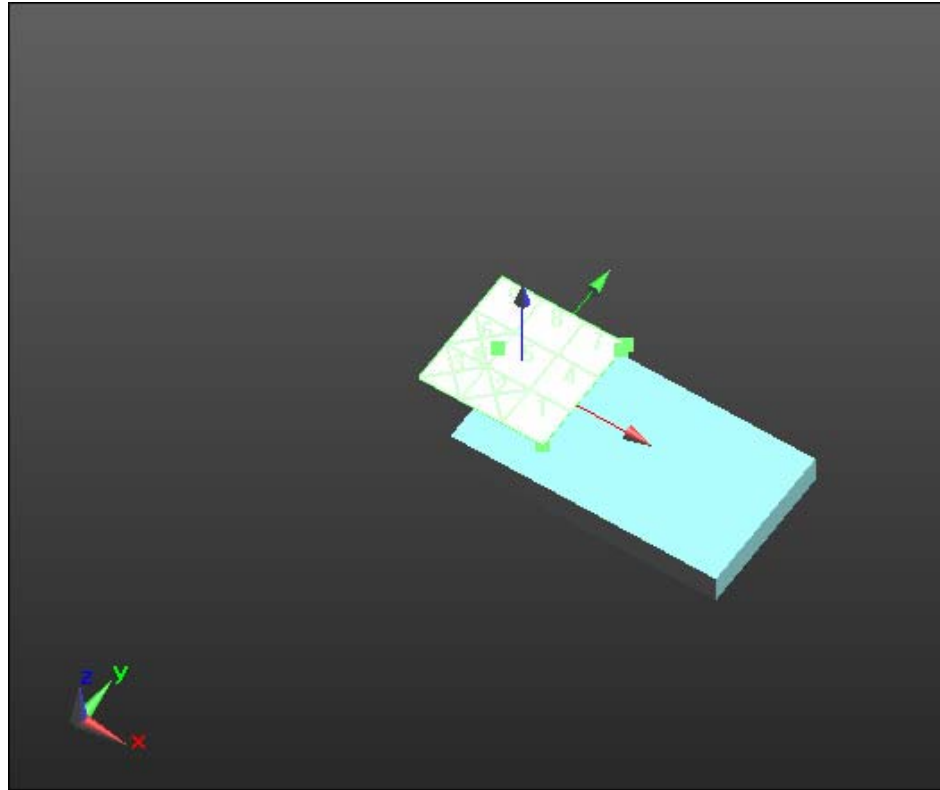
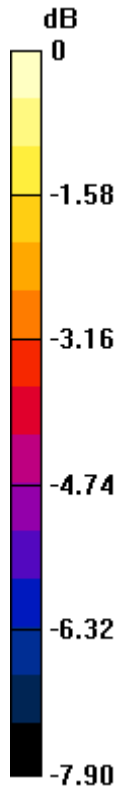
Grid 1 M4 0.069 A/m	Grid 2 M4 0.069 A/m	Grid 3 M4 0.078 A/m
Grid 4 M4 0.059 A/m	Grid 5 M4 0.076 A/m	Grid 6 M4 0.079 A/m
Grid 7 M4 0.078 A/m	Grid 8 M4 0.072 A/m	Grid 9 M4 0.067 A/m

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

Report No
RTS-6026-1304-52

FCC ID
L6ARFQ110LW



0 dB = 0.07762 A/m = -22.20 dBA/m

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Date/Time: 4/28/2013 2:45:59 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_CDMA1900_Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 333CB445

Communication System: CDMA 1900; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BADASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_telecoil_Full_Rate/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08000 A/m; Power Drift = 0.07 dB

PMR not calibrated. PMF = 0.9900 is applied.

H-field emissions = 0.07927 A/m

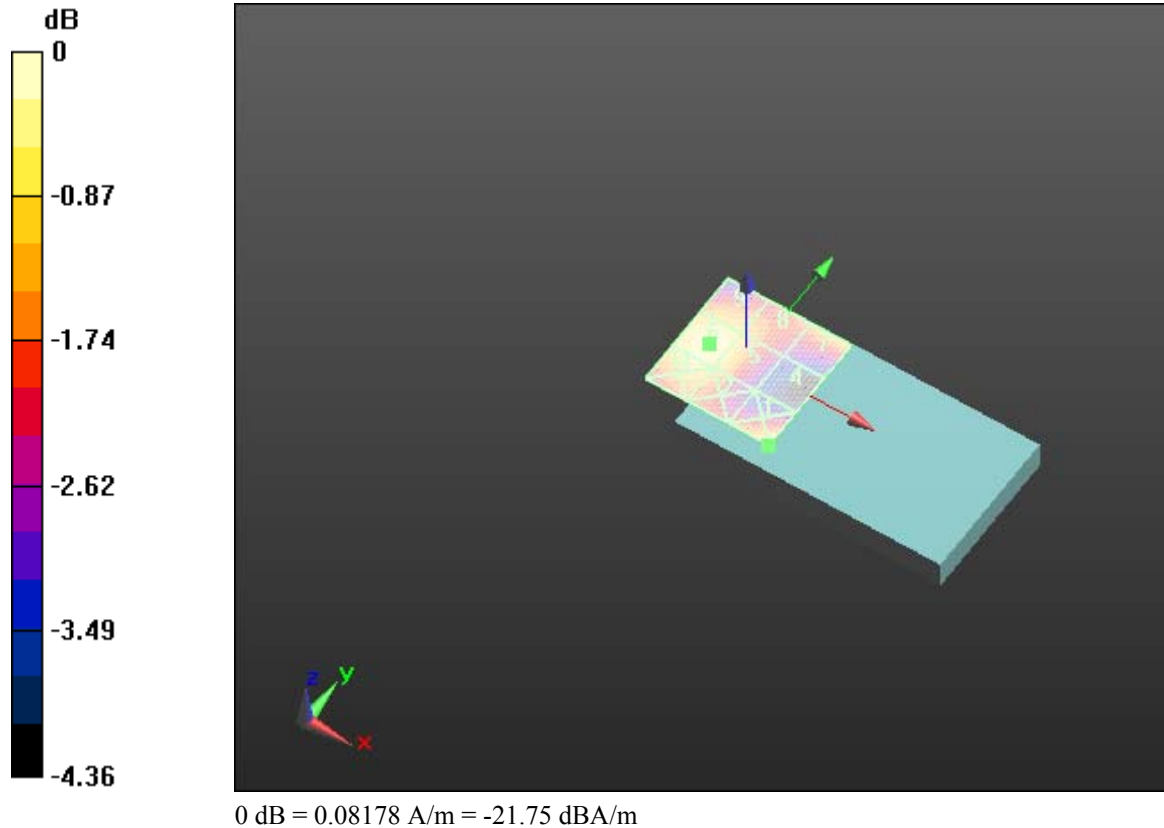
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.082 A/m	Grid 2 M4 0.074 A/m	Grid 3 M4 0.077 A/m
Grid 4 M4 0.059 A/m	Grid 5 M4 0.076 A/m	Grid 6 M4 0.079 A/m

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Grid 7 M4 0.074 A/m	Grid 8 M4 0.073 A/m	Grid 9 M4 0.074 A/m
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Date/Time: 4/28/2013 3:29:44 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_1900_2100mA

DUT: BlackBerry Smartphone; Type: Sample; Serial: 333CB445

Communication System: GSM 1900; Frequency: 1909.8 MHz

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_telecoil_2100mA_Battery/Hearing Aid

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05500 A/m; Power Drift = 0.03 dB

PMR not calibrated. PMF = 2.860 is applied.

H-field emissions = 0.1522 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

Grid 1 M4 0.133 A/m	Grid 2 M4 0.140 A/m	Grid 3 M3 0.147 A/m
Grid 4 M4 0.108 A/m	Grid 5 M3 0.152 A/m	Grid 6 M3 0.159 A/m
Grid 7 M3	Grid 8 M3	Grid 9 M3

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0.152 A/m	0.151 A/m	0.158 A/m
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Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device_high_chan_2100mA_Battery/Hearing Aid Compatibility

Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05500 A/m; Power Drift = -0.03 dB

PMR not calibrated. PMF = 2.860 is applied.

H-field emissions = 0.1597 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

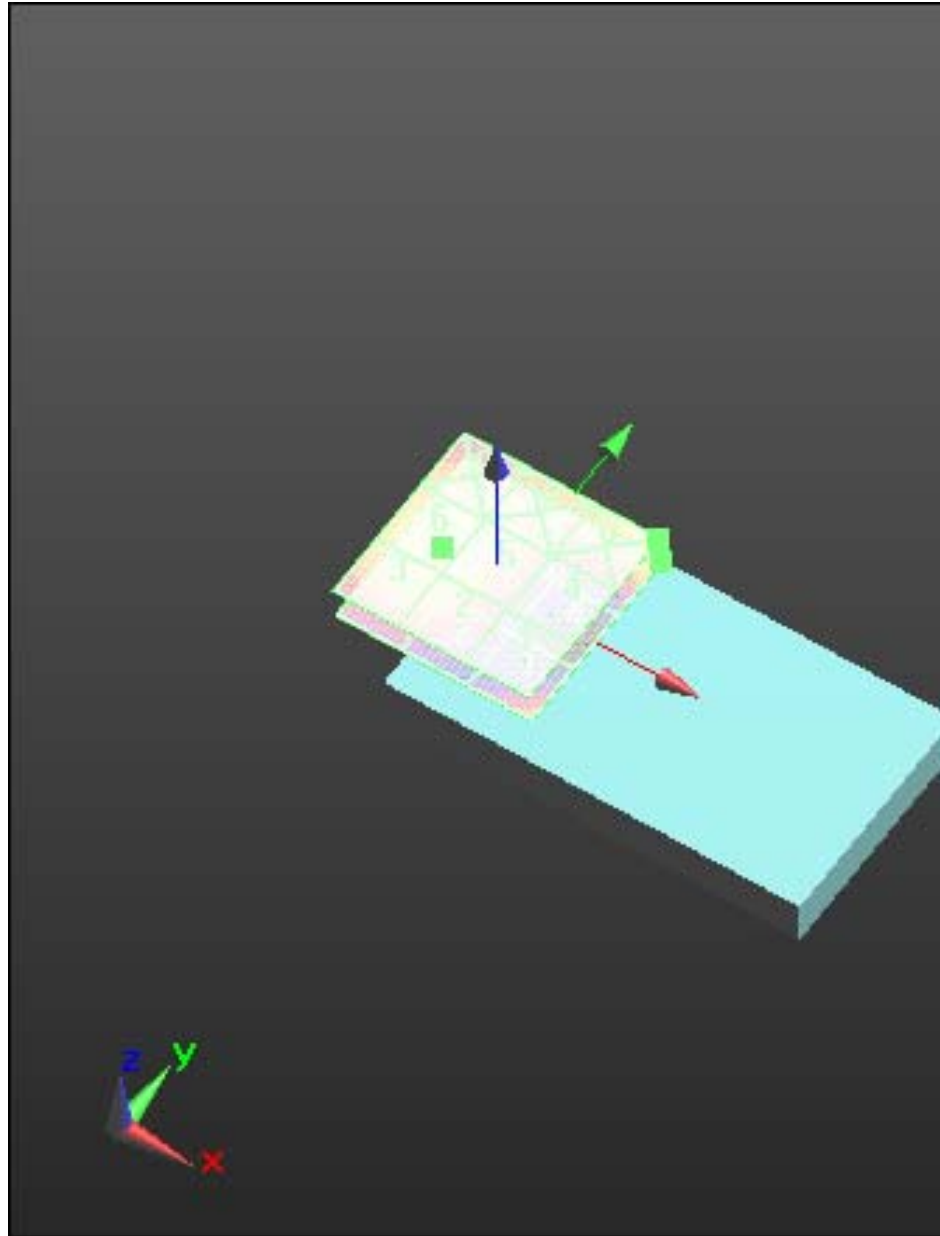
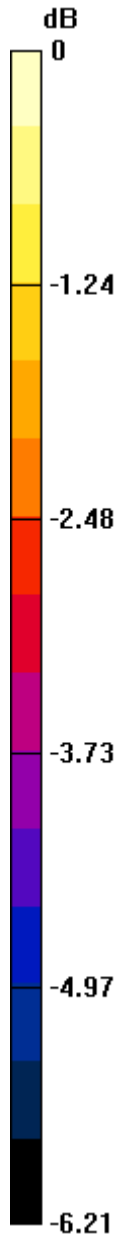
Grid 1 M4 0.108 A/m	Grid 2 M3 0.154 A/m	Grid 3 M3 0.156 A/m
Grid 4 M4 0.122 A/m	Grid 5 M3 0.158 A/m	Grid 6 M3 0.160 A/m
Grid 7 M3 0.170 A/m	Grid 8 M3 0.153 A/m	Grid 9 M3 0.153 A/m

Author Data
Daoud Attayi

Dates of Test
**Feb. 17-29, June 28, 2012
 April 24-26, 2013**

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0 dB = 0.1605 A/m = -15.89 dBA/m